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> Contract JPL-954796 Quarterly Report April to July 1978 (DRD Line Item 6)

> > November 1978





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The JPL Low-Cost Silicon Solar Array Project is sponsored by the U.S. Department of Energy and forms part of the Solar Photovoltaic Conversion Program to initiate a major effort toward the development of low-cost solar arrays. This work was performed for the Jet Propulsion Laboratory, California Institute of Technology by agreement between NASA and DOE. DOE/JPL-954796-78/4 Distribution List 647 of 5-15-1978

ANALYSIS AND EVALUATION

OF PROCESSES AND EQUIPMENT

IN TASKS II and IV

of the

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ABSTRACT

The significant economic data for the current production multiblade wafering and inner diameter slicing processes were tabulated and compared to data on the experimental and projected Varian multiblade slurry, STC ID diamond coated blade, Yasunaga multiwire slurry and Crystal Systems fixed abrasive multiwire slicing methods. Cost calculations were performed for current production processes and for 1982 and 1986 projected wafering techniques.

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1. INTRODUCTION

The manufacturing methods for photovoltaic solar energy utilization systems consist, in complete generality, of a sequence of individual processes. This process sequence has been, for convenience, logically segmented into five major "work areas": Reduction and purification of the semiconductor material, sheet or film generation, device generation, module assembly and encapsulation, and system completion, including installation of the array and the other subsystems. For silicon solar arrays, each work area has been divided into 10 generalized "processes" in which certain required modifications of the work-in-process are performed. In general, more than one method is known by which such modifications can be carried out. The various methods for each individual process are identified as process "options". This system of processes and options forms a twodimensional array, which is here called the "process matrix".

In the search to achieve improved process sequences for producing silicon solar cell modules, numerous options have been proposed and/or developed, and will still be proposed and developed in the future. It is a near necessity to be able to evaluate such proposals for the technical merits relative to other known approaches, for their economic benefits, and for other techno-economic attributes such as energy consumption, generation and disposal of waste by-products, etc. Such evaluations have to be as objective as possible in light of the available information, or the lack thereof, and have to be periodically updated as development progresses and new information becomes available. Since each individual

process option has to fit into a process sequence, technical interfaces between consecutive processes must be compatible. This places emphasis on the specifications for the work-in-process entering into and emanating from a particular process option.

The objective of this project is to accumulate the necessary information as input for such evaluations, to develop appropriate methodologies for the performance of such techno-economic analyses, and to perform such evaluations at various levels. The first application of this developing methodology was made to the Czochralski's crystal pulling process.

Previously, we had examined the reduction of quartzite to metallurgical grade silicon and did a comparative evaluation of competing Czochralski techniques for growing single crystal, cylindrical ingots. The next major process step in the sequence for producing single crystal silicon wafers, today and in the near future (up to 1982), is the slicing technique. The evaluations were started with the current methods of multiblade slurry slicing, and inner diameter slicing using a diamond coated blade for which a large amount of the needed information is available. Nevertheless, substantial gaps or uncertainties were found in important information required for both technical and economical evaluation of the currently practiced processes. In proceeding to the evaluation of processes which are still in the developmental or even conceptual stage, the gaps in needed information become very large. In these cases, it is necessary to fill the gaps more extensively with estimates based on extrapolations or analogies. Such estimates always leave some doubt on the accuracy of the evaluations, and it will be necessary to also make "probable error"

estimates to reduce decision mistakes based on early evaluations. Nevertheless, collecting the information and carrying our evaluations at the earliest possible time provides not only a planning tool, but also aids in uncovering the deciding attributes about which information ought to be obtained at an early stage of the development process.

We have tabulated production experience data obtained from Spectrolab⁽¹⁾ for slicing 2-cm rectangular, 5.4-cm and 7.5-cm diameter wafers using the Varian multi-blade slicing system, and similar data obtained from HAMCO⁽²⁾, for ID slicing of 10.16-cm diameter ingots using their equipment. Experimental data from OCLI⁽³⁾, Varian⁽⁴⁾ and TI⁽⁵⁾ for multiblade wafering, from OCLI⁽⁶⁾ and STC⁽⁷⁾ for ID slicing, and from JPL⁽⁸⁾ for the Yasunaga multi-wire slurry slicing system, were also tabulated. To complete the analysis, projections made by Varian⁽⁹⁾ for multiblade slicing, by STC for ID slicing⁽⁷⁾ by Crystal Systems⁽¹⁰⁾ for their fixed abrasive multi-wire system, and by Solarex⁽¹¹⁾ for the Yasunaga multi-wire slurry system were examined.

2. TECHNICAL DISCUSSION

A. BRIEF DESCRIPTIONS OF THE SLICING TECHNIQUES

1. Multiblade Slicing

The multiblade slurry sawing method is one of the two techniques used in current production slicing. In its present configuration 230-250 blades of 38-cm length of hardened 1095 steel are mounted and evenly spaced on a blade head that is, for slicing, reciprocated, at frequencies below 2 Hz (normally about 1.6 Hz), across the workpiece using approximately a 20-cm stroke. The abrasive slurry is pulsed sprayed or, at times, dripped onto the top surface of the workpiece and recirculated by a pump. The slurry is a SiC abrasive suspended in PC oil. It is normally used for one load before it is discarded. There are no practical ways, at present, to re-use the abrasive slurry for more than one load.

The current multiblade slicing machines can accept blade heads up to 18.5-cm wide. However, the number of blades in a blade head, and consequently, the number of slices that could be produced per load, is not limited by the blade head width per se, but rather by the maximum tension force the blade head can exert on the blades. This is about 401,800 N for current production blade heads⁽⁴⁾. An adequate saw force commonly called "blade load", is necessary to achieve economically acceptable cutting rates in the slicing process. A blade load of about 1-2 N/blade⁽⁵⁾, is usually applied. Excessive blade loading, and even normal loading after some blade wear, can cause deflection of the blades, often called "buckling", which results in inaccurately sliced wafers or even broken

wafers. To minimize buckling, the blades need to be stressed as much as possible, which, in current practice, is 80% of the yield strength of 1095 steel, or 1.37 GPa⁽⁵⁾. Therefore, the maximum number of blades permitted per blade head is 401.8/1.37*A, where A is the cross-sectional blade area in mm^2 . For a 6.35 mm high blade, 0.20 mm thick, a size that is normally used in production⁽⁴⁾, the maximum number of blades thus is 230. Reducing the blade thickness to 0.15 mm will increase the maximum number of 6.35 mm high blades to 307. At present, the thicker 0.20 mm blades are used in production because of their better wafer yield, as they are less susceptible to buckling which can be caused by vertical misalignment at the beginning of the slicing process and by increased blade tension, resulting from reduced crossection because of blade wear near the end of slicing⁽⁵⁾.

There are two types of blade packages available: the drill-pin package and the epoxy package. In the former, the alternately arranged blades and spacers which determine the thicknesses of the kerf and wafers are held together by four threaded rods. It is the cheaper of the two types of package (\$50 compared to \$175), but often requires additional alignment before mounting on the slicing machine⁽³⁾. In the epoxy package, an adhesive is applied between the spacers and the blade ends to hold the package together⁽⁴⁾.

The production procedure for multi-blade slicing involves first mounting the workpiece, or silicon crystal, with wax, epoxy, or other suitable cement on a graphite or ceramic base plate. The workpiece is then clamped by the baseplate to the slicing machine. To help increase the

yield, ceramic bars are often similarly cemented longitudinally onto the cylindrical crystal near its top and bottom horizontal tangents. The bars "smooth-out" the slicing by decreasing the variation in kerf length and blade load as the blades travel downward through the cylindrical crystal. In addition, ceramic bars near the top tangent minimize the effect of vertical misalignment by reducing blade buckling by the time they enter the silicon crystal. Those bars near the bottom, help to smooth the transition of the blades cutting into the base material by equalizing the slicing properties above and below the crystal to base transition. Some of these benefits are also obtained, in some places, without the use of ceramic bars by varying the blade load according to the changing kerf length during the slicing process. After the slicing is finished, the wafers, still attached to the base, are removed from the slicing machine and the wafers are then detached from the base.

The effective linear cutting rate of the multiblade process is presently about 550 times smaller than the ID diamond saw. The linear cutting rate cannot be increased significantly because of the limit on the blade load and because of the blade head mass which limits the reciprocating frequency. The blade load cannot be increased much beyond its present value without significantly increasing blade buckling since the tensile strength of the blades is fixed. Varian found that a blade load of 2.77 N/ blade caused severe enough buckling to separate the crystal from its mount⁽⁴⁾. In another experiment, a reciprocating frequency increase to 2 Hz resulted in sufficient vibration to break all wafers⁽⁴⁾. Therefore, in order to increase the throughput rate, or the wafer area produced in the multi-blade slicing process per unit time, either the number of slices

in the load, or the area yield per load, has to be increased without significantly increasing the time of the run. The area output per load can be increased in a combination of several ways: by increasing the number of blades per unit blade head width, as can be achieved by decreasing the blade and/or spacer thickness; by increasing the width of the blade head without changing blade and spacer thicknesses; or by increasing the width of the workpiece.

The blade thickness has a lower bound set by its strength. If the blade is too thin, it will buckle under the blade load, or break from the blade tension, resulting in broken wafers and low yields. Reduction of the spacer thickness is limited by the wafer strength.

Slicing wafers too thin increases their chance of breakage due to pressure from the lateral blade movement, blade vibration, blade buckling, etc. As the blade and spacer thicknesses are decreased, the increased fragility of the blades and the wafers ultimately leads to significantly lowered yields. Experimentally, Varian⁽⁹⁾ has found that using 0.15 mm thick blades with 0.30 mm spacers still results in good yields. Under these conditions 0.25 mm thick wafers with 0.20 mm kerf are produced. This gives, assuming a wafer yield of 95%, which has been demonstrated by Varian, an area conversion ratio of 0.9 m²/kg-Si which is a 50% improvement over Spectrolab's recently experienced area conversion ratio in slicing 5.4-cm and 7.5-cm diameter wafers.

Varian is also currently experimenting with a larger blade head width that can accept 900 to 1000 blades. This blade head weighs approximately one ton. Therefore, the workpiece will be reciprocated against the stationary blades. The workpiece size is projected to be 12-cm in diameter and 40.5-cm long yielding a wafer area of 9.67 m²/load using the 900-blade machine with the aforementioned blade and spacer thicknesses. This area yield is over four times higher than obtained in present commercial practice. Details on the Varian 900-blade head slicing machine, as well as other slicing processes discussed in the report, are listed in Tables I-III, and in the "University of Pennsylvania Process Characterization" formats which are attached as an Appendix.

A third method to potentially increase the area yield per load without increasing the slicing time would be to increase the width of the workpiece, or the kerf length, by slicing two or more ingots, placed side-by-side, simultaneously. TI⁽⁵⁾ has found that the machine slicing time, and, correspondingly, the linear cutting rate, is essentially independent of the kerf length. TI has therefore proposed slicing two 12-cm diameter ingots at one time to increase the multi-blade slicing productivity. The area yield per load, with details of this projection given in Tables I to III, can thus be doubled without significantly changing the slicing time.

2. Inner Diameter Slicing

In the process of inner diameter, or ID, slicing, one wafer is sliced at a time with a rotating, diamond impregnated blade. The rotation speed depends upon the blade size, and is 2,100 rpm for a blade with a

15.25-cm diameter hole, and 1650 rpm for a 20.32-cm diameter, inner diameter blade. The blade consists of a stainless steel core which is 0.10 and 0.15 mm thick for 15.24 and 20.32-cm blades, respectively, with diamond plated edges. The total thickness of the 15.24-cm blade is approximately 0.30 mm, and the 20.32-cm blade is about 10% thicker. The blade is mounted around its rim in a vise-like holder where hydraulic pressure is applied to tension it radially.

The linear cutting rate, or the rate that the inner diameter blade traverses the silicon can be up to 305 cm/h, or almost three orders of magnitude higher than for the slurry, multi-blade process. There are several reasons for this. First, the inner diameter blade speed is approximately 1,600 cm/sec as opposed to less than 80 cm/sec for multiblade slicing. Therefore, the contact length per unit time between the blade and the silicon for ID slicing is twenty times higher than for multiblade slicing. Also, fixed abrasive slicing removes more kerf in a unit contact length because there are two surfaces moving relative to each other instead of three as in slurry slicing. In slurry slicing, the abrasive is pushed into the workpiece and is "rolled out". Whereas for fixed abrasive slicing, the abrasive cuts into the workpiece to remove the kerf. Finally, the diamond plated layer on the ID blade increases the blade's rigidity and thickness and allows the application of more force, by the blade, on the workpiece than in multiblade slicing. The total thickness of the ID blade is 300-330 um thick while the multiblade is 150-200 um thick. It should be noted that the effective ID cutting rate is about 10-20% lower than indicated by the blade's linear cutting rate because of the 18 to 24 seconds between two consecutive slices, when the blade is returning to its

original vertical position and the silicon crystal is being indexed.

In mounting the ingot, one end is attached to a graphite base with epoxy and the ingot is then placed in a box with rubber supports along it's length to keep it rigid. The stiffness of the mount will affect the vibration level between the blade and workpiece, influencing the wafer thickness and yield⁽³⁾. At present, ID machines can accommodate ingots up to 50-cm $\log^{(2,3)}$. The current practice of slicing 10.16-cm diameter wafers, 0.50 mm thick with a 0.33 mm kerf, yields a area of 4.8 $m^2/10$ ad or 0.50 m^2/kg , at a practical wafer yield of 98%. During slicing, either water or water mixed with a small percent of Rust-Lick is sprayed on the cutting edge, at a rate of about 2 m % sec, to cool the blade. The blade must be dressed, every 50 slices for the 15.24-cm blade and every 25 slices for the 20.32-cm blades for proper slicing, in order to remove dirt and expose a fresh cutting surface. The dressing is done with 5 cuts of an alumina stick. The lifetime of the blade is dependent on the rate of diamond "pull-out" and the degree of metal fatigue and varies quite extensively from blade-to-blade. The lifetime median is about 3,000 7.52-cm diameter slices for the 15.24-cm blade and 5,000 10.16-cm diameter slices for the 20.32-cm blade.

A method being investigated, to increase the ID saw's productivity by a factor of two, is crystal rotation⁽⁷⁾. The cutting speed is doubled using a rotating crystal since the blade has to traverse only half-way through the crystal diameter. The half penetration in rotating crystal slicing permits the use of a cheaper, smaller diameter, and thinner inner diameter blade. For slicing 10-cm diameter wafers with this technique the wafer thickness and kerf are expected to be 225 μ m and 210 μ m respectively⁽⁷⁾.

A UPPC format for slicing rotating 10-cm diameter crystals with the ID saw is attached to the Appendix. This process is expected to be in commercial use by 1982.

3. The Yasunaga YQ-100 Multiwire Saw System

The Yasunaga multiwire saw is a slurry slicing system which uses a single wire (600 to 30,000 m inlength) routed around a rocker arm tensioning device, a wire guide catridge, and a take-up reel. The continuous wire forms up to 250 multiple loops around the three grooved wire guides, arranged in an equilateral triangle, that are the key parts of the wire guide catridge. During slicing, the wire guide catridge oscillates, while the workpiece is raised against the wires with a preset force. An abrasive slurry is sprayed on the cutting surface. The procedure for mounting the silicon crystal for multiblade slicing is similar to that described for multiblade slicing.

The chief potential benefit of the Yasunaga saw is its high area-mass conversion ratio by employing closely-spaced, small diameter wires. The current YQ-100 model has a workpiece capacity of $10 \times 10 \times 10$ cm and as demonstrated by experiments,⁽⁸⁾ results of which are listed on a UPPC format attached in the Appendix, it can slice 215, 212 <u>+</u> 7 µm thick wafers with less than 200 µm kerf using 0.4 mm pitch guides, 0.16 mm diameter wire and 13 µm SiC abrasive. Under those conditions an area to unit mass ratio of 1.04 m²/kg is obtained, which is about 50% higher than what anyother current production or experimental slicing system achieves. This higher area to mass ratio effectively reduces the consumption of

single crystal silicon, to produce a given wafer area, by a third. It is projected that the Yasunaga saw can achieve an area-mass ratio of 1.42 m^2/kg by employing closer spaced pitch guides (0.3 mm), smaller diameter wire (0.08 mm) and a finer abrasive (5 μ m). This would yield a 200 μ m thick wafer with 100 μ m kerf⁽¹¹⁾.

It is believed that the narrow lapping band of the wires of the Yasunaga saw results in wafers with less subsurface damage than with other commercial slicing techniques⁽¹¹⁾, and this is being investigated⁽⁸⁾.

Currently, the Yasunaga saw is not used for the production of silicon wafers, at least not in the USA, although Solarex has recently obtained a machine for pilot line operation.

4. The Multiwire Fixed Abrasive Slicing Technique ("FAST")

This method is similar to multiblade slicing, except that the silicon is sliced with diamond-impregnated wires instead of steel blades and an abrasive slurry. In FAST, the diamond impregnated wires are mounted and evenly spaced, at a linear density expected to be up to 25 cm^{-1} , on a light weight frame that is reciprocated across a rocking workpiece⁽¹⁰⁾. The wires are coated with 22 to 45 µm diamonds imbedded in a metal matrix, and can be coated on their bottom halves only to reduce abrasive costs. Development is still proceeding towards finding an optimum wire composition, but it has been found that heat-hardened, tungsten core wire, diamond-impregnated, and nickel-plated, has a good lifetime, which means it could be used for about 10 loads before significantly losing its cutting ability⁽¹⁰⁾.

Crystal Systems has conducted most of their experiments pertaining to FAST, on a modified Varian 686 wafering machine. Consequently, the slicing potential of multiwire, fixed abrasive slicing has not been fully demonstrated. For example, workpiece size has been, for most of the experiments only 4 x 4 cm, and the reciprocating rate lower than required for optimum fixed-abrasive slicing. A slicing machine, built to Crystal Systems' specifications, have just been delivered to them and slicing with this machine has just been initiated. The new slicing machine has been designed to provide higher cutting rates and lower wafer and kerf thicknesses and operate with a much lighter blade carriage, at higher reciprocating frequencies, and reduced vibration than the Varian machine. It is expected that this multiwire, fixed abrasive slicing technique could have a cutting rate of 0.6 cm/h (twice the value previously achieved with good yields), with an area to mass ratio of $1.1 \text{ m}^2/\text{kg}$ by producing wafers 200 µm thick with a 200 µm kerf.

The add-on prices for "FAST", detailed in one of the UPPC formats attached to the Appendix, have been projected for 1986 since the state of development of the system and the comparatively small base of experimental data available, making it unlikely that this slicing technique could be in significant commercial operation by 1982.

B. TABULATION OF OPERATION, LABOR, MATERIAL AND COST DATA

Tables I to III summarize the data provided by various organizations for the slicing techniques that are being used or developed. Included in these tables are production experience data from Spectrolab⁽¹⁾ for multi-

TABLE IN

SLICING OPERATION DATA FOR MULTIBLADE WAFERING

2. No. 10a 3. Sli	ices/load fer thickness	2 cm Rectangular 8 x 17 cm not appli- cable 1750 (2x2 cm) 0.35/0.45 cut 0.2/0.3	5.4 cm Diameter 16 cm long 3 750	7.5 cm Diameter 16 cm long 2	10.16 cm Diameter 15 cm long 1	no P-005) 10cm Diameter 11.7 cm long	(Projection) 10cm Diameter 13.5 cm long	projection) 12cm Diameter 40.5 cm long	<pre>incl. Projection l2cm Diameter 2,13 cm long</pre>
2. No. 10a 3. Sli 4. Waf	. of workpieces/ ad ices/load fer thickness m)	not appli- cable 1750 (2x2 cm) 0.35/0.45 cut	3	2		11.7 cm long	13.5 cm long	40.5 cm long	2.13 cm long
loa 3. Sli 4. Waf	ad icss/load fer thickness a)	cable 1750 (2x2 cm) 0.35/0.45 cut			1		l l		ingots
4. Waf	fer thickness m)	cm) 0.35/0.45 cut	750			1	1	1	2
	m)	cut		500	230	234	300	900	460
	rf thickness	etched	0.4 cut 0.3 etched	0.4 cut 0.3 etched	0.33 ± 0.03	0.29 <u>+</u> 0.04	0.25 <u>+</u> 0.015	0.25	0.32
5. Kez	a) (a	0 275	0.275	0.275	0.33	0.22	0.2	02	0.24
6. Pra	actical Wafer eld	0.95	0.95	0.95	0 84	0.83	0.95	0.95	1.00
inc	action Silicon corporated in fer	0.53/0.59	0.56	0.56	0.42	0.47	0.53	0.53	0.57
	pth of Subsur- ce damage ()跏)	75	75	75	n.a.	10-15	10-15	л.а.	10 severe 33 slight
9. Abr	rasive	600 grit SiC	600 grit SiC	600 grit siC	400 grit SiC	600 grit SiC	600 grit SiC	600 grit SiC	600 grit SiC
10. Vet	hicle	PC oil	PC oil	PC oil	PC oll	PC oil	PC 011	PC oil	PC oil
	ncentration g/ 9	0.24	024	0.24	0.8	0.36	0 36	0.36	0.24
12. Flo	.ow rate (L/h)	low	low	low	n.a.	n.a.	n.a.	n.a.	18
13. Tyr	pe of Blade	1095 steel 0.2 mm thick	1095 steel 0 2 mm thick	1095 steel 0.2 mn thick	1095 steel 0.2 mm thick	1095 steel 0.15 mm thick	1095 steel 0.15 mm thick	1095 steel 0.15 mn thick	1095 steel 0.20 nm thick
14. Bla	ade dimensions	n.a,	n.a.	n.a.	6.35 mm high - 0.46 mm spacers	6.35 mm high 0.35 mm spacers	6.35 mm high 0.30 mm spacers	6.35 mm high 0 30 mm spacers	6.35 mm high 0.36 mm spacers
	ount on chine	250 blade drill pin pack	250 blade drill pin pack	250 blade drill pin pack	230 blade epoxy package	300 blade package	300 blade package	900 blade package	230 blade package
for	o. of runs be- pre blade lange	7	2	1	1.5	1	1	2	1
(m ²	· 1	0.69	1.63	2.10	1.57	1.53	2.24	9.67	5.20
(m ²	ea yield 7/kg)	0 65/0 56	0 60	0 60	0 54	0.71	0-90	_0.90_	Q. 76
rat	fective cutting te (cm/h)	0.36	0 25	0.34	0.5	0 31	0.34	0.41	0.66
seg	gment/load (h)	5.5	22	22	20.5	32.0	29.5	29.5	18.2
(h/	ad/Unload time /load)	0.25	0.25	0.25	0.45	0.5(p)	0.5	0.5	0.5
cha ser	ange, machine arvice (h/load)	0.2	05	10	0 67	0.5(p)	0.5	0.5	06
tin	chine segment me (h/load)	5 95	22 75	23.25	21.6	33 0	30.5	30.5	20.0
	chine product- rity (m ² /h)	0.115	0 071	0 090	0 07	0 046	0.074	0 317	0.24

OF POOR QUALITY

TABLE IB

-

SLICING OPERATION DATA FOR MULTIWIRE AND INNER DIAMETER WAFERING

	1	Multr	<u>1</u> 1	nner Diameter Slig	ring			
Organization		<u>Crystal Systems</u> Fixed Abrasive Method (projection)	<u>Yasunaga Y</u> (Experimental) 7.6 cm diameter		OCL: (Experimental) 7.6 cm diameter	[(1.xperimental) 10.16 cm djameter	<u>HAMBO</u> (Production exp.) 10.15 cm diameter	
1.	Workpiece size	30x10x10 cm	10 cm long	10 cm long	50 cm long	25 mm long	45 cm long	
	No. of workpieces/ load	1	۲1	1	l	1	1	
3	Slices/load	250	215	333	725	350	555	
4.	Wafer thickness (num)	0.1	0.21 <u>+</u> 0.01	0.2	0 36 <u>+</u> 0.02	0.36 <u>+</u> 0.02	0.50	
5.	Kerf thickness (mm)	0.3	0 2	0.1	0.33	0.35	0.33	
6.	Practical Wafer Yield	1.00	1.00	1.00	0.95	1.00	0.98	
7.	Fraction Silicon Incorporated in Wafer	0.25	0.51	0.67	0.50	0.51	0.59	
8.	Depth of Surface damage (µm)	Fissures ex- tend 3 µm	~15	~65	n.a.	n.a.	n.a.	
9.	Abrasive	none	GC 1200 (13 µm)	5 µm SiC	none	none	none	
10.	Vehicle or coolant	l:l water: ethylene glycol	lapping oil	n.a.	80.1 water: rust lıck	80:1 water: rust lick	water	
11.	Concentration (kg/l)	-	~1.5	n.a.	-		-	
12.	Flow rate (L/h)	na.	3600	3600	7.2	8.4	n.a.	
13	Type of blade or wire	W1 plated, tungsten wire, diamond im- pregnated	Steel wire	Steel wire	Model STC-16 ID blade, diamond plated	Model STC-22, ID blade, dlamond plated	IP blade diamonđ plated	
14.	Blade or wire dimensions	0 125 mm core 0.25 mm total diameter 45 μm diamonds	0 16 mm dia- meter 0.4 mm pitch guides	0.08 mm diameter, 0.3 mm pitch guides	42 23 cm OD 15.24 cm ID 0.10 mm thick core, 0.28-0.30 total thickness	55.88 cm OD, 20.32 cm ID, 0.15 nm thick core, 0.33- 0.36 total thickness	n.a.	
15	Amount on machine	250 wire blade package	~17,000 m	~35,000 m	1	1	1	
16.	No. of loads before blade change	9	3	3	_ 4.1	14.3	1	
17	Wafer area/load (m ²)	7.50	0.98	2.62	3.14	2.84	4.41	
18.	Area yield (m ² /kg)	1.1	1.04	1.42	0.59	0.60	0.505	
19	Effective cut- ting rate (cm/h)	0.6	0.84	0.3	305	305	305	
20.	Slicing time segment/load (h)	16.67	9.0	30.0	23.9	14.7	23.12	
21.	Load/Unload time (h/load)	1,33	n.a.	n.a.	1.23	0.735	0.083	
22	Cutting tool change, machine service (h/load)	na.	na	na	1.02	0.84	0.33	
23	Machine segment time (h/lond)	18.0	10.0(e)	3 1(e)	26.2	16.3	23 5	
24	Nachine product- ivity (m ² /h)	0 42	0 098	0.085	0.126	0.176	0.19	

•

blade slicing and from HAMCO ⁽²⁾ for ID slicing, and experimental results for multiblade slicing, from $OCLI^{(6)}$, $Varian^{(4)}$ and $TI^{(5)}$ for multi slicing from JPL⁽⁸⁾ and ID slicing from $OCLI^{(6)}$. In addition, projections made by Varian for multiblade slicing⁽⁹⁾, by Crystal Systems⁽¹⁰⁾ for their "FAST" method, and by Solarex⁽¹¹⁾ for the Yasunaga saw are included. In the Appendix, UPPC formats containing the details of the information obtained, are shown for these principle applications or projections for the slicing techniques.

The operation data for multiblade slicing are listed in Table IA, while Table IB contains the corresponding data for the fixed abrasive and slurry multiwire and the inner diameter slicing processes. These tables contain the process attribute of slicing which are summarized on Figure 1. The first two lines of Table I are the dimensions of the workpiece and the number of workpieces per load, the product of which is the slicing machine's capacity. The wafer area produced in a load is related to the workpiece capacity through the wafer and kerf thicknesses and practical wafer yield. This wafer area per load (Table I, line 17) can also be calculated as the product of the theoretical number of slices cut per load (Table I, line 3), the "practical wafer yield" (Table I, line 5), and the area of the single wafers. The "practical wafer yield" fraction is the number of acceptable wafers divided by the theoretical number sliced per load. The wafer area per unit mass (Table I, line 18) is calculated by dividing the practical wafer yield by the product of the sum of the wafer and kerf thicknesses (Table I, lines 4 and 5) and the density of silicon, or

PROCESS ATTRIBUTES

.

WORKPIECE SIZE AND NUMBER/LOAD

WAFER THICKNESS

KERF THICKNESS

PRACTICAL YIELD

(DEPTH OF DAMAGE)

EFFECTIVE CUTTING RATE LOAD/UNLOAD TIME (INCL. TOOL CHANGE) MACHINE PRODUCTIVITY MACHINE AVAILABILITY

Figure 1.

$$1.18 = \frac{10 * 1.6}{(1.4 + 1.5) * 2.34} m^2/kg,$$

where I.n represents the value from Table I, line n.

The wafer thickness, kerf and practical wafer yield are necessary for finding the division of the input silicon crystal or workpiece into the silicon incorporated in the work-in-process wafer (Table I, line 7) and that silicon lost in kerf and broken wafers.

The procedures for determining the subsurface damage depths, listed in line 8 of Table I, were not consistent between organizations. The most accurate method for determining subsurface damage depth is to remove wafer surface material until the cell efficiency becomes independent of any further removal. Spectrolab's values reflect this procedure⁽¹⁾. The other subsurface damage depths were determined by chemical etching to remove surface material followed by Wright etching to reveal defects⁽⁴⁾, by etching and x-ray topography⁽⁵⁾, and by angle lapping and Sirtl etching⁽⁸⁾.

Indirect material requirements, briefly summarized on Figure 2, in terms of the abrasive and vehicle, or coolant type, the slurry concentration and its flow rate or that of the coolant, are listed in lines 9-12 of Table I. Lines 13-16 describe the expendible tooling requirements such as the type of blade or wire, its dimensions, the size of the blade patk and its life expectancy. These data are necessary for determining the expendible tooling and material costs.

The effective cutting rate (Table I, line 19) is defined here as the workpiece diameter divided by the slicing time segment, which is the

time the machine is actually sawing (Table I, line 20). The time periods when the machine is not actually slicing and cannot be used for slicing because of preparatory or service operations, are listed in lines 21 and 22. The sum of these lines and the slicing time segment is the machine segment time (Table I, line 23), or the average time needed for slicing a load, including loading, unloading and servicing. The machine segment time is needed for calculating the number of loads processed annually, and the machine productivity (Table 1, line 24) which is the wafer area sliced in a load divided by the machine segment time.

The requirements per machine load for labor, included that needed for service and repair, for indirect material needs, including electricity consumption, for capital expenses, which consists of machine and facility components, are included in Tables IIA and IIB. These data form the basis for calculating of the manufacturing cost components of labor, expendable tooling, indirect materials, and capital. Also listed in these tables are values necessary for calculating direct material or silicon costs: the proportion of silicon lost in grinding the cylindrical ingots to a uniform diameter, the unit mass of silicon incorporated in the wafer and that lost in kerf and broken wafers.

The labor times required for each part of the crystal slicing operation (see Fig. 2), that is crystal mounting, machine loading and machine monitoring are listed in lines 1-3 of Table II, with their total on line 4. The service labor time, which includes changing the blades or wires, is listed in line 5.

Table IIA

SLICING LABOR AND MATERIAL ANALYSIS FOR MULTINLAUE SLICING

	SDICING LABOR AND INTERIAL AUGUSTS FOR HULTINLADE SLICING										
	Organization	(Þ 2 cm Rectangular	<u>Bpectrola</u> roduction Exp 5.4 cm Diameter		OCL1 (Experimental) 10 16 cm Diameter	(Fxperiment no. P~005) lOcm Diameter		(900 blade projection) 12cm Diameter	<u>Ti</u> (Experimental incl. Projection) 12cm Diameter		
1	. Crystal Mount time (h/load)	0.5	0.25	0,25	0.25	0.27	n.a.	п.а.	1.0		
2	Machine load- unload labor (h/load)	0.25	0.25	0 25	0.45	0.4	0.67	0.67	n.a.		
	Machine super- vision during slucing (h/load)	0 58	5 1	52	0.45	0.67	0.67	1.60	0.07		
	Total direct labor time (h/load) (excluding main- tenance)	1 33	5.6	5.7	1.15	1.33	1.33	2.27	1.07		
	Cutting tool change, machine service labor (h/load)	04	14	1.4	0.87	0 67	0.67	0.67	0.6		
	Blade or wire set cost (\$) Vehicle or	~50	~50	~50	175	~50	23.50	39.45	6.90		
	coolant con- sumption (1/load)	7.6	7.6	7.6	6.8	7.6	7.6	15.0	n.a.		
	abrasive con- sumed (kg/load)	1.8	1.8	1.8	5.45	2.74	2.74	5.4	n.a.		
	Power require- ments (k W/machine)	1	1	1	1	1	0.75	1.67	ı		
	Energy con- sumption (kWh/load)	5.5	22	22	20.5	32	22	49.3	18.2		
	Machine avail- ability (%) Potential no.	90	90	90	90	90	90	90	90		
	of runs in a year (8280 h work year)	1250	325	320	345	225	245	245	370		
13	Machine cost		{			{					
14	chine cost	20,000	20,000	20,000	20,000	20,000	20,000	30,000	30,000		
15.	(\$/year) Allocatable building	4,280	4,280	4,280	4,280	4,280	4,280	6,420	6,420		
16.	area (m ² / machine) Allocatable building	11.2	11.2	11.2	11.2	11.2	11.2	11.2	11.2		
17	cost (\$/ machine} Annual	8,400	8,400	8,400	8,400	8,400	8,400	8,400	8,400		
	building cost (\$/y)	980	980	980	980	980	980	980	980		
18	Fraction of silicon lost in grinding ingots (%) (100 x(0.6/d))		11.1	8.0	5.9	6.0	50	5 0	5.0		
19	Silicon in- corporated into wafer (kg/m ² -wafer)	0.81/1 05	0.94	0.94	0.77	0.58	0 59	0.59	0.75		
20.	Kerf and broken wafer loss (kg/m ² - wafer)	0.68/0 73	0.73	0.73	1.07	0.76	0.52	0 52	0.56		

OF POOR QUALITY

TABLE IIB

SLICING LABOR AND MATERIAL ANALYSIS FOR MULTIWIRE AND INNER DIAMETER WAFERING

	SLICING LABOR AND MATERIAL ANALYSIS FOR MULTIWIRE AND INNER DIAMETER WAFERING											
Į		<u>Mu</u> 1	tiwire Wafering		Inner Diameter Slicing							
Organization		Crystal Systems Fixed Abrasive Method (Projection)	Yasunaga (Experimental) 7.6 cm diameter	<u>YO-100</u> (Projection) 10 cm diameter	(Experimental) 7.6 cm diameter	LI (Experimental) 10.16 cm diameter	HAMCO (Production exp.) 10.16 cm diameter					
1	Crystal Mount time (h/load) n.a.		n.a.	n.a.	0 41	0.23	0.25					
	Machine load- unload labor (h/load)	n.a.	na	n.a.	1 015	0.525	0、083					
3.	Nachine super- vision during slicing (h/load)	0,92	0.33(e)	l (e)	0.298	0.23	4.3					
4.	fotal direct labor time (h/load) (excluding main-	-										
	tence) Cutzing tool	1.75(e)	083(e)	1.5(e)	1.72	0.985	4.63					
	change, machine service labor (h/load)	0.5(e)	0.5(e)	0.5(e)	1.015	0.875	0.8					
6	Blade or wire set cost (\$) Vehicle or	82	~97	143.50	60	150	55					
	coolant con- sumption (l/load) Amount of	n.a.	3 kg (~3.25l)	n.a.	5.1	1.75	0					
9	abrasive con- sumed (kg/load)	0	5	n.a.	0	0	0					
	Power require- ments (kW/machine)	, 1.5	0.6	0.6	2 (e)	² (ç)	2 (e)					
10.	Energy con- sumption (kWh/load)	25	5.4	18	47.8	29.4	46.2					
11.	Machine avail- ability (%)	90 (e)	90 (e)	90 (e)	95	95	95					
12.	Potential no. of runs in a year (8280 h work year)	415	745	240	300	480	325					
13.	Machine cost (\$)	30,000	30,000	30,000	40,000	40,000	40,000					
	Annual ma- chine cost (\$/y)	6,420	6,420	6,420	8,560	8,560	8,560					
	Allocatable building area (m ² / machine)	11.2	8	8	18	18	18					
	Allocatable building cost (\$/ machine)	8,400	6,000	6,000	13,500	13,500	13,500					
	Annual building cost (S/y)	980	700	700	1,580	1,580	1,580					
18. 19	Fraction of silicon lost in grinding ingots (%) (100 x(0.6/d)) Silicon in- corporated	6.0(e)	8 0	60	8.0	6.0	6.0					
20	into wafer (kg/m ² -wafer) Kerf and	0.23	0.49	0.46	0,84	0.84	1,17					
	broken wafer loss (kg/m ² - wafer)	0.70	0 47	0 23	0.86	0.82	0.81					

Expendable tooling and indirect material requirements, in terms of the blade or wire set costs and the quantities of vehicle or coolant and abrasive consumed during a run, are listed in lines 6=8 of Table II. The electrical consumption for a run (Table II, line 10) is considered as an indirect material and is obtained by multiplying the slicer's power requirements by the slicing time segment (Table I, line 20).

In order to calculate the potential number of loads that can be sliced annually, shown in line 12, the machine segment time (Table I, line 23) is divided into 8280. This last value, 8280, is taken from $SAMICS^{(12)}$ and is the number of annual hours the wafer slicing plant operates. The plant operation schedule is continuous except for one 1-week vacation, two 4-day weekends, and one 3-day weekend, and was chosen to maximize annual production by minimizing slicer shutdowns during a run due to plant closings.

After dealing with expenses, the sum of the machine and facility costs, or the capital cost portion of the manufacturing costs needs to be considered. The capital costs are dependent on the factors listed on Figure 3. The annual machine cost (Table II, line 14) is the product of the initial cost of the slicing machine, including installation, taken from the data sources, and the standardized charge rate of 0.2135 y^{-1} . This charge rate was taken from SAMICS⁽¹²⁾, using a depreciation schedule of 7 years, a state tax of 2% on one-half the capital, a 4% insurance premium, and a 12% interest-on-debt rate on one-twelfth the initial capital cost. The low ratio of dept to capital, or the low financial leverage, is due to the postulate that the photovoltaic industry would be

LABOR AND INDIRECT MATERIALS

LABOR TIMES: ATTACH SUPPORT BLOCK TO INGOT MACHINE LOAD/UNLOAD MACHINE MONITORING TOOL CHANGE/MACHINE SERVICING

INDIRECT MATERIAL COSTS: SLURRY (COOLANT) TYPE UNIT COST USAGE TOOL (BLADE) TYPE COST LIFE MACHINE REPLACEMENT PARTS PURCHASED MACHINE SERVICING MISC. (MOUNTING BLOCKS, ADHESIVE) ENERGY

CAPITAL COSTS

-

MACHINE COST

(MACHINE LIFE)

ALLOCATABLE BUILDING AREA

(SPECIAL SERVICES)

Figure 3.

unable to raise large amounts of debt capital, without large interest rates, because it will be a rapidly evolving industry with appreciable risks⁽¹²⁾.

The second capital cost contribution comes from the building. The allocatible building area, shown in line 15 of Table II, was taken, according to $SAMICS^{(12)}$, as twice the machine's operating area. The doubling accounts for indirect and overhead space needed e.g., for functions such as maintenance, administration and receiving/inventorying, as well as for aisles, washrooms, etc. The initial building cost (Table II, line 16) is taken as $1506.95/m^2$, according to SAMICS⁽¹²⁾, and is based on the machine operating area only. This cost figure includes appropriate cost allocations for the additional building space needed as outlined above. The facilities charge rate used to calculate the annual building cost (Table II, line 17), from the initial cost, is 0.117 y^{-1} . This value was obtained in the same fashion as the equipment charge rate, except that a 40-year life expectancy is employed for determining the depreciation rate of the building. Also a 31% surcharge on the annual cost of capital is included, in the 0.117 y^{-1} factor, to account for special services which are the "indirect" utility consumption, that is for heating, air-conditioning, lighting, etc. for the building.

To properly calculate the direct material cost, that is the cost of the cylindrical slicing ingot, the amount of the silicon crystal lost in grinding is necessary. The grinding of the cylindrical ingots to a uniform outside diameter, previous to slicing, facilitates the slicing operation, as well as tooling and handling of the sliced wafers in subsequent device fabrication procedures. In calculating the mass fraction of silicon lost in grinding, shown in line 18 of Table II, the average diameter

loss is assumed to be 0.6 cm. With this diameter loss, and the consequent loss of mass, the price per unit mass of silicon entering into the slicing operation can be determined. Since the grinding diameter loss stays constant with crystal diameter, the fraction of lost silicon is inversely proportional to the diameter of the crystal.

The difference between the add-on processing cost and the work-inprocess cost is the cost of the direct material contained in the wafers. The latter value for a unit area can be obtained by multiplying line 19 of Table II by the unit mass silicon cost. To obtain the amount of silicon contained in a unit wafer area, the incorporated silicon fraction is divided by the wafer area per unit mass (Table I, line 18). The incorporated wafer fraction is the product of the yield fraction (taken from Table I, line 6) and wafer thickness (Table I, line 4) divided by the sum of the wafer and kerf thicknesses. In equation form, the fraction of silicon contained in the wafer is,

II.19 =
$$\frac{1.6 \times 1.4}{(1.4 + 1.5) \times 1.18} \frac{kg}{m^2}$$

with the roman numerials representing the table numbers and the arabic numbers, the line numbers for that table. The kerf and broken wafer loss, necessary for differentiating the operating add-on cost from the specific add-on cost, is calculated in a similar fashion to line 19 of Table II, except that the kerf loss is represented by the kerf thickness and the broken wafer loss by the broken wafer fraction multiplied by the wafer thickness. Therefore

II.20 =
$$\frac{(I.5 + (1 - I.6) * I.4)}{(I.4 + I.5) * I.18} \frac{\text{kg}}{\text{m}^2}$$

From the operation data and expenses, listed in the first two tables, the add-on components of the slicing manufacturing slicing cost can be calculated. For the most part, the add-on cost components, shown in Table III, on a per unit area basis, are derived from the data of the proceeding tables using the relationships given in that table. The exceptions include the unit costs of the indirect materials which were taken from the sources footnoted in Table III. In addition, the purchased service cost for multiblade slicing (Table III, line 4), which includes the cost of machine maintenance and overhaul performed on the outside or under contract, used was \$1529.3 y⁻¹ and was obtained from Spectrolab⁽¹⁾. HAMCO⁽²⁾ supplied the purchased service cost for an inner diameter slicing as \$285.7 y⁻¹. The total material cost which is the sum of the first four lines of Table III was increased by 5.26%, in accordance to SAMICS charge factors⁽¹²⁾, to account for handling and other miscellaneous expenses.

The labor costs were calculated using the labor times, listed in Table II and the labor rates shown in the Cost Account Catalog of the SAMICS Support Study⁽¹³⁾. For calculating the direct labor costs which involve crystal mounting, machine loading and supervision the wages paid an electronics semiconductor assembler, whose duties are described under SAMICS' occupation classification no. 726884 and wages under catalog no. B3096D⁽¹³⁾ were employed. The maintenance labor rate of a maintenance mechanic II (occupation classification no. 726884, catalog no. B3736D) was used to find the labor cost of internal machine service and cutting tool charges. The listed labor rates were multiplied by 1.432 to take into consideration fringe benefits, such as vacations, medical health plans, social security benefits, etc, and miscellaneous expenses. A surcharge of 25% was added to the direct

TABLE IIIA

ADD-ON COST COMPONENTS FOR HULTIBLADE BLICING (8/#2)

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			<u>AD0-0</u>	N COST COMPON	ENTS FOR MULTIPLY		<u></u>		1
	Organization	2 cm Rectangular	Spectrolat (Production Expo 5 4 cm Diameter		<u>OCti</u> (Experimental) 10 16 cm Diameter	(Experiment no P-005) locm Diameter	<u>Varian</u> (Projection) 10cm Diameter	(900 blade projection) 12cm Diameter	TI (Experimental) incl Projection) 12cm Diameter
2	Expendible tooling (11A 6 # JA~16* IA 17) Haterials Electrical	10,35 21.15 (m)	15 34 8 95 (a)	23 81 6.95 (m)	74 31 16 35 (b)	32 68 7.50 (c)	10 49 3 40 (c)	2 04 3.85 (c)	1.)] 0 30 (d)
	energy cost (\$0 032 *11A.10 * IA 17)	0 25	0.43	0 33	0.42	D 67	0 32	0.16	0 12
1	Roplacement parts 5 pur- chased service	1 65	3 01	2.37	2.94	4.62	2 90	0 67	0 83
5	lotal material costs (1.0526* {1 +2 +3 +4 })	35 37	29 19	35 22	98 96	47.86	18 01	7.07	2 70
6	Direct Labor (S5 58*11A 4 ± 1A.17)	10.75	19.16	15.14	4.08	4 85	3 31	1.31	1 15
]	Maintenance labor (\$ 8.12* IIA 4 3 IA.17)	4 71	6,98	5 42	4 50	3.55	2 43	0 56	0.94
8	Other indirect labor (25% of 6 + 7)	3 86	6 53	5 14	2 15	2 10	1 44	0 46	0 52
9	Tota, labor (6 + 7 + 8)	19 32	32 67	25 70	10 73	10.50	7 10	2.33	2 61
10	Equipment cost (IIA 14 - IIA.12 * IA.17}	4.96	8 08	6.37	7 90	12.43	7,80	2 71	2.23
11	Facilities cost (IIA 17 % IIA 12 *IA 17)	1 14	1.05	1.46	181	2 85	1 79	0.41	0 34
12	Capital Cost (10 + 11)	6.10	9.93	7.83	0.71	15.28	9.59	4 50	2.56
	Overhead (0 059 * (10.) + 0 168 * 01))	0 42	0 68	0 53	0 66	1.04	0 65	0 20	0-17
14.	Return on equity (0 192*(5.) + 0 192*(9.)+ 1.22 + (10) + 4 73*(11.)	21 94	30,49	26.37	39.26	39.85	22.62	7 05	5.34
15	Add-on price (Si price assumed zero)								
	5 +9 +12 +13. +14 }	03.15	102.70	95.33	159.25	114.29	58,10	21.15	13,34
			Silicon	Ingot Price (U	inground) \$ \$139	15/kg (1978 est	imation)		
16	uld-on cost of grinding (\$/kg)	-	20.97	13,99	9.77	9.96	9.96	8,07	8 07
17	Cost of ground Si (\$/kg)	-	160.12 116.89	153.14	148.92 158.80	149.11 113.21	149.11 78.05	147.22	147.22 82.68
18 19	Lost Silicon Add-on price		219,59	207.31	318,14	227.50	136 15	98.20	96.02
	Price	-	368.50	349.73	433.15	328.6B	223 61	184.32	206,93
		'	Silico	n Ingot Price	(Unground) P \$65	98/kg (1982 pr	ojection		
	Add-on cost of grinding (\$/kg)	-	12.84	8,13	5,45	5.56	5 56	4.41	4.41
1	Cost of ground Si (\$/kg)	-	78.82	74.11	71,43	71.55	71.55	70.39	70,39
	Lost 51		57.54	54.10	76,43	53.66	37.21 95.31	36.61 57.75	39,43 52,87
1	Add-on price Price (\$/m ² }	-	160 24 233.83	149.43 219.00	235.68 290 83	167.95 216.50	137 17	98 94	105 58
\vdash		<u>├</u>		Ingot Price	1	46/kg (1986 pro	jection)		
26.	Add-on cost of grinding (\$/kg)	-	8,23	4.01	3,09	3.07	3.07	2.34	2.34
27	Cost of ground Si (\$/kg)	-	32 69	29.27	27,46	27.53	27.53	26.80	26.80
28	Lost Silicon	•	23.06	21.37	29.38	20.65	14.32	13.94	15.05
29 30	Add-on Price Price		126.56 157.16	116.90 144.30	168.63 209.83	134.94 153.62	72.42 88.53	35.09	28,39 48,46
Ľ		<u> </u>	L					1	1

(a) Calculated using \$7/gallon for the slurry mixture and including \$0.60/load for the ceramic bass and bars.

inclusing \$0.50/10ad for the cerebic biss and bers.
(b) H I Yoo, "Asserment of Present State of the Art Sawing Technology," OCLL DOE/JPL 954830-77/12, p 34 (12/77)
(c) \$ C Holden and JR Flexing, "Slicing of Silicon into Sheet Material" Varian Asnoclates, ERDA/JL 954374-77/2, p 22 (7/77)
(d) Samuel N Rea and Faul S Gloim, "Large Area Czochralski Silicon," Toxas Instruments, ERDA/JL-954475-76/2 p 17, (9/76)

TABLE IIIB

ADD-ON COST COMPONENTS FOR MULTIWIKI AND INNER DIAMETER SLICING (\$/m2)

1	The state of the s									
	Multiplan unforter									
ł		Crystal Systems	tiwire Wafering Yasunar	<u>a vo-100</u>	CLI HARD					
		Fixed Abrasive	(Experimental)	(Projection)	(Experimental)	(Experimental)	(Production exp.)			
	Organization	Method (projection)	7.6 cm diameter	10 cm diameter	7.6 cm	10 16 cm	10 16 cm			
ļ		(Frejesseen)	uluaetei		diameter	diameter	diameter			
1	Expendible tooling (IIB.6 7 18.16 *1817)	1.25	33	18 25	4.65	3.70	12,45			
2.	-IBI7) Materials	0.30 (a)	32.95 (b)	41.05 (d)	2,65 (e)	2.05 (c)	12:45 1 85 (f)			
з.	Electrical energy cost (\$0.0319* 18.10 + T B.17)	0.11	0.18	0.22	0.49	0.33	0.33			
4.	Replacement parts and			[0.33			
	purchased service	n.a.	n.a.	n.a.	0 30 (g)	0 21 (g)	0.20 (g)			
r :	Total materials 1.0526*(1 + 2, + 3, +4.))	1 74	69.61	62.65	8 52	4 52	13.54			
6.	Direct labor (\$5.58*118 4 + 18.17)	1,30	4.72	3.19	3.05	1.93	13.51			
	Haintenance labor(\$8.12*IIB.5 ÷ 1B.17)	0.54	4.14	1.55	2.63	2.50	5.85			
8	Other indirect labor				*****	2.50	1.47			
	(25% of (6 + 7.))	0.45	2.22	1.19	1.42	1.11	183			
9	Total labor (6. + 7. + 8)	2.30	11 08	5 93	7.10	6.54	9.15			
10.	Equipment cost (IIB.14 - 118.12 IS.17)	2.06	8.79	10 21	9.09	6.28	5.97			
11.	Facilities cost (IIb.17 ÷IIB.12 13,17)	0.32	0.96	1 12	1.67	1 15	1.10			
12.	Capital Cost (10 + 11.)	2.38	9.75	11.33	10 76	7 43	7.07			
13.	Overhead (0.059* (10.) +		1							
	0.108 *(11.)) Return on equity	0.16	0.57	0.66	0.72	0.49	0.471			
14	(0.192*		1							
	(5.)+0.192*(9.) + 1.22* (10.) + 4.73*(11.))	4.80	30.57	30.92	21,99	15.22	16.84			
15.	Add-on price (Si price									
1	assumed zero) (5. +9. +12.									
	+13. +14.)		1		ł					
		11.38	121.57	111.62	49.06	36.29	47.04			
		Silicon	Ingot Price (Un	ground) @ \$139 15	/kg (1978 estimation	1)	k			
16.	Add-on cost of grinding	•••					r			
I I	(\$/kg)	9.94	13.77	9.96	13.77	9.77	9.77			
11.	Cost of ground silicon (\$/kg)	149.09	152.92	149.11	152.92	148.92	148.92			
18.	Lost Silicon (\$/m ²)	104.66	71.57	34.30	131.09	122.17	120.96			
	Add on price (\$/m ²)	116.04	193.14	145 92	180.15	158.46	168.00			
	Price (\$/m ²)	150.93	268 45	215.70	309.02	280.48	342.31			
		Silicon	Ingot Price (Ung	round) @ \$65.98/k	g (1982 projection)					
21.	Add on cost of grinding									
	(\$/kg)	5.55	7.99	5 56	7.99	5.45	5.45			
	Cost of ground Si (\$/kg)	71.53	73.97	71 55	73.97	21 43				
	Lost Si	50.21	34.03	16.46		71.43	71 43			
1	Add-on price	61.59		128.08	62.87	58.57	57.99			
	Price (\$/m ²)	78.33	155.60 192.03	128.08	111.93	94.86	104.83			
			192103		174 24	155.03	188.40			
		Silicon	Ingot Price (Un	ground) @ \$24.46/	kg (1986 projection	.)				
	Add-on cost of			1	1					
	grinding (\$/kg)	3.06	4.71	3.07	4.71	3.00	3.00			
	Cost of ground 51 (\$/kg)	27 52			1					
	Lost Si	27.52 19.32	29 17	27.53	29.17	27.46	27.46			
29.1	Add-on Price	30 70	13.42	6.33	24.79	22.52	22.29			
		20.00	134.99	117.95	73.85	58.80	69.33			
- 1	Price	37.14	149.16	130.83	94,65		03.33			

(a) F. Schmid and C.P. Khattack, "Heat Exchanger-Ingot Casting/Slicing Process" Crystal Systems, ERDA/JPL 954373-77/3, pp 78-79 (10/77).
 (b) Calculated using \$12.10/kg^(C) for the abrasive and \$1.25/2^(C) for the PC oil and assuming the slurry is used twice.

(c) LSSA Project Report, "Multiwire Slurry Wafering Demonstrations," Jet Propulsion Laboratory, DOE/JPL-1012-7817, (2/78).

(d) Estimated from materials cost of Yasunaga's 7.6 cm diameter ingot

(e) H.I. Yoo, "Assessment of Present State-of-the-Art Sawing Technology," OCLI, DOE/JPL 954830-77/12, p. 38 (12/77)

(f) Estimated from OCLI's material cost data

1 1

(g) Assuming total purchased service is \$2,000 for the machine's lifetime.



labor and maintenance labor costs to account for the cost of supervisory, management, and other support personnel.

The unit area equipment and facility costs, which constitute the capital cost, were obtained by dividing the respective annual costs by the annual area factory output. The overhead, listed in line 13 of Table III, is defined as the insurance, state taxes, and interest-on-debt payments on the working capital. As suggested by SAMICS⁽¹²⁾, the working capital was taken as 15% of the equipment plus facility cost, or 15% of the capital cost.

The profit and the amortization of one-time costs is represented by the return-on-equity (ROE), shown in line 14 of Table III. This value is equal to the SAMICS' return-on-equity (EQR), which is 20% of the equity portion of the book value⁽¹²⁾, plus the amortization of the start-up costs (AOC), minus the income tax investment credit (ITC) on 10% of the annual equipment depreciation divided by the product of one minus the federal income tax credit ($1 - \tau$) and one minus the miscellaneous expense fraction, (1 - x), or

ROE (III.14) =
$$\frac{EQR + AOC - ITC}{(1-x) * (1-\tau)}$$
 \$/m².

The add-on cost components described above can be used to calculate a unit area wafer price that ignores the cost of the silicon ingots. This add-on price shown in line 15 of Table III, is the sum of the material, labor, capital, overhead and return-on-equity. To convert this value into a wafer price, the unit mass cylindrical crystal price, and the add-on

grinding cost must be added to it. The unground silicon crystal or ingot prices shown for 1978, 1982 and 1986 are taken from our previous evaluations.⁽¹⁴⁾ For 1978, the ingoc price is based on pulling 7.8-cm diameter ingots with a Leybold-Heraeus single charge puller. The silicon ingot prices employed for the years 1982 and 1986 are projections for multi-pulling Cz-grown 10.2-cm and 15.2-cm diameter ingots, respectively.

Previous to slicing, the silicon ingots must be ground to a uniform diameter and this cost has to be included in the cost of the direct material. The add-on cost of grinding, listed in line 16 of Table III, consists of two parts: a) the cost of the grinding operation which is projected to be 0.20/cm-crystal length, based on industry data⁽¹⁾, and b) the cost of the silicon lost from grinding, which is equal to $\frac{11.18}{(100 - 11.18)}$ * (Si ingot price (\$/kg)), where II.18 is the percentage of material lost in grinding. Summing the add-on grinding cost to the Si ingot price yields the cost of ground silicon prices (Table II, lines 17, 22, 27) which are used to calculate silicon wafer prices.

Also of interest in our analysis is the cost of the silicon lost in kerf and broken wafers. These values, shown in line 18, 23, 28 of Table III, are the product of the unit area kerf and wafer loss mass (Table II, line 20) and the ground silicon prices. The add-on wafer prices, shown in lines 19, 24 and 29 of Table III, are defined, here, as the sum of add-on wafer price, assuming a zero silicon price (Table III, line 15) and the cost of the lost silicon.

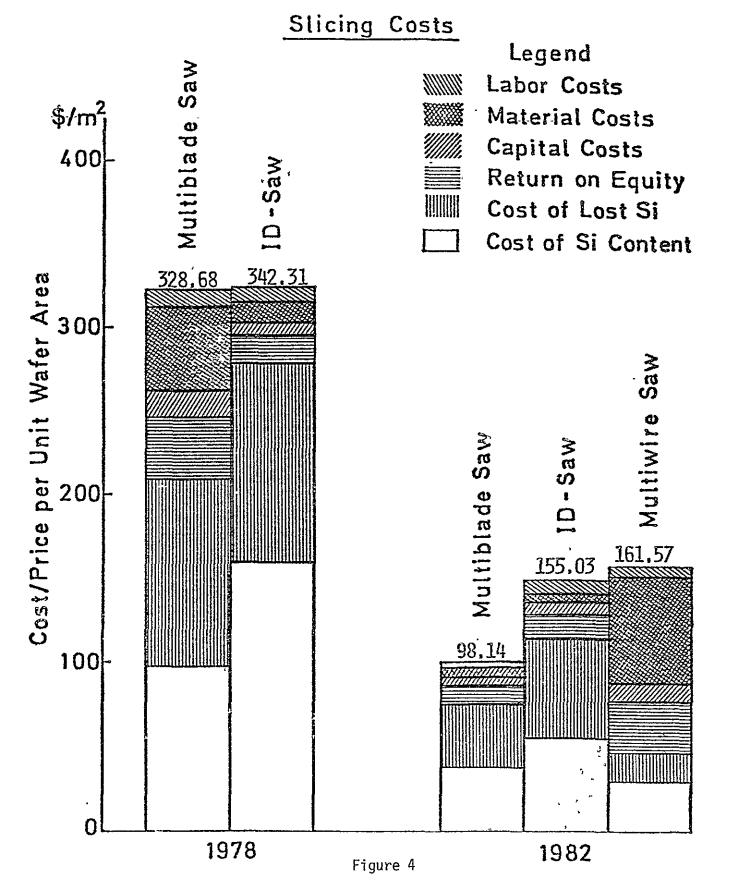
To arrive at a unit area wafer price listed in lines 20, 25, and 30 of Table III, the add-on price and the cost of silicon incorporated in the

wafer are summed. The latter value is the cost of the ground silicon ingot multiplied by unit area silicon mass contained in the wafers (Table II, line 19).

C. COST STRUCTURES OF THE SLICING PROCESSES

The more important unit area manufacturing cost components for selected current production or experimental slicing capabilities, using 1978 silicon prices, and projected future capabilities, using 1982 and 1986 projected silicon proces are summarized in Table IV. These silicon prices apply to single crystal ingots grounded to a uniform diameter. Also included in this table are the costs of the lost silicon and that contained in the wafer. In Table IV, one can observe the decreases in expendible tooling, indirect materials, labor and capital costs that are expected for 1982 in ID, multiblade and slurry multiwire slicing. Illustrated in Figure 4 are the more relevant data of Tables III and IV, in a bar graph format. In Figure 4, the relative impacts of the material, labor and capital costs can be readily compared to each other for the current multiblade and ID slicing processes and for the near future (1982) projected multiblade, ID, and slurry multiwire processes.

As evidenced in Table IV, the indirect material costs (primarily slurry) and the costs for expendible tooling (the steel blades or wires) are much higher for the slurry sawing processes (multiblade and Yasunaga multiwire) than those for the fixed abrasive approaches (ID saw and FAST wire saw). This is a consequence of the more effective utilization of the abrasive in the fixed abrasive system, coupled with longer tool life. Reductions of these expendible tooling costs for the multiblade and slurry multiwire slicing processes are expected in the future through lower cost tool fabrication techniques are expected to result from larger



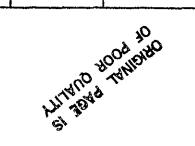
Costs of silicon wafer production in the years 1978 and 1982 by the slicing cost components, including the cost of the single crystal silicon content.

TABLE IV

KEY COSTS (\$/m²)

Турс	ID	Saw		ultiblade	Multiwire			
Source N-tal Dia (cm) Data Type	OCLI 7.6 Exper. 1978	STC 10 Projected 1982	Spectrolab 7.5 Product.	Van 10 Exper.	rian 12 Projected 1982	Yasu 7.6 Exper.	naga 10 Projected <u>1982</u>	Cryst. Systems* 10 x 10 rect. Projected 1986
Tooling	4.65	1.46 .	23.81	32.68	2.04	33.00	18.25	0.33
Ind. Materials	2,65	-	6.95	7.50	3.85	32.95	41.05	0.35
Dir. Labor	3.05	1.48	15.14	4.85	0.77	4.72	3.19	1.67
Maint. Labor	2.63	0.15	5.42	3.55	0.56	4.14	1.55	0.54
Equip't Cost	9.09	3.66	6.37	12.43	2.71	8.79	10.21	2.55
Facil. Cost	1.67	0.50	1.46	2.85	0.41	0.96	1.12	0.47
Add-On Cost	27.07	7.25	69.16	74.44	13.43	91.00	80.70	7.61
Ret. on Equity	21.99	7.68	28.37	39.85	6.92	30.57	30.92	6.18
Lost Si	131.09	38.97	111.79	113.21	36.61	71.57	16.46	12.88
Add-On Frice	180.15	53,90	207.32	227.50	56.96	193.14	128.08	26.67
Sı Content	128.87	37.65	142.41	101.18	41.18	75.14	33.49	12.88
<u>Frice</u>	309.02	91.55	349.73	328.68	98.14	268.14	161.57	39.55
Si ground X-tal (\$/kg)	152.92	71.55	153.14	149.11	70.39	152.92	71.55	27.52

*Calculated using an effective cutting rate of 0.4 cm/h.



scale, automated assembly⁽⁹⁾ and a simplification of the assembly process⁽¹¹⁾. Investigations are currently being conducted into possibilities for the -slurry-costs, for instance by reclycling the slurry or substituting a cheaper vehicle (e.g. mineral oil) for the PC oil. In spite of these projected reductions, the indirect material and expendible tooling costs for the multiblade and the Yasunaga multiwire techniques remain sizable components of the total add-on costs for those processes. In the nearterm projections, these components are 44% and 73% of the add-on cost for the multiblade and slurry multiwire processes, respectively. This compares to 20% and 9% of the 1982 projections for the add-on costs in the ID and fixed abrasive multiwire saws, respectively.

The current prices are essentially equal for production wafers cut by either the Varian multiblade or the ID sawing processes, although the ID saw has twice the productivity (Table I, line 24) and experiences lower indirect material and tooling costs. The higher productivity directly results in lower labor, capital, and return-on-equity costs, as shown in Figure 4. These lower processing costs for the ID slicing are counterbalanced, however, by a higher silicon consumption resulting from the practice to cut the wafers to greater thickness with higher kerf than achieved with the slurry saws. At the current silicon prices, this has a considerable cost impact.

The 1978 wafer prices shown here are somewhat lower than the contemporary commerical wafer and the 1978 values of the LSA Interim Price Allocation Guidelines⁽¹⁴⁾. This difference results from two facts: a) the data of this report do not include the cleaning, etching, or polishing process steps usually included in commercially sold wafers; and b) the standardized indirect cost model (SAMICS-IPEG) purposely omits several

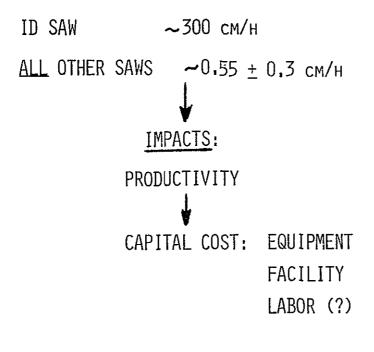
indirect charges on partially processed items such as wafers. Since the indirect cost structure models a vertically integrated industry, marketing costs for wafers, e.g. are not incurred.

CONCLUSIONS

The cost-analysis data, and particularly the projections, which include reduced expendible tooling and indirect material cost components, show that the dominant influence on the add-on price of sliced wafers is the productivity of the slicing machine. The machine productivity (the time rate of output unit expressed in wafer area) has a direct inversely proportional impact on the capital cost allocation to the wafer area produced of the cost components for equipment and facility, and on that part of the labor expenditures which are devoted to machine monitoring and maintenance, as shown in Figure 5. Figure 5 shows that the effective linear cutting rate (the workpiece diameter divided by the slicing time-segment) is 0.55 + 0.3cm/h for the multiblade and multiwire processes. The inner diameter diamondcoated blade process has an effective linear cutting rate of approximately 300 cm/h, a nearly 550 times larger value than that for the other processes. To achieve comparable machine productivities, the low linear cutting rates have to be compensated by simultaneous multiple slicing. The current efforts of Crystal Systems, Solarex, and Varian are therefore directed at increasing the number of wafers sliced during a run. Current multiblade packages contain about 250 blades. Varian has built an experimental slicer incorporating a blade pack of over 900 blades. Similarly, the wire package proposed by Crystal Systems (10) is projected to have 750 cutting wires. Solarex hopes to slice⁽¹¹⁾ 333 wafers at a time with the Yasunaga YQ-100 slicing machine.

The slicing technology improvements projected for the 1982 production lines are based on the results of recent experimental runs and on

CUTTING RATES:



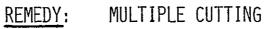


Figure 5.

developments in progress (Table IV, Fig. 5). For the multiblade saw, the primary advancement will be a nearly four-fold productivity increase via Varian's development of a machine using a 900-blade-pack. Simultaneously, a 25% blade thickness reduction in combination with a 37.5% wafer thickness decrease, while maintaining a wafer yield of 95%, is projected to result in an area yield of 0.9 m²/kg-Si crystal, a 50% increase from Spectrolab's mass to area conversion ratio in slicing round wafers.

Slice and kerf thickness reductions to values similar to those projected for the multiblade slurry process, are also expected for the ID-sawing method. Recently acquired data from STC are reflected in a 1982 projection for 10-cm diameter crystals using ID slicing with ingot rotation, as shown in Table IV and in a UPPC format attached to the appendix. The wafers from this process are expected to be 225 µm thick with 210 µm kerf. In addition, crystal rotation is expected to double the effective cutting rate of the ID process. This essentially doubles the productivity of the ID saw, and results in comparable projected productivities for the 900-blade multiblade and the ID sawing processes. Remaining differences in the costs of these two processes are, however, overshadowed by the cost of the silicon incorporated into the wafer or lost. At the projected 1982 price for ground single crystal ingots, the cost of this silicon still amounts to nearly 80% of the wafer price.

One slicing method has been projected to 1986, primarily, because only a comparatively small base of experimental data is available, so that this method cannot be expected to be in significant commercial operation by 1982. This method is Crystal Systems' fixed abrasive

multiwire sawing. The current projections are contained in Table IV, while Table IIIB is based on earlier inputs. The difference results primarily from a recently communicated reduction in tooling costs based on wirehead fabrication improvements, and from the use in Table IV of a more conservative effective cutting rate corresponding to the experimentally found rates averaged over the life of the bladehead. The process add-on costs are comparable to those of the two previously discussed processes. If the silicon price of 1982 would have been used, an approximately: \$11/m² lower wafer price would have resulted in comparison to the ID process. While the fixed abrasive multiwire process currently projects the lowest wafer price, it is also the one with the least experience data. It is therefore of great importance to gain a significant data base through pilot line operation.

Considering the uncertainties in the projections, the data indicate no considerable differences in the competitiveness of the three approaches, and a reasonable potential for all-three to meet the 1986 guideline goal.

4. <u>NEW TECHNOLGY</u>

No new technology was developed during this quarter.

- 5. REFERENCES
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- 3. H.I. Yoo, OCLI, Report DoE/JPL 954830-77/12 (12/77).
- 4. S.C. Holden and J.R. Fleming, Varian Associates, Report ERDA/JPL 954374-77/2 (7/77).
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- 6. H.I. Yoo, ibid.
- 7. P. Aharonyan, Silicon Technology Corp., Oakland, N.Y., private communications (8/78).
- 8. C.P. Chen, JPL-LSA Project Report DoE/JPL-1012-78/7 (2/78).
- 9. S.C. Holden and J.R. Fleming, ibid.
- F. Schmid and C.P. Khattack, Crystal Systems, Report ERDA/JPL 954373-77/3 and 77/4 (10/77 and 12/77).
- 11. J. Lindmayer et. al., Solarex, Report ERDA/JPL-77/2 (8/77).
- 12. R.W. Aster and R.G. Chamberlain, JPL-LSSA Project Report 5101-33 (9/77).
- 13. Theodore Barry and Associates, Report ERDA/JPL-954800-77/2.1 (9/77).
- 14. W. Callaghan, presented at the Ninth PIM; Pasadena, CA, (4/78).

6. <u>APPENDIX</u>

The University of Pennsylvania Characterization Formats for Production, Experimental and Projected Slicing Processes

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet Generation

Subprocess: Wafer Generation

Option: Mounting of crystal ingots on

ceramic base with wax (Spectrolab)

INDEX

Form	Pages	Rev.	Date	<u>Remarks</u>
1			_3/78	<u>All forms have same date.</u>
2	l to <u>1</u>			
3	1 to <u>1</u>			
4	1 to <u>0</u>			
5	1 to <u>1</u>			
6	1 to <u>1</u>			
7	1 to <u>1</u>			
8	1 to <u>1</u>			
9-1	1 to _0_			
9-2	1 to <u>0</u>			
9~3	1 to _0	·		
10	1 to <u>0</u>			
11	1 to <u>0</u>			
12	1 to <u>1</u>			
13~1	1 to <u>1</u>			
13-2	l to <u>1</u>			
14	1 to <u>0</u>			
15	1 to <u>1</u>			
16	1 to _0			

Form 2

				Page <u>1</u> of <u>1</u>
			Revision	Date3/78
ocess No. 2	4 0 1 - 0 1		0.1 Value Added:	\$/
ocess Descrip	tion: Mounting of two, 7.5 cm diameter, 16 - cm long s	ingle cryst	al. silicon	
ingot	s on a ceramic base with wax. Material and labor requ			b.

Input Speci	fication:			
	m:			
Dimensions:	7.5 cm in diameter, 16.875 cm in length, and 1.744	<u>kg.</u>	<u></u>	
Material: _	high purity silicon			
Other Speci	figations:		<u></u>	
	-			
, <u></u> ,,,				
			<u></u>	
				<u>, , , , , , , , , , , , , , , , , , , </u>
] 			
-				
	1.1 Quantity Required: 3.49 kg	/ <u>load</u>	Unit Cost: 15	53.14 \$/ kg
			1.2 Input Value:	\$/
	· · · ·		1.3 Input Cost:	534.31 \$/load
				······································

Note to Item 1.3: Use price, if input produced in own plant.

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Process No.	2.4.01-01			Form	3
2.1 Direct	Materials:	Revision		·	<u>1</u> of <u>1</u> 3/78
	Type: <u>Ceramic base</u>			1	
		<u></u>	 ;	ı	
	Quantity Required: /; Unit Cost:0.60 Type: Mounting wax		Cost:	0.60	\$/ load
	Specification:Cost is estimated. Can be recycled.				
	Quantity Required: /; Unit Cost:0.10			0.10	\$/load_
	Type:Specification:				
	Quantity Required:/; Unit Cost:	<u></u>	i	, ,	_\$/
	2.1 Subtotal I	Direct Mater:	lals:	0:70	\$/load

Proc	ess No	. 2	. 4 . 0 1 - 0 1			Form 5
2.3	Expen	dable I	Cooling:			Page <u>1</u> of <u>1</u>
	2.3_	Type:			Revisi	on Date <u>3/78</u>
			Quantity Required:	/: Unit Cost:\$/_	Cost:	\$/
	2.3_	Туре:				
			Quantity Required:	/: Unit Cost:\$/_	Cost:	\$/
	2.3_	Type:		<u> </u>		
		<u> </u>	Quantity Required:	/: Unit Cost:\$/_	Cost:	\$/
	2.3_	Type:				
			Quantity Required:	/: Unit Cost:\$/_	Cost.	\$/
				2.3 Subtotal Expendable	Tooling:	\$/
						<u></u>
2.4	Energ	у				
	2.4 <u>1</u>	Type:	Electricity (2 kW power rating)		1	
		<u></u>	Quantity Required: 0.50 kWh/	<u>load</u> : Unit Cost: 0.0319 \$/	(Wh Cost:	0.02 <u>\$/ load</u>
	2.4_	Type:				
			Quantity Required:	: Unit Cost:\$/_	Cost:	\$/
				2.4 Subtotal Energ	y Costs:	\$/
				2.5 Subtotal 2.1 to 2.4;		0.72 \$/ load
				2.6 Handling Charge: <u>5.26 %</u> of	E 1tem 2.5	0.03 \$/ <u>load</u>
			_	2.7 Subtotal Materials and Sup (2.5 + 2.6)	plies:	0.75 \$/ <u>load</u>
				•		

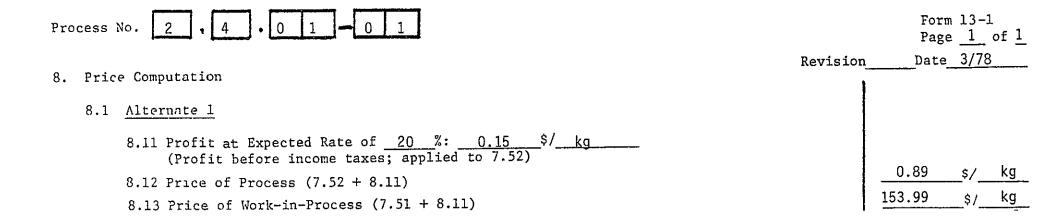
Proce	ess No.	2.4.01-01			Revision	Form 6 Page <u>1</u> Date3	
3.1		Labor:					
	3.11	Category: Semiconductor assembler	Activity: Wor	<u>kpiece mountir</u>	1g		
		(SAMICS B3096D) Amount Required: 0.25 h/ load	; Rate: \$ <u>3.894</u>	/h; Load 36.()%; Cost:	1.34	\$/ <u>load</u>
	3.1_	Category:	Activity:				
		Amount Required:h/	; Rate: \$	_/h; Load	%; Cost:		_\$/
	3.1	Category:	Activity:		······································		
		Amount Required:h/	; Rate: \$	/h; Load	%; Cost:		\$/
				3.1 Direct La	ibor Subtotal:	<u> </u>	_\$/
3.2	Indire	ct Labor: Taken as 25% of direct	labor				
	3.2	Category:	Activity:				
		Amount Required:h/	; Rate: \$	_/h; Load	%; Cost:		\$/
	3.2	Category:	Activity:				
		Amount Required:h/	; Rate: \$	_/h; Load	%; Cost:		\$/
	3.2	Category:	Activity:				
		Amount Required:h/	; Rate: \$	_/h; Load	%; Cost:		\$/
					Labor Subtotal:	0.33	\$/ <u>load</u>
4 0,000-00	<u></u>			3.3 Subtotal	3.1 and 3.2	1.67	\$/ <u>load</u>
				3.4 Overhead	on Labor: <u>5.26</u> %	0.09	\$/ <u>load</u>
				3.5 Subtotal	Labor	1.76	\$/ <u>load</u>

.

	ess No		Revision_	Form 7 Page <u>1</u> of <u>1</u> Date <u>3/78</u>
4.1	Equipi	nent	1	
	4.1_1	Type: Hot plate (25 x 40 cm) with bench.		
		Cost: 2,000 \$; Installation Cost:\$; Throughput: <u>2 loads</u>	/h;	
		Plant Oper'g Time8280h/y; Machine Avail'ty:99_%; Machine Oper'g Time	8200 h/y	
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	\$/y	
		Useful Life:y; Charge Rate% of Cost/y; Capital Cost:430	\$/y	0.03 \$/ <u>load</u>
	4.1_	Type:		
		Cost:\$; Installation Cost:\$, Throughput:	/h;	
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y	
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	\$/y	
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y	\$/
	4.1_	Type:		
00		Cost:\$; Installation Cost:\$; Throughput:	/h;	
ORIGINAL		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time		
Ŝ₽		Servicing Costs. Laborh/y at\$/h;Parts or Outside Service:	\$/y	
PAGE		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y	\$/
オあ		4.1 Subtotal Equip	ment Cost:	0.03 \$/ <u>"load</u>

ess No. 2.4.	0 1 - 0 1						Form 8 Page <u>1</u> of 1
Facilities:						Revision	Date 3/78
4.2 <u>1</u> Type: Bench ar	rea	_ Floor Area:	2.(m ² ; Throughput: <u>16,4(</u>	0 <u>10a</u>	ds_/y	3.0
Charge Rate:	179.13*	_\$/(m ² ·y);		Maintenance Costs:			
	Energy Use:	1	Labor	h/y ath	\$/	h	
Heating	/y at	\$/		Supplies:	\$/	у	
Air Cond'g	/y at	\$/	}	Outside Services:	\$/	у	
Lighting	/y at	\$/		Total Cost:	360	\$/y	0.02 \$/load
4.2_ Type:		_ Floor Area:		m ² ; Throughput:		/y	
Charge Rate:		\$/(m ² ·y);		Maintenance Costs:		•	
	Energy Use:		Labor	h/y ath	\$/	h	
Heating	/y at	\$/		Supplies:	\$/	у	
Air Cond'g	/y at	\$/	6	Outside Services:	\$/	y	
Lighting	/y at	\$/	┝╍╍ 	Total Cost:		\$/y	\$/
4.2_ Type:		_ Floor Area:		m ² ; Throughput:		_/y	
Charge Rate:		$_{(m^2 \cdot y);}$	ru ur i	Maintenance Costs:		~~~~	
1000 0000 0000 00000 00000 00000 0000	Energy Use:		Labor	:h/y at	\$/:	h	
			•	Supplies:	\$/;	y	
Air Cond'g	/y at	\$/	6 	Outside Services:	 \$/·	y .	
Lighting	/y at	\$/	haya ay }	Total Cost:		\$/y	\$/
			ς.	4.2 Subtot	al Facilit	:ies:	<u>0.02</u> \$/ <u>load</u>
*INCLUDE	S ENERGY USE			4.3 Equipment and Facilit	ies Subtot	al :	0.05 \$/load
	Facilities: 4.2 <u>1</u> Type: <u>Bench and</u> <u>Charge Rate:</u> <u></u> <u>Heating</u> <u>Air Cond'g</u> <u>Lighting</u> 4.2_ Type: <u></u> <u>Charge Rate:</u> <u>Heating</u> <u>Air Cond'g</u> <u>Lighting</u> 4.2_ Type: <u></u> <u>Charge Rate:</u> <u>Heating</u> <u>Lighting</u> <u>Lighting</u>	Facilities: 4.21 Type: Bench area Charge Rate: 179.13* Energy Use: Heating /y at Air Cond'g /y at Lighting /y at 4.2_ Type:	Facilities: 4.21 Type: Bench area	Facilities: 4.21 Type: Bench area Floor Area: 2.0 Charge Rate: 179.13* $\$/(m^2 \cdot y)$: Labor Heating /y at $\$/_{}$ Air Cond'g /y at $\$/_{}$ Lighting /y at $\$/_{}$ 4.2_ Type: Floor Area: $\$/_{}$ Charge Rate: $\$/(m^2 \cdot y)$; Labor Heating /y at $\$/_{}$ Air Cond'g /y at $\$/_{}$ Lighting /y at $\$/_{}$ Air Cond'g /y at $\$/_{}$ Lighting /y at $\$/_{}$	Facilities: 4.21 Type: Bench area Floor Area: 2.0 m ² ; Throughput:16,40 Charge Rate: 179.13* \$/(m ² ·y): Maintenance Costs: Labor:	Facilities: 4.21 Type: Bench area Floor Area: 2.0 m ² ; Throughput: 16,400 loa Charge Rate: 179.13* \$/(m ² .y); Maintenance Costs: \$/ Heating	Revision Facilities: 4.21 Type: Bench area Floor Area: 2.0 m ² ; Throughput: 16,400 loads /y Charge Rate: 179.13* $S/(m^2 \cdot y)$: Maintenance Costs:

Process No. 2 . 4 . 0 1 - 01 7. Process Cost Computation 7. Process Cost Computation 7. 11 Manufacturing Add-On Costs (sum of 2.7, 7.22 Other Indirect Costs:% of 7.1 7.21 Total Operating Add-on Costs of Process 7.22 G & A% of 7.21 7.31 Total Gross Add-On Cost of Process 7.32 Credit for Salvaged Material (5.8) 7.33 Cost of Work-in-Process Lost (5.3) 7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained Output Work-in-Process (5.4)	ion Date 3/78
7.22 Other Indirect Costs: % of 7.1 7.21 Total Operating Add-on Costs of Process 7.22 G & A% of 7.21 7.31 Total Gross Add-On Cost of Process 7.32 Credit for Salvaged Material (5.8) 7.33 Cost of Work-in-Process Lost (5.3) 7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained	
7.21 Total Operating Add-on Costs of Process 7.22 G & A% of 7.21 7.31 Total Gross Add-On Cost of Process 7.32 Credit for Salvaged Material (5.8) 7.33 Cost of Work-in-Process Lost (5.3) 7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained	, 3.5, 4.3, 6.) <u>2.56</u> \$/ load
7.21 Total Operating Add-on Costs of Process 7.22 G & A% of 7.21 7.31 Total Gross Add-On Cost of Process 7.32 Credit for Salvaged Material (5.8) 7.33 Cost of Work-in-Process Lost (5.3) 7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained	L1\$/_load
7.31 Total Gross Add-On Cost of Process 7.32 Credit for Salvaged Material (5.8) 7.33 Cost of Work-in-Process Lost (5.3) 7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained	
7.32 Credit for Salvaged Material (5.8) 7.33 Cost of Work-in-Process Lost (5.3) 7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained	\$1
7.33 Cost of Work-in-Process Lost (5.3) 7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained	<u> 2.56 </u> \$/ <u>load</u>
7.34 Specific Add-On Cost of Process (7.31 + 7.35 Cost of Input Work-in-Process Contained	\$/\$
7.35 Cost of Input Work-in-Process Contained	\$/\$
-	+ 7.33)-(7.32) <u>2.56</u> \$/ <u>load</u>
	d in Good 534.31 \$/_load
7.36 Loading on Item 7.35 at Rate%	\$/
7.37 Cost of Output Work-in-Process (7.34 +	7.35 + 7.36) <u>536.87</u> \$/ <u>load</u>
7.41 Theoretical Yield (or Conversion Rate, if output units of work-in-process do not equal input units)	<u>oad</u>
7.42 Practical Yield 100	<u>0 </u> %
7.43 Effective Yield (7.41 x 7.42)	
7.44 Number of Units of Good Output Work-in-Process per Computation Unit Used up to 7.35	oad
7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	1 <u>53.84</u> \$/_kg
7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	\$/kg



Process No. 2 4 0 1 0 1	Form 13-2 Page <u>1</u> of <u>1</u>
Revision	_Date <u>3/78</u>
8.2 <u>Alternate 2</u> (SAMICS Methodology):	
8.21 Profit Computation:	
0.9274* 0.026 \$/ load from Subtotal 4.1 = 0.024 \$/ load	
1.946* 0.022 \$/ load from Subtotal 4.2 = 0.043 \$/ load	
Subtotal = 0.067 \$/ load	Î
8.22 Costs of Amortization of the One-Time Cost:	
0.192* 0.75 \$/ load from Subtotal 2.7 = 0.145 \$/ load	
0.192* 1.76 \$/ load from Subtotal 3.5 = 0.338 \$/ load	
0.2958* 0.026 \$/ loadfrom Subtotal 4.1 = 0.008 \$/ load	
2.77* 0.022 \$/ load from Subtotal 4.2 = 0.061 \$/ load	
Subtotal = 0.551 \$/ load	
8.23 Total Net Cost of Equity (8.21 + 8.22):	0.62 \$/ load
8.24 Profit and Amortization of Start-up Costs per Unit of Good Output Work-in-Process: (Divide Subtotal 8.23 by <u>3.49 kg / load</u> from 7.44) <u>0.18 \$/ kg</u>	
8.25 Price of Process (7.52 + 8.24)	0.92 \$/ kg
8.26 Price of Work-in-Process (7.51 + 8.24)	1 <u>54.02\$/_kg</u>

•

Process No. 2 . 4 . 0 1 - 0 1		Form 15 Page <u>1</u> of <u>1</u>
/ Re	evision	Date 3/79
0. Output Specification:		
Name of item: Mounted silicon ingots		
Dimensions: 15.2 - cm in diameter, 7.62 - cm high and 16.875 - cm long		
Material:		
Other Specifications: The capital cost for mounting an ingot for MBS is proportional	<u>to l * r .</u>	Therefore
the unit mass capital cost for mounting is inversely proportional to r. Since the cap	oital cost i	s a small
part of the total cost, the mounting cost is essentially independent of ingot size.	For MBS, the	e mounting
cost is \$3.18/load.		
		······································
		<u> </u>

Form 1

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet Generation

Subprocess: Wafer Generation

Option:

on: Mounting of ingot on graphite block

with epoxy for use on ID-blade machines.

Data supplied by OCLI. INDEX

Form	Pages	Rev.	Date	Remarks
1			3/78	Dates on all forms are the same.
2	1 to <u>1</u>	•		
3	1 to <u>1</u>			
4	1 to <u>1</u>			
5	1 to _1			
6	1 to <u>1</u>			
7	1 to <u>1</u>	<u> </u>		
8	l to <u>1</u>			
9-1	1 to <u>0</u>			
9-2	1 to _0			
9-3	1 to _0			
10	l to _0			
11	l to _0			
12	l to <u>1</u>			
13-1	1 to <u>1</u>			
13-2	1 to <u>1</u>			······································
14	1 to <u>1</u>	·		
15	1 to <u>1</u>			
16	l to _ <u>0_</u>			

Form 2

				Page <u>1</u> of <u>1</u>
	-		Revision	Date3/78
Process No. $2, 4, 01 - 03$			0.1 Value Added:	\$/
Process Description: <u>Mounting of ingot on</u> slicing. Data supp				
1. Input Specification:		<u></u>		
Name of Item: Single crystal, silicon				
Dimensions: <u>10.16 - cm in diameter, 25</u>	- cm in length, and	<u>mass is 4.74 kg</u>		
Material: High purity silicon			<u></u>	
Other Specifications:				
Other Specifications:				
				* ****
l.1 Quanti	Lty Required: 4.74	kg / <u>load</u>	Unit Cost:	71.43_\$/_kg
		T	1.2 Input Value:	ş/
			1,3 Input Cost:	338.58 \$/ load
		l l		

Note to Item 1.3: Use price, if input produced in own plant.

Process No.	2.4.01	- 0 3						Form (3 1 _{Of} 1
2.1 Direct	Materials:					Revision			
2.1 <u>1</u>	Type: Ingot mount	ing material			·		I		
	Specification:	Includes epoxy and grap	phite				_		
		Data taken from OCLI.							
	.						_;		
	Quantity Required:		/,	Unit Cost	: <u>1.36</u>	\$/ <u>load</u> ;	Cost:	1.36	\$/load
2.1_	Туре:			<u> </u>			;		
	Specification:	·····		······································			_;		
							-		
							-		. (
									\$/
2.1_									
	Specification:								
							-		
	Quanta ty Poquirod:						ے Cost:		s/
	Quantity Required.		,	5MIL 0031		Y/	, ,		
						、			
				2.1	Subtotal	Direct Mater	rials:	1.36	\$/ <u>1oad</u>

Process No. 2	4.01-03			For	m 5
2.3 Expendable Toc				Pag	e <u>1_</u> of <u>1</u>
2.3 _ Type:	-			Revision	Date <u>3/78</u>
	Quantity Required:		\$/	Cost:	\$/
2.3 _ Type:	~~~~				
	Quantity Required:	/: Unit Cost:	\$/	Cost:	\$/
2.3 Type:					
	Quantity Required:	/: Unit Cost:	\$/	Cost:	\$/
2.3_ Type:					
	Quantity Required:	/: Unit Cost:	\$/	Cost:	\$/
		2.3 Subtotal Expe	ndable 1	fooling:	\$/
			···		

2.4 Energy

2.4 <u>1</u> Type: <u>Power rating of hot plate is estimated t</u> Quantity Required: <u>0.23 kWh</u> /		<u>0.007 \$/ load</u>
2.4Quantity Required:	; Unit Cost:\$/ Cost: 2.4 Subtotal Energy Costs:	\$/ 0.007\$/_load_
	2.5 Subtotal 2.1 to 2.4; 2.6 Handling Charge: <u>5.26 %</u> of item 2.5	<u>1.37 \$/ load</u> 0.07 <u>\$/ load</u>
	2.7 Subtotal Materials and Supplies: (2.5 + 2.6)	1.44 \$/ load

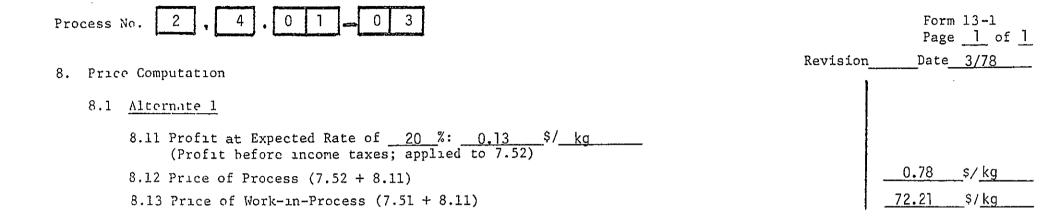
Process No.	and a second		Revision	Form 6 Page <u>1</u> of <u>1</u> Date <u>3/78</u>
3.1 Direct			Ingot mounting	
3.1_1	Category: <u>Semiconductor Assembler</u> (SAMICS B3096D)	Activity:	Ingot mounting	
	Amount Required: 0.23 h/ loa	d; Rate: \$ <u>3.895</u>	_/h; Load <u>36.0%;</u> Cost:	\$/ <u></u> \$/oad
3.1	Category:	Activity:		
_	Amount Required:h/			\$/
2 1	Category:			
J.T.	Amount Required:h/	· Rate: \$	/h: Load %; Cost:	\$/
	Amount Required:	,	3.1 Direct Labor Subtotal:	
3.2 Indire	ct Labor: Taken as 25% of direct		J.T DIFFEC Haber Superset.	
3.2	Category:	Activity:		
	Amount Required:h/			\$/
3.2_	Category:	Activity:		
	Amount Required:h/	; Rate: \$	/h; Load%; Cost:	\$/
3.2	Category:			
<u> </u>	Amount Required:h/			\$/
	· · · · · · · · · · · · · · · · · · ·		3.2 Indirect Labor Subtotal:	0.30 \$/load
		<u>,</u>	3.3 Subtotal 3.1 and 3.2	1.52 \$/load
		-	3.4 Overhead on Labor: <u>5.26</u> %	\$/_load
			3.5 Subtotal Labor	<u>1.60 \$/load</u>

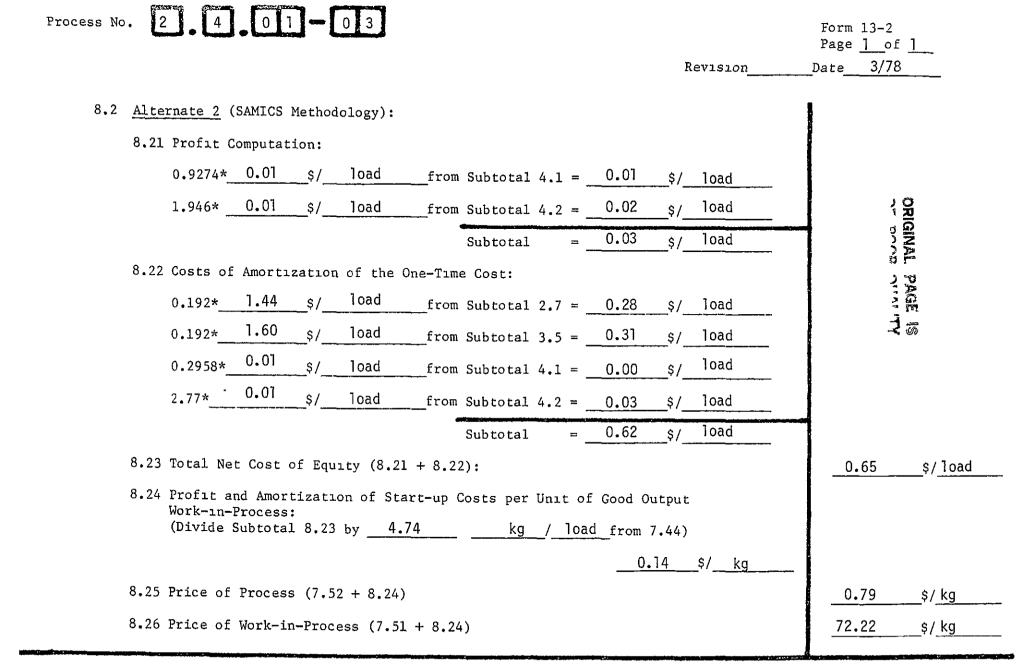
Process No. 2 4 0 1 - 0 3 A.1 Equipment	Form 7 Page 1 of 1 Date 3/78
<pre>4.1_] Type: Hot plate (20 x 20 cm) with work bench Cost: 1,000 \$; Installation Cost: \$; Throughput: 2 loads /h; Plant Oper'g Time 8280 h/y; Machine Avail'ty: 95 %; Machine Oper'g Time 7866 h/y Servicing Costs: Labor h/y at \$/h;Parts or Outside Service: \$/y Useful Life: y; Charge Rate: 21.35 % of Cost/y; Capital Cost: 213.50 \$/y</pre>	0.01 \$/ load
4.1Type:	
4.1Type:	
4.1 Subtotal Equipment Cost:	0.01 \$/]oad

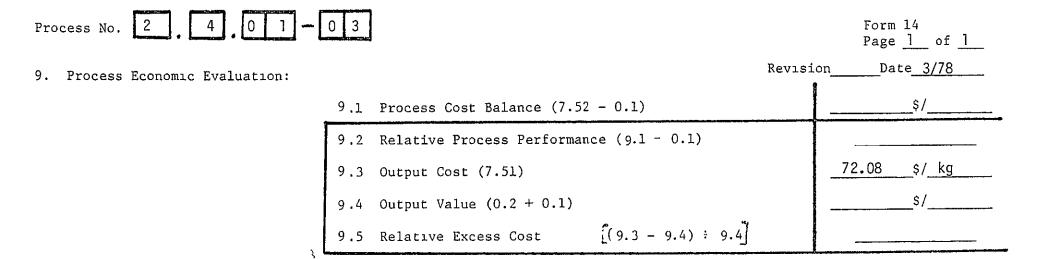
Proc	ess No. 2, 4,	01-03						Form 8 Page 1	of l
4.2	Facilities:						Revision	Date	
	4.2 <u>1</u> Type: <u>Bench are</u>	a	Floor Area:	1	m ² ; Throughput: 15,73	<u>32 10</u>	<u>ads</u> /y		
	Charge Rate:	179.13*	_\$/(m ² ·y);	- -	Maintenance Costs:				
		Energy Use:		Labor	:h/y at	\$/	h i		
	Heating	/y at	\$/		Supplies:	\$/	y		
	Air Cond'g	/y at	\$/	1	Outside Services:	\$/	у		
	Lighting	/y at	\$/	┗━╴╺━ ┃	Total Cost:	179	\$/v	<u>0.01</u> \$,	/ <u>load</u>
	4.2Tvpe:		Floor Area:		² ; Throughput:		_/y		
	Charge Rate:		\$/(m ² ·y);	<u> </u>	Maintenance Costs:		•		
	و ويستر ويستر بسيده هيدو بيده	Energy Use:	dereta therefore and	Labor	:h/y at	\$/	n		
	Heating	/y at	\$/	1	Supplies:	\$/	y		
	Air Cond'g	/y at	\$/	k 1	Outside Services:	\$/	,		
	Lighting	/y at	\$/	h 1	Total Cost:		\$/y	\$/_	
-	4.2_ Type:		Floor Area:		m ² ; Throughput:		_/y		
	Charge Rate:		\$/(m ² ·y);	~~ ~ ~ ~ l	Maintenance Costs:				
	aladi daga katala daga katala	Energy Use:		Labor	: h/y at	\$/	1		
	Heating	/y at	\$/	•		\$/;			
	Air Cond'g	/y at	\$/	•			1		
	Lighting	/y at	\$/		Outside Services: Total Cost:	\$/	\$/y	\$,	/
	Madamatan (4.2 Subtota	l Facilit		0.01 \$/	load
	* Includes energy u	se		ŀ	4.3 Equipment and Faciliti				/ load
				Ĺ			.a.t. •	<u> </u>	

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	Form Page	12 1 of 1
cess No. $2 \cdot 4 \cdot 0 \cdot 1 - 0 \cdot 3$	Revision Date_	3/78
Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	3.06 \$/load
	7.22 Other Indirect Costs:% of 7.11	0 \$/load
	7.21 Total Operating Add-on Costs of Process:	3.06_\$/load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	<u>3.06</u> \$/ <u>load</u>
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	\$/
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	<u>3.06</u> \$/load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	338.58 \$/load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	341.64 \$/ load
7.41 Theoretical Yield (or Conversi work-in-process do not equal i		
7.42 Practical Yield	100 %	
7.43 Effective Yield (7.41 x 7.42)	/	
7.44 Number of Units of Good Output Computation Unit Used up to 7.		
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	\$/_kg
	7.52 Specific Add-On Cost per Unit of Good	







Process No. 2	4 0 1 - 0 3	Form 15 Page <u>1</u> of <u>1</u>
	Revision	Date 3/78
0. Output Specifi	cation:	
Name of item:_	Mounted silicon ingot	
Dimensions:	10.16-cm in diameter, 25-cm in length	
Material:	Silicon with graphite base	
Other Specific	ations: The capital cost of mounting an ingot for ID-slicing is proportioned t	o <u>r², therefore</u>
this unit mas	s cost for mounting is inversely proportioned to the length of the crystal. Since	e the capital cost
is small comp	ared to material and labor costs, the absolute mounting cost is essentially indep	en <u>dent of crystal</u>
size. For I)-slicing, it is \$3.71/load.	
<u> </u>		
····		
<u> </u>		
······································		
		
<u> </u>		
<u> </u>		

Process No. 2 . 4 . 0 2 - 0 1

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet generation

Subprocess: Ingot slicing

Option: Multiblade slurry slicing of

5.4-cm diameter ingots (Spectrolab)

INDEX

Form	Pages	Rev.	Date	<u>Remarks</u>
1			3/78	All forms have same date
2	1 to <u>1</u>			
3	1 to _0			
4	1 to 1			
5	1 to]	· · · · ·		
6	1 to <u>1</u>			
7	1 to _1			
8	l to <u>1</u>			
9-1	l to <u> </u>			
9-2	l to <u>0</u>			
9-3	1 to <u>0</u>		·	
10	1 to <u> </u>			
11	l to <u>1</u>			
12	1 to <u>1</u>			
13-1	1 to <u>1</u>			
13-2	l to <u>1</u>			
14	1 to]			
15	1 to <u>1</u>			
16	1 to			

Form 2

	roduction line per load with	0.1 Value Addeo	.on Date <u>3/78</u> d:\$/
Spectrolab's p		experience	d:\$/
Spectrolab's p			
ots are sliced	per load with	a 250 blade-pack.	
4-01-01			<u></u>
eter and 16.875	5-cm long. Th	<u>ree ingots per load.</u>	
ree ingots are	<u>e mounted on a</u>	ceramic block.	
.903 kg			
71 kg			
,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			
		۵٬۰۰۰ می دور دور می داد. و می داد و می دور می	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,
quired: 2.71	kg /load	Unit Cost:	161.30 \$/ kg
		1.2 Input Value	e:\$/
	eter and 16.87 pree ingots ar 0.903 kg 71 kg	eter and 16.875-cm long. The pree ingots are mounted on a 0.903 kg 71 kg	eter and 16.875-cm long. Three ingots per load mee ingots are mounted on a ceramic block. 0.903 kg 71 kg quired: <u>2.71 kg / load</u> Unit Cost:

Note to Item 1.3: Use price, if input produced in own plant.

Proc	ess No	$2 \cdot 4 \cdot 0 = 0 = 0 = 0$			Form 4
2.2	Indir	ect Materials (incl. supplies and non-energy utilities):			Page <u>]</u> of <u>]</u>
		Type: Abrasive slurry	Revis	sion	Date3/78
	-	Specification: PC oil with 600 grit SiC abrasive		_;	
		Concentration is 0.24 kg/L, slurry cost given by Spectrolab.			
		Ouantity Required: 7.6 _2 / load; Unit Cost:\$/_;		 Cost:	$14.06 \ \text{$/load}$
	2.2_	Type:	·		
		Specification:			
				-	
		Quantity Required:; Unit Cost:\$/;	:		\$7
	2.2_	Type:	· /		/
		Specification:		-	
			<u>-</u>	-	
		Quantity Required:; Unit Cost:\$/;	;	- Cost:	ş/
		2.2 Subtotal Indire	ect Mate	rials:	14.06 \$/load

Proce	ess No.	2	4.02-01					Form 5
2.3	Expend	able To	poling:					Page] of]
	2.3 <u>1</u>	Type: _	250 blade drill-pin pack, consisting of O	.2 mm thick	1095 steel	blades.	Revisı	on Date <u>_3/78</u>
			Quantity Required: 0.5 P	ack_/load:	Unit Cost:	\$/_Pa	<u>ck</u> Cost:	25\$/_load_
	2.3_	Type: _		·····				
			Quantity Required:	/:	Unit Cost:	\$/	Cost:	\$/
	2.3_	Type: _		····				
		·- 	Quantity Required:	/:	Unit Cost:	\$/	_ Cost:	\$/
	2.3_	Туре: _				·····		
		<u> </u>	Quantity Required:	:	Unít Cost:	\$/	_ Cost:	\$/
				2.3	Subtotal Ex	cpendable To	oling:	<u>25_\$/load</u>

2.4 Energy

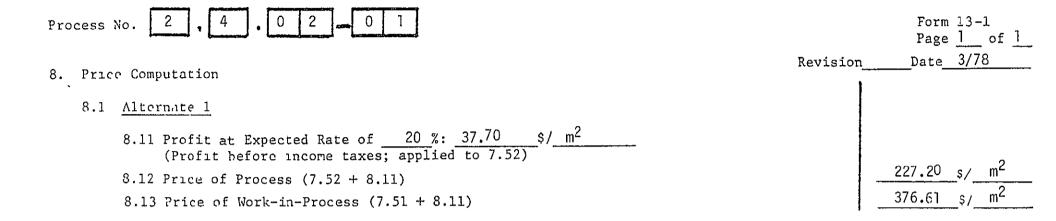
·	Quantity Required: <u>22 kWh/</u>	<u>load</u> : Unit Cost: <u>0.0319</u> \$/ <u>kWh</u> Cost:	_0.70\$/_load
2.4 Type:			
	Quantity Required:	: Unit Cost:\$/ Cost:	\$/
		2.4 Subtotal Energy Costs:	<u>0.70</u> \$/ <u>load</u>
		2.5 Subtotal 2.1 to 2.4;	<u>39.78 \$/ loac</u>
		2.6 Handling Charge: <u>5.26 %</u> of item 2.5	2.09 \$/ <u>loac</u>
		2.7 Subtotal Materials and Supplies: (2.5 + 2.6)	41.87 \$/ load

Proc	ess No.	2.4.02-01		Revision	Form 6 Page <u>1</u> of <u>1</u> Date <u>3/78</u>
3.1	Direct	Labor:			
	3.1_]	Category: <u>Semiconductor Assembler</u> (SAMICS B3096D) Amount Required: <u>0.25</u> h/ <u>load</u>			1.32 \$/load
	3.12	Category: Semiconductor Assembler (SAMICS B3096D) Amount Required: 5.1 h/load		<pre>machine supervision/h; Load36.0%; Cost:</pre>	\$/_load
	3.1 <u>3</u>	Category: <u>Maintenance Mechanic II</u> (SAMICS B3736D) Amount Required: <u>1.4</u> h/ <u>load</u>		blade head changing/adjusting/h; Load36.0%; Cost:	<u>10.80</u> \$/ <u>load</u>
				3.1 Direct Labor Subtotal	39.18_\$/load
3.2		et Labor: Taken as 25% of direct			
	3.2_	Category:			-
	•	Amount Required:h/	; Rate: \$	/h; Load%; Cost:	\$/
	3.2_	Category:	Activity:		
		Amount Required:h/	; Rate: \$	/h; Load%; Cost:	\$/
	3.2	Category:			
		Amount Required:h/	; Rate: \$	/h;-Load%; Cost:	\$/
				3.2 Indirect Labor Subtotal:	9.80 \$/ load
1				3.3 Subtotal 3.1 and 3.2	
				3.4 Overhead on Labor: 5.26 %	2.57 \$/ load
				3.5 Subtotal Labor	51.55 \$/ load
				مسوحة فالمحجور والبالحجين مسترابين كالبشا الأعفاد فترجيب والمحام المتحد والمستجفان وتشوير جديد فتعا بتشابية بتبويته ويحت	

Process No. 2. 4. 0 2 4.1 Equipment	2 - 0 1	Revision_	Form 7 Page <u>1</u> of <u>1</u> Date <u>3/78</u>
4.1_1 Type: <u>Multiblade sl</u> Cost: <u>20,000</u> Plant Oper'g Time_ Servicing Costs: La	licing machine \$; Installation Cost:\$; Throughput: <u>327 los</u> 8280h/y; Machine Avail'ty: <u>90</u> %; Machine Oper'g Time aborh/y at\$/h;Parts or Outside Service: /y; Charge Rate:_ <u>21.35</u> % of Cost/y; Capital Cost:427	h/y \$/y	<u>17.92</u> \$/ <u>load</u>
Cost: Plant Oper'g Time Servicing Costs: L	\$; Installation Cost:\$; Throughput: h/y; Machine Avail'ty:%; Machine Oper'g Time aborh/y at\$/h;Parts or Outside Service: y; Charge Rate:% of Cost/y; Capital Cost:	eh/y \$/y	\$/
Cost: Plant Oper'g Time_ Servicing Costs: L	\$; Installation Cost:\$; Throughput: h/y; Machine Avail'ty:%; Machine Oper'g Time aborh/y at\$/h;Parts or Outside Service: y; Charge Rate:% of Cost/y; Capital Cost:	eh/y \$/y	\$/
	. 4.1 Subtotal Eq	juipment Cost:	<u>17.92</u> \$/ <u>load</u>

Proce	ess No. 2, 4, 0	2 - 0 1						Form 8 Page <u>1</u> of <u>1</u>
4.2	Facilities:						Revision_	Date
	4.2 <u>1</u> Type: <u>Slicing ma</u>	chine area	Floor Area		5.6 m ² ; Throughput:	<u>327 loads</u>	/y	
	Charge Rate:	179.13*	_\$/(m ² ·y):	r -	Maintenance Costs:			
		Energy Use:		-	r:h/y at _	\$/1	n	
	Heating			1	Supplies:	\$/	7	
	Air Cond'g	/y at	\$/	l *	Outside Services:	\$/y	7	
	Lighting	/y at	\$/	<u>ل</u> ے ۔۔۔	Total Cost:	1003.13	\$/y	<u>3.07</u> \$/ <u>load</u>
	4.2 Type:		Floor Area		m ² ; Throughput.		_/y	
	Charge Rate:		_\$/(m ² ·y);	<u> </u>	Maintenance Costs:	میری همینو رو سیس ا		
		Energy Use:	Praya Cray Rains Cay	Labor	::h/y at	\$/}		
	Heating	/v at	\$/		Supplies:	\$/y	,	
	Air Cond'g	/y at	\$/	•	Outside Services:	\$/y		
~	Lighting	/y at		h 1	Total Cost:			\$/
	4.2_ Type:	·····	Floor Area:		m ² ; Throughput:			
	Charge Rate:		_\$/(m ² ·y);		Maintenance Costs:	ينها بينينية حسب الن		
		Energy Use:	annia (kanto dina	Labor	:h/y at	\$/h		
	Heating	/y at	\$/	•		\$/y	ļ	
	Air Cond'g	/y at	\$/	.		<u> </u>		
	Lighting	/y at	\$/		Outside Services: Total Cost:	\$/y	\$/y	\$/
-	*Includes ene	rav use	وي يشير من يوجو ويك الألك التي تيني بين من ال			otal Facilit		3.07 _{S/} load
		<u> </u>						
				l	4.3 Equipment and Facil:	LLES SUDTOT	ал	20.49 \$/ load

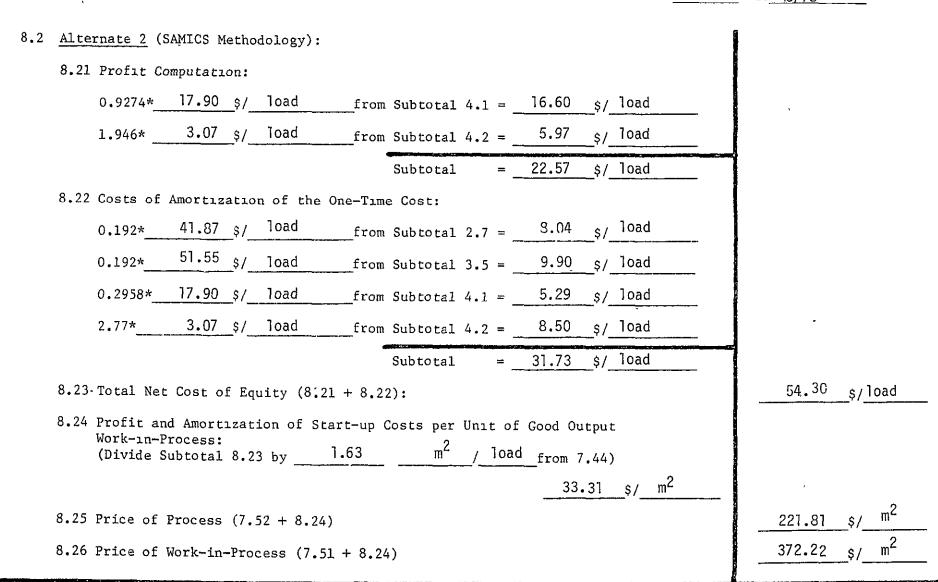
				Form 9-1	
				Page <u>]</u> of	· _]
Pro	cess No	2, 4, 02 - 01	Revision	bate	3/78
5.	Salvag	ed Material (Work-in-process)			
	5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	<u>1.52 k.g</u>	/_load	
	5.21	Input Work-in-process 1. Not Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	<u>1.19 kg</u>	/_load	
	5.22	Net Amount of 5.21 which is sold for Credit As-Is or			
		After Applying Re-Process		/	
	5.23	Credit for 5.22 at the Market Value of\$/:	ş	/	
	5.24	Cost of Reprocessing Material of 5.22 at the Average Reprocessing Cost of\$/:	\$	/	
	5.25	Net Credit for 5.22 (5.23 minus 5.24):			\$/
	5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)	<u>1.19 k.g</u> /	<u>]oad</u>	
	5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)			<u>191.95</u> \$/load_
_	5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)			245.18 s/load
	Salva	led Materials Summary:			-
	5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)	<u>, an </u>	anan manana ang kang kang pang pang kang kang kang kang kang kang kang k	\$/

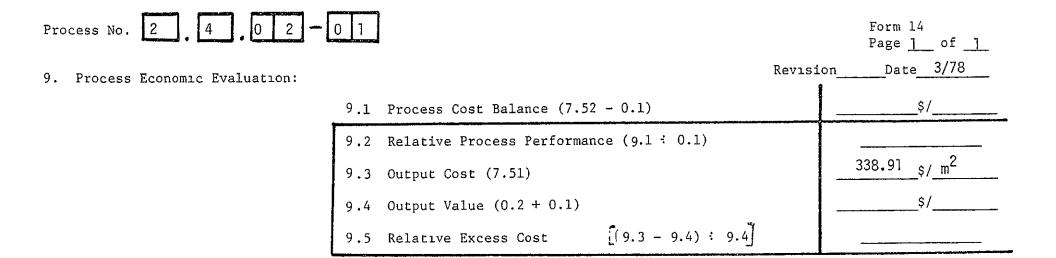


Process No. 2 4 0 2 - 0 1

Form 13-2 Page] of]

Revision Date 3/78





	Contraction of the local division of the loc	1		1 1		() () () () () () () () () ()	1			
Process No.	2		4		0	2	-	0	1	

	Form 19	
	Page <u>]</u>	
Revision	Date	3/78

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0. Output Specification:

.

Name of item: Silicon wafer, as-cut
Dimensions: 5.4-cm in diameter, 0.4 mm thick
Material:
Other Specifications: Depth of subsurface damage is 75 µm

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Process No. 2.4.02-01

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: _____Sheet Generation ______

Subprocess: Ingot Slicing

Option: N

Multiblade Slurry slicing of 7.5-cm diameter

ingots (Spectrolab)

INDEX

Form	Pages	Rev.	Date	<u>Remarks</u>
1				<u>Dates are the same for all forms</u>
2	l to <u>1</u>			
3	1 to <u>0</u>			
4	l to <u>1</u>			
5	l to <u>1</u>			·····
6	1 to <u>1</u>			
7	l to <u>1</u>			
8	l to <u>1</u>			
9-1	1 to <u>1</u>			
9-2	1 to _0			
9-3	1 to _0			
10	1 to _1_			
11	1 to _0			
12	l to <u>1</u>			
13-1	1 to <u>1</u>			
13-2	l to <u>1</u>			
14	1 to <u>1</u>			
15	1 to <u>1</u>			
16	1 to _0			

Form 2

		Page <u>1</u> of <u>1</u>
	Revision	Date <u>3/78</u>
Process No. $2, 4, 02 - 01$	0.1 Value Added:	\$/
Process Description: <u>Multiblade slurry slicing</u>		
Data listed here were obtained from Spectrolab's production experience	ce.	
Blade head has 250 blades and two ingots are sliced per load.		
L. Input Specification:		
Name of Item: Prepared machine load from 2.4 , 01 - 01	<u></u>	
Dimensions: <u>7.5 cm diameter 17 cm long, 3.57 kg/load</u>		
Material.		
Other Specifications:	on a ceramic block.	<u></u>
see 2.4 .01 - 01		
1.1 Quantity Required: 3.49 kg /loac	d Unit Cost: <u>1</u>	54,04_\$/_kg
	1.2 Input Value:	<u> </u>
	1.3 Input Cost:	<u>537.57</u> \$/load

Note to Item 1.3: Use price, if input produced in own plant.

Proc	ess No.	2	. 4 . 0	2 - 0								Form 5)
			ooling:									Page <u>1</u>	of <u>1</u>
	-		-	0 blade	<u>drill pin</u>	<u>pack consis</u>	ting of 0.2 m	<u>n thick</u>	<u>1095 ste</u>	el blades	Revisi	on	Date <u>3/78</u>
			Q	uantity	Required: _	1	pack / load:	Unit C	ost: <u>50</u>	\$/_pacl	çCost:	50	\$/ <u>load</u>
	2.3 _	Type:									-		
			Q	uantity	Required: _	,	/:	Unit C	ost:	\$/	Cost:		\$/
	2.3_	Туре:									-		
			Q	uantity	Required: _		/:	Unit C	ost:	\$/	Cost:		_\$/
	2.3_	Type:					<u></u>				.		
							/:			\$/	Cost:		_\$/
							2.3	Subtot	al Expen	dable Too	ling:	50.00	_\$/_ <u>load</u>
							1 9-99-99-99-99-99-99-99-99-99-99-99-99-9						
2.4	Energy	7											
	2.4 <u>1</u>	Type:	Electrical	, 1 kW	main and a	uxiliary mo	tors		<u></u>		- 1		
			Qu	antity R	equired:	22	kWh/load :	Unit C	ost:0.03	19_\$/ <u>kWh</u>	Cost:	0.70	\$/ <u>load</u>
	2.4_	Type:	·····								_		

Quantity Required:	: Unit Cost:\$/ Cost:	\$/
	2.4 Subtotal Energy Costs:	<u>0.70</u> \$/ <u>load</u>
	2.5 Subtotal 2.1 to 2.4: 2.6 Handling Charge: <u>5.26</u> % of item 2.5	<u>64.76</u> \$/ <u>load</u> <u>3.41</u> \$/ <u>load</u>
	2.7 Subtotal Materials and Supplies: (2.5 + 2.6)	68.17 \$/ load

Process No. 2.4.02-01	Revision	Form 6 . Page <u>1</u> of <u>1</u> Date <u>3/78</u>
3.1 Direct Labor:		
3.1 1 Category: <u>Semiconductor Assembler</u>	Activity: Loading/unloading	
(SAMICS B3096D) Amount Required: 0.25 h/ <u>load</u> ;	Rate: \$ 3.90 /h; Load 36.0 %; Cost:	1.32 \$/load
3.1_ Category: Semiconductor Assembler (SAMICS B3096D)	Activity: <u>machine_supervision</u>	
(SAMICS B3096D) Amount Required: <u>5.2</u> h/load;	Rate: \$ <u>3.90</u> /h; Load <u>36.0</u> %; Cost:	27.59 \$/load
	Activity: <u>blade_head_changing/adjusting</u>	
(SAMICS B3736D) Amount Required: <u>1.4</u> h/ load ;	Rate: \$_5.67 /h; Load_36.0 %; Cost:	10.80 \$/ <u>load</u>
-	3.1 Direct Labor Subtotal:	39.71\$/ <u>load</u>
3.2 Indirect Labor: 25% of direct		
3.2_ Category:	Activity:	
Amount Required:h/;	Rate: \$/h; Load%; Cost:	\$/\$
3.2_ Category:	Activity:	`
Arrount Poquired: h/	Rate: \$ /h; Load %; Cost:	\$/

	Amount Required:	h/	; Rate: \$	/h; Load	%; Cost:		\$/
3.2_	Category:		Activity	۱ <u></u>		,	
—	Amount Required:	h/	; Rate: \$	/h; Load	%; Cost:		\$/
	-			3.2 Indirect 1	Labor Subtotal:	9.93	\$/ <u>load</u>
<u> </u>				3.3 Subtotal	3.1 and 3.2	49.64	\$/ <u>load</u>
				3.4 Overhead	on Labor: <u>5.26 %</u>	2.61	\$/ <u>load</u>
				3.5 Subtotal	Labor	52.25	\$/]oad

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Proc	ess No.	2 4 0 2 - 0 1	Revision		of <u>1</u>
4.1	Equip	nent			3//0
	4.1 <u>1</u>	Type: <u>Multiblade slicing machine</u>			
		Cost: 20,000 \$; Installation Cost: \$; Throughput: 320 loads	_/y;		
		Plant Oper'g Time 8280 h/y; Machine Avail'ty: 90 %; Machine Oper'g Time 7452	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:1592.30	_\$/y		
		Useful Life:y, Charge Rate: 21.35 % of Cost/y; Capital Cost. 4270		18.31	\$/load
	4.1_	Туре:			
		Cost:\$, Installation Cost:\$; Throughput:	_/h,		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs. Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost	\$/y		_\$/
	4.1_	Type:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		_\$/
		4.1 Subtotal Equipmer	nt Cost:	<u>18.31</u>	\$/10ad

	ess No. 2.4.	02-01				Revisi	Form 8 Page <u>1</u> of <u>1</u> on Date <u>3/78</u>
4.2	Facilities:				0		<u> </u>
				5.6	m ² ; Throughput: <u>3</u>	20loads_/y	
	Charge Rate:	179.13*	_\$/(m ² ·y);		Maintenance Costs:		
		Energy Use:		Labor	:h/y at	\$/h	
	Heating	/y at	\$/	•	Supplies:	\$/y	}
	Air Cond'ĝ	/y at	\$/		Outside Services:	\$/y	
i	Lighting	/y at	\$/		Total Cost:	<u>1003.13</u> \$/y	3_13\$/_load
	4.2_ Type ·		_ Floor Area:		m ² ; Throughput:	/y	
	Charge Rate:		_\$/(m ² ·y);	r	Maintenance Costs:		1
	يستر يستيه بتسبير هدي جيمتها	Energy Use:	pangin dinang dinang dinang	Labor	:h/y at	\$/h	
	Heating	/y at	\$/	l	Supplies:	\$/y	
	Air Cond'g	/y at	\$/	ł	Outside Services:	\$/y	
	Lighting	/y at	\$/	┝ ╏	Total Cost:	• •••• •••• •••• •	\$/\$
-	4.2_ Type:		_ Floor Area:		² ; Throughput:	/y	
	Charge Rate:_		_\$/(m ² ·y);	, 	Maintenance Costs:		
	and then share along the	Energy Use:	ana ining ting dag	Labor:	h/y at	\$/h	
	Heating	/y at	\$/	•	Supplies:	\$/y	
	Air Cond'g	/y at	\$/	ł			
	Lighting	/y at	\$/	اسہ میں 1	Outside Services: Total Cost:	\$/y \$/y	\$/
•					4.2 Subto	Stal Facilities:	3.13 \$/load
	*1n	cludes energy use		F	4.3 Equipment and Facili	ities Subtotal :	21.45 \$/load

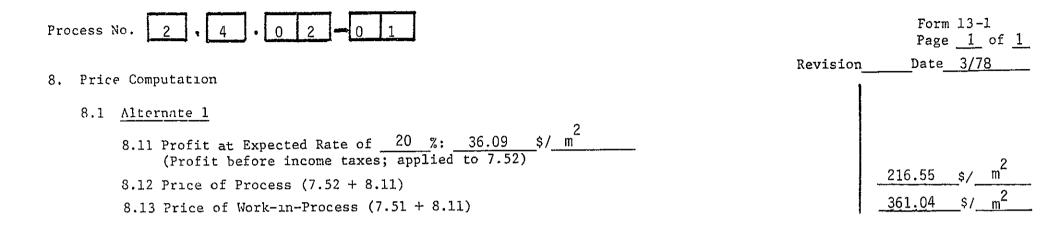
					Form	n 9-1		
					Page	e <u>1</u> of	_1_	
Pro	ocess No	2, 4, 0, 2 - 01		Revisio	on	Date	3/78	
5.	Salvaç	ed Material (Work-in-process)				3		
	5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	1.97	<u>kq</u>	_/ <u>loac</u>	<u>1</u>		
	5.21	Input Work-in-process 1. <u>Not</u> Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	1.53	<u>kg</u>	_/ <u>loac</u>	<u>1</u>		
	5.22	Net Amount of 5.21 which is sold for Credit As-is or After Applying Re-Process						
	5.23	Credit for 5.22 at the Market Value of\$/:	····		\$/			
	5.24	Cost of Reprocessing Material of 5.22 At the Average Reprocessing Cost of\$/:			\$/			
	5.25	Net Credit for 5.22 (5.23 minus 5.24):						_\$/
-	5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)	1.53	kg	/ <u>10ad</u>			
	5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)					235.67	_\$/_ <u>lo</u> a
	5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)					<u>303.44</u>	_\$/ <u>lo</u> a
-	Salvag	ed Materials Summary:						
	5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)			in the second			_\$/

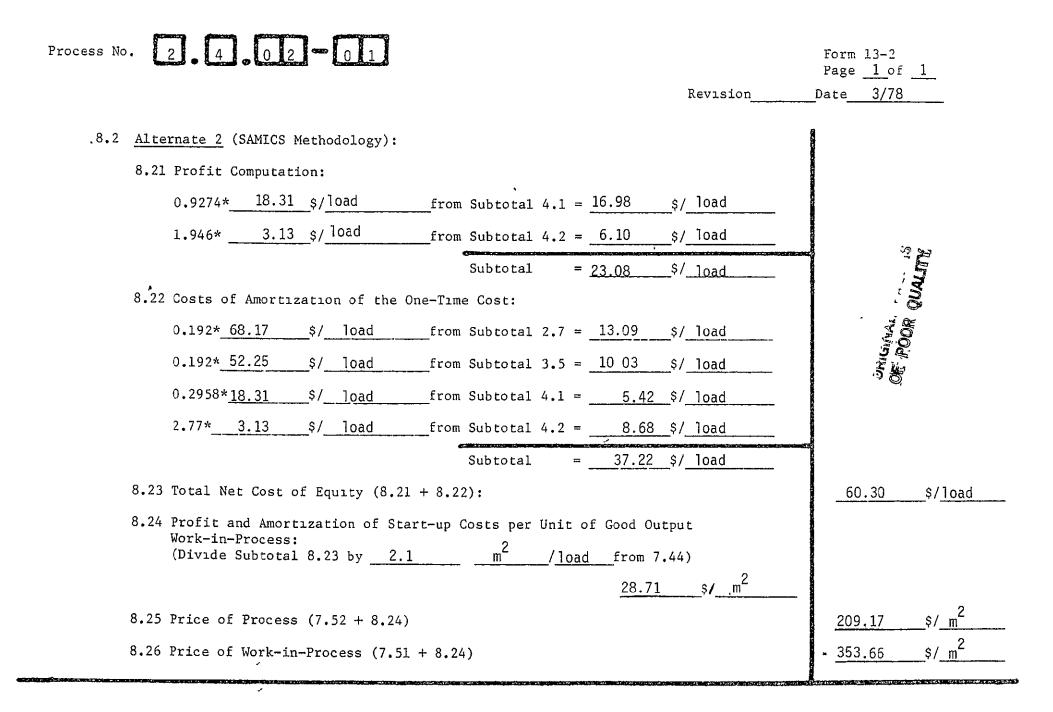
Prod	ess No.	2, 4, 0, 2 - 0, 1			Form 10 Page <u>1 </u> of <u>1 </u>
		ts and Wastes	Re	evision	Date3/78
	6.1 Soli	d Byproducts/Wastes			
	6.1 <u>1</u>	Type (Composition): Silicon chips and dust	Quantity Produced: 0.175	kg/ <u>load</u>	
		Physical Shape/Size:	Energy Content:	kWh/	
		Density: <u>2.34</u> g/cm ³ ; Water Solubility:			
		Toxicity:Biodegradable:	Other Remarks:		
		Type of Disposal:			
		Input Material for:	Cost/(Credit)\$/	, Cost:	\$/
	6.2 Liqu	ıd Byproducts/Wastes (ınorganic):		t	
	6.2_	1 Type (Composition): <u>PC oil slurry</u>	Quantity Produced: <u>7.6</u> &k	/ <u>load</u>	
		Density: 0.95g/cm ³ ; Suspended Solids: <u>SiC abras</u>	ive Amount:0.24 kg/1 pH:	N.A.	
		Toxicity: Heavy Metal Content:	_mg/l Other Remarks:	1	
		Kerf; 1.425 kg/load, concentration 187.6 g/	٤		
		Type of Disposal: can be stored in drums			
		Input Material for:	_Cost/(Credit)_0_\$/_0	Cost;	\$/
				Carry:	'\$ <i>1</i>
				Carry:	¥/

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Form 12 Page<u>1</u>of<u>1</u>

Process No. 2. 4. 02-01	RevisionDate_	3/78
. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	<u>141.87</u> \$/load
	7.22 Other Indirect Costs:% of 7.11 (0.059 x (4.1) + 108x(4. 2))	<u> 1.418 </u> \$/load
	7.21 Total Operating Add-on Costs of Process:	<u>143.29</u> \$/ <u>load</u>
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	<u>143.29</u> \$/ <u>load</u>
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	_235.67_\$/_load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	<u>378.96</u> \$/ load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	<u>303.44</u> \$/_load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	<u>682.40 \$/ load</u>
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu		
7.42 Practical Yield	95%	
7.43 Effective Yield (7.41 x 7.42)	$0.60 \text{ m}^2 / \text{kg}$	
7.44 Number of Units of Good Output Wor Computation Unit Used up to 7.35	rk-in-Process per2.10 m ² / load	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	<u>324.95</u> \$/ m ²
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	<u>180.46</u> \$/_m ²





Process No. 2 . 4 . 0 2 - 0 1

9. Process Economic Evaluation:

Pro	cess No. 2 4 0 2 0 1	,	Form 15 Page <u>1 of 1 </u>
		Revision	Date3/78
0.	Output Specification:		
	Name of item: <u>Silicon wafer, as-cut</u>		
	Dimensions: 7.5-cm in diameter and 0.4 mm thick		,,
	Material:high purity silicon		
	Other Specifications:		
	subsurface damage depth is 75 µm		
		<u> </u>	
~		NGINE -	
\mathbf{i}		TE O	
$\dot{\gamma}$		QUAL S	<u></u>
ł		75	
	I	······································	·····
			· · · · · · · · · · · · · · · · · · ·

Process	No. 2 4	02	-03	Form 1		
University of Pennsylvania <u>PROCESS CHARACTERIZATION</u> (UPPC)						
Pro	cess: Sheet	generat				
Sub	process: Ingot	slicing				
Opt	ion: <u>ID fi</u>	xed - ab	<u>rasive sli</u>	cing,		
	10.16	cm diam	eter, ingot	s (HAMCO)		
	<u>ر با</u>	12.1 11.1 1.1	<u>ÍNDEX</u>			
Form	<u>Pages</u>	<u>Rev.</u>	Date	<u>Remarks</u>		
1			4/78	All forms have same date		
2	1 to _]					
3	1 to <u>0</u>					
4	1 to <u>1</u>					
5	1 to <u>1</u>					
6	1 to					
7	l to					
8	l to					
9-1	1 to <u> </u>		·			
9-2	1 to _0_					
9-3	1 to <u>0</u>			·		
10	1 to <u>1</u>					
11	1 to <u>1</u>					
12	1 to <u>1</u>		·			
13-1	1 to <u>1</u>					
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14	1 to <u>1</u>					
15	1 to <u>1</u>					
16	1 to _0					

Form	2
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				Page] of]
			Revision	Date <u>4/78</u>
Pro	cess No. 2.4,	0 2 - 0 3	0.1 Value Added:	\$/
Pro	cess Description:	Inner diameter slicing of 10.16 cm diameter ingots.		
		Analysis derived from data supplied by HAMCO.		
		555 slices made per load.		
				
1.	Input Specification:			
	Name of Item:	Prepared machine load from 2.4 : 01 : 03		
	Dimensions:	10.16-cm in diameter, 46-cm long, 8.72 kg/load		
	Material:	High purity silicon		
	Other Specifications	: See 2.4.01-03		
	<u></u>			
			ىرىمى ئىلى يەرىپى بىلەر يەرىپى بىرى بىلەر يەرىپ بىلەر يەرىپ بىلەر يەرىپ يەرىپ يەرىپ يەرىپ يەرىپ	
	<u>a. a. 1944. ila 1977. a. 19</u> 79. ^{a.} 1979. a. 1979. a. 1979.			
	<u></u>	1.1 Quantity Required: 8.726 kg / load	Unit Cost: 1	49.31_\$/_kgr-s
			1.2 Input Value:	<u>1302.90 \$/ load</u>
			1.3 Input Cost:	\$/
			harten an er	

Note to Item 1.3: Use price, if input produced in own plant.

Process No	2.4.02-03		Form 4
			Page <u>1</u> of <u>1</u>
2.2 Indir	rect Materials (incl. supplies and non-energy utilities):	Revision	Date4/78
2.2]	Type: Coolant	;	
•	Specification: Filtered domestic wafer with Rust-Lick		
	80:1 water to Rust-Lick ratio		
	Quantity Regulred: 1 gallon /load; Unit Cost: 3.65 s/ ga	11ons Cost:	3.65 \$/ load
2.2_2	2 Type· _Blade dressing		
	Specification:Alumina_stick		
	Quantity Required	2; Cost:	3.15 s/ load .
2.2_	Type:		
	Specification:		
	Quantity Required: / _; Unit Cost:\$/	; Cost:	\$/
	2.2 Subtotal Indire	ct Materials:	6.80 \$/load

Proc	ess No. 2	4.02-03					Form 5
2.3	Expendable T	ooling:					Page <u>1</u> of <u>1</u>
	2.3 <u>1</u> Type:	ID blade, diamond plated				Revisi	on Date_4/78
	2.3 _ Type:	Quantity Required: blade	/load	Unit Cost: _	55_\$/bla	deCost:	<u> 55 \$/ load </u>
	2.3_ Type:	Quantity Required:	/:	Unit Cost: _	\$/	Cost:	\$/
	-	Quantity Required:	/:	Unit Cost:	\$/	Cost:	\$/
	······	Quantity Required:	/:	Unit Cost:	\$/	_ Cost:	\$/
	•		2.3	Subtotal Expe	endable To	oling:	55 \$/ <u>10ad</u>

2.4 Energy

2.4 _ Type:	Quantity Required:	46.2 kWh/load : Unit Cost:032 \$/ kWh Cost:	<u>1.48</u> \$/ <u>load</u>
	Quantity Required:	: Unit Cost:\$/ Cost: 2.4 Subtotal Energy Costs:	\$/].48 _{\$/} load
		2.5 Subtotal 2.2 to 2.4; 2.6 Handling Charge: <u>5.26 %</u> of item 2.5	63.28 \$/ load 3.32 \$/_load
		2.7 Subtotal Materials and Supplies: (2.5 + 2.6)	\$/load

Process No. 2 4 0 2 0 3 Revision	Form 6 Page <u>1</u> of <u>1</u> Date <u>4/78</u>
3.1 Direct Labor:	
. 3.1] Category: <u>Semiconductor Assembler</u> <u>Activity: Loading/unloading</u> (SAMICS B3096D)	
Amount Required: 0.083 h/load ; Rate: \$ 3.89 /h; Load 36.0 %; Cost:	0.439 \$/ <u>load</u>
3.1_2 Category: <u>Semiconductor Assembler</u> <u>Activity: Machine supervision</u>	
(SAMICS B3096D) Amount Required: <u>4.3</u> h/ <u>load</u> ; Rate: \$ <u>3,89</u> /h; Load <u>36.0</u> %; Cost:	22.81 \$/ load
3.1 <u>3</u> Category: <u>Maintenance Mechanic</u> <u>Activity: Blade head changing</u> (SAMICS B3736D)	
(SAMICS B3/36D) Amount Required: 0.80 h/load ; Rate: \$ 5.67 /h; Load 36.0 %; Cost:	<u>6.17</u> \$/ <u>load</u>
3.1 Direct Labor Subtotal:	29.42 \$/load
3.2 Indirect Labor: Taken as 25% of direct	
3.2_ Category:	
Amount Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2_ Category:	-
Amõunt Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2 Category:Activity:	
Amount Required:h/; Rate: \$/h; Load%; Cost:	<u>\$/</u>
3.2 Indirect Labor Subtotal:	7.35 \$/ load
3.3 Subtotal 3.1 and 3.2	<u>36.77 \$/ load</u>
3.4 Overhead on Labor: <u>5.26</u> %	<u>1.93</u> \$/ <u>load</u>
3.5 Subtotal Labor	<u>38.70 \$/ load</u>

•

Process No	. 2 . 4 . 0 2 - 0 3	-		_ of _]
4.1 Equip	ment	Revision_	Date	4/78
4.1_7	Type:ID_saw_slicing_machine			
	Cost: 40,000 \$; Installation Cost: \$; Throughput: 325	_/k;y		
	Plant Oper'g Time8280h/y; Machine Avail'ty:95_%; Machine Oper'g Time786	6h/y		
	Servicing Costs: Laborh/y at\$/h;Parts or Outside Service 285.71	_\$/y		
	Useful Life:y; Charge Rate 21.4_% of Cost/y; Capital Cost:8560	\$/y	27.21	\$/ <u>load</u>
4.1_	Туре:			
	Cost:\$; Installation Cost:\$; Throughput:	_/h;		
	Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
	Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
	Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		\$/
4.1_	Type:			
oìr−	Cost:\$; Installation Cost:\$; Throughput:	_/h;		
GRIGINAL B POOR	Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
NAL NAL	Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
PAGE I QUALITI	Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		_\$/
Ĵ.	4.1 Subtotal Equipmen	t Cost:	27.21	_\$/load

*

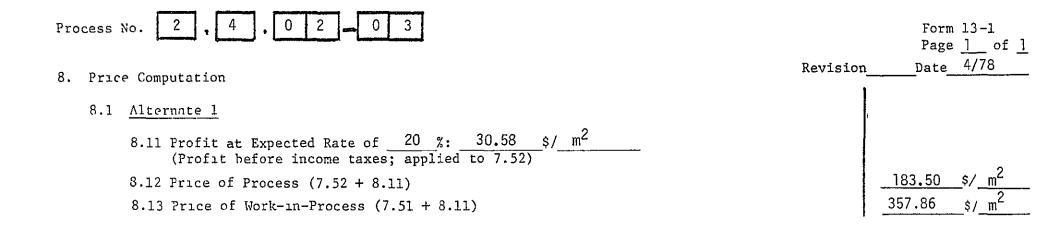
Proc	ess No. 2.4.	0 2 - 0 3						Form 8 Page <u>1</u> of <u>1</u>
4.2	Facilities:						Revision	Date <u>4/78</u>
~	4.2] Type: <u>Machine</u>	area	_ Floor Area:	9.0	m ² ; Throughput:	325 loads	/y	
:	Charge Rate:	. 179.13*	$_{(m^2 \cdot y);}$	- -	Maintenance Costs:			
	··· •• •• •••••	Energy Use:			r:h/y at _	\$/	h	
	Heating	/y at	\$/	ł	Supplies:	\$/	y ,	
	Air Cond'g	/y at	\$/		Outside Services;	\$/	y	
	Lighting	/y at	\$/	└── <u>─</u> ─	Total Cost:	1612	\$/y	4.96 \$/load
	4.2_ Type:		_ Floor Area:		m ² ; Throughput:		/y	
	Charge Rate:	dentale danna gerado destado	\$/(m ² ·y);	r	Maintenance Costs:		•	
		Energy Use:		Labo	h/y ath	\$/1	h	
	Heating	/y at	\$/	l 1	Supplies:	\$/:	y I	
	Air Cond'g	/y at	\$/	ŧ 1	Outside Services:	\$/	<i>y</i>	
	Lighting	/y at	\$/	} 	Total Cost:	•	_\$/y	<u> </u>
	4.2 Type:		_ Floor Area:		m ² ; Throughput:		/y	
	Charge Rate:		\$/(m ² ·y);	 	Maintenance Costs:			
	and this to a second the second the	Energy Use:	inter grapp gauge data	l Laboi	:h/y at	\$/1	. I	
	Heating	/y at	\$/	•		\$/3		
	Air Cond'g	/y at	\$/	•			l l	
	Lighting	/y at	\$/	╘ _┺ ┙╴╺╸ ╊	Outside Services: Total Cost:	\$/1	\$/y	\$/
•		an a		Č	4.2 Subt	otal Facilit		4.96 _{\$/} load
					4.3 Equipment and Facil	ities Subtot	al:	32.17 \$/ load
	·	-						

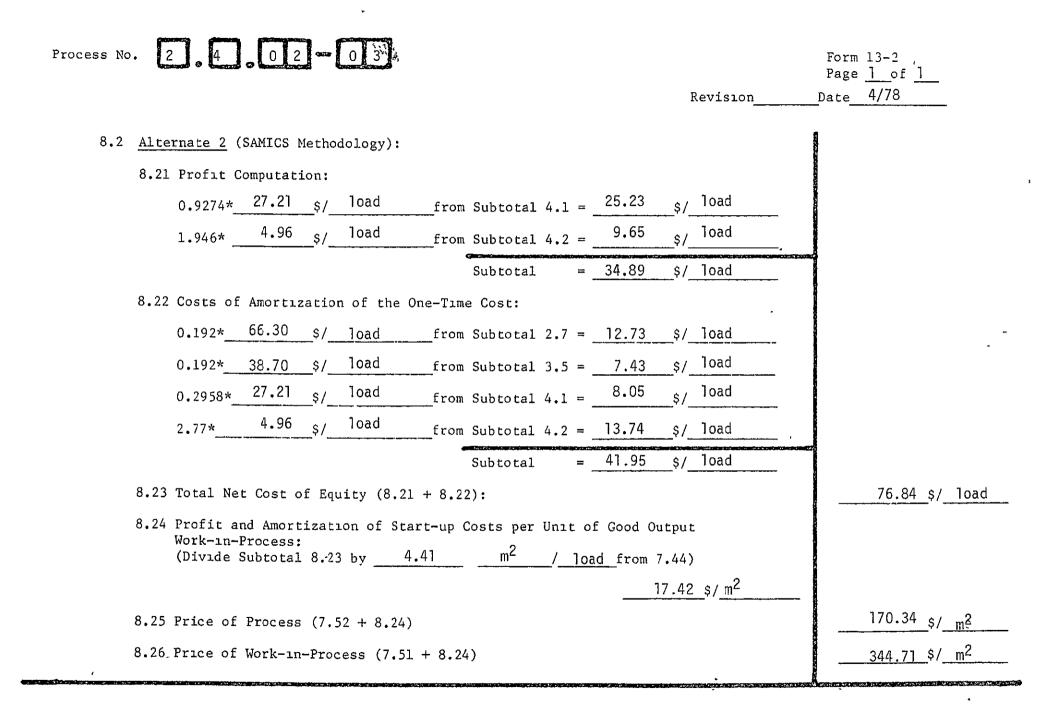
*Includes energy use

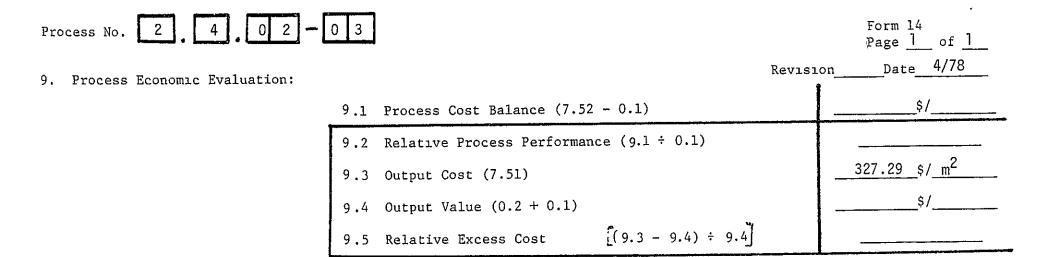
				Form	9-1		
				Page	l_of	1	
cess No	2, 4, 02 - 03	Re	evision	<u></u>	Date	4/78	
Salvag	ed Material (Work-in-process)						
5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	5.15	kg/	load			
5.21	Input Work-in-process 1. Not Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	3.57	kg	/ load			
5.22	Net Amount of 5.21 which is sold for Credit As-Is or						
	After Applying Re-Process		/	′	_		
5.23	Credit for 5.22 at the Market Value of\$/:	<u></u>	\$/	/			
5.24	Cost of Reprocessing Material of 5.22 at the Average Reprocessing Cost of\$/:	•	\$,	/			
5.25	Net Credit for 5.22 (5.23 minus 5.24):						_\$/
5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)		/			a construction of the second	
5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)		-			533.04	\$/
5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)					768.95	_\$/_]
Salvag	ed Materials Summary:						
5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)						_\$/

Pro	cess No.	2 - 4 - 0 - 0 - 3			Form 10 Page <u>1</u> of <u>1</u>
6.	Byproduct	s and Wastes		Revision	Date//8
	6.1 Solid	Byproducts/Wastes			
	6.1_1	Type (Composition): Silicon chips and dust	Quantity Produced: 0.	105 kg/ 10ad	
		Physical Shape/Size:	Energy Content:	kWh/	
		Density: 2.34 g/cm ³ ; Water Solubility: 0	_g/l at ⁰ C;	рН:	
		Toxicity:Biodegradable:	Other Remarks:		
		Type of Disposal:			
		Input Material for:	Cost/(Credit)\$/	; Cost:	\$/
	6.2 Liqui	d Byproducts/Wastes (inorganic):			
	6.2 <u></u> 1	Type (Composition): water and silicon kerf	_ Quantity Produced:_30	0_l/_load_	
		Density:g/cm ³ ; Suspended Solids: <u>3.47 kg/load</u>	Amount: <u>11.6</u> g/l]	pH:	
		Toxicity: Heavy Metal Content:	_mg/1 Other Remarks:		
		Type of Disposal:			
		Input Material for:		Cost:	\$/
				Carry:	\$/
				Gallyi	· · · · · · · · · · · · · · · · · · ·

	Form Page	12 1_of_1_
ocess No. 2.4.02-03	Revision Date4/78	
Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	<u>137.17 \$/load</u>
	7.22 Other Indirect Costs:% of 7.11 0.059*(4.1)+0.108*(4.2)	\$/load
	7.21 Total Operating Add-on Costs of Process:	<u>139.32</u> \$/load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	<u>141.36</u> \$/ <u>load</u>
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	<u>533.04</u> \$/ <u>load</u>
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	<u>674.40 \$/load</u>
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	<u>768.95 \$/load</u>
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	1443.35 \$/ load
7.41 Theoretical Yield (or Conversi work-in-process do not equal i		
7.42 Practical Yield	%%	
7.43 Effective Yield (7.41 x 7.42)	0.505 m ² /kg	
7.44 Number of Units of Good Output . Computation Unit Used up to 7.		
	7.51 Cost of Únit of Good Output Work-in- Process (7.37 ÷ 7.44)	327.29 \$/ m ²
	7.52 Specific Add-On Cost per Unit of Good	152.92 _{s/} m ²







Process No. 2	4 0 2 0 3	Revision	Form 15 Page <u>1</u> of <u>1</u> Date <u>4/78</u>
). Output Specific	cation:	Rev 191011	
Name of item:	Silicon wafers, as cut		
Dimensions:	10.16 cm in diameter, 0.50 mm thick		
Material:	Silicon		
Other Specifica	tions:		
<u></u>			
- <u></u>			
····			
<u></u>		- <u></u>	
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<u></u>			
		<u> </u>	

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process:	Sheet	generation	 	
Subprocess:	Wafer	generation		

Option: STC Current Production

ID Slicing (10-cm diameter wafers)

INDEX

Form	Pages	Rev.	Date	Remarks
1			8/78	All forms have same date
2	1 to <u>0</u>			
3	1 to <u>1</u>		. <u></u>	
4	1 to _1		. <u></u>	
5	1 to <u>1</u>			
6	1 to			
7	1 to <u>1</u>			
8	l to <u> </u>			
9-1	l to <u> </u>			
9-2	1 to <u>1</u>			
9-3	1 to <u>1</u>			
10	1 to <u>0</u>			
11	1 to <u>0</u>			
12	1 to <u>1</u>			
13-1	1 to <u>1</u>			
13-2	1 to <u>1</u>			
14	1 to <u>0</u>			
15	l to <u> </u>			
16	1 to _0_			

,

				Form 2
				Page <u>l</u> of <u>l</u>
			Revision	Date 8/78
Pro	cess No. 2.	$4 \cdot 0 2 - 0 3$	0.1 Value Added:	\$/
Pro	cess Descriptio	n: Inner diameter slicing as performed commercially by STC	's ID slicing machine	2
			·····	
				<u></u>
	T			
1.	Input Specific		-	
		Single crystal silicon ingot, prepared as specified in 2.4-0	<u> -</u>]7·	
	Dimensions:	10-cm diameter, 60 cm long, 11.027 kg		
	Material:	high purity silicon		
	Other Specific	ations:		
	Office officiarie			
				<u></u>
			<u></u>	
		1.1 Quantity Required: 11.027 kg load	Unit Cost:]	19.45 \$/ <u>kg</u>
	<u> </u>			
			1.2 Input Value:	<i>میدیک میں پینی ہے۔ یہ جس میں میں کی جو پر میں ہوتا ہے۔ اور اور اور اور اور اور اور اور اور اور</i>
			1.3 Input Cost:	

Note to Item 1.3: Use price, if input produced in own plant.

Process No. 2 . 4 . 0 2 - 0 3 2.2 Indirect Materials (incl. supplies and non-energy utilities): Revision Date 2.2 Type: Misc. materials	
2.2_1 Type:;	
Specification: Includes: alumina sticks, mounting epoxy, graphite mounting bar, etc.	
Quantity Required:/; Unit Cost:; Cost:	/_load
2.2 ² Type Coolant	
Specification: 80:1 water to Rustlick	
Coolant is recycled and filtered so that consumption/load is	
negligible. Flow rate is 7 %/h	
Quantity Required:	/
2.2_ Type:	
Specification:	
-	
Quantity Required: / _; Unit Cost:\$/; Cost:\$	/
2.2 Subtotal Indirect Materials: 2.50 \$	/load

			$\boxed{4} \cdot \boxed{02} - \boxed{03}$			Form 5 Page <u>1</u> of <u>1</u>
2.3	_		Tooling:		Revisior	n Date8/78
	2.3 _1		STC-22 ID diamond coated blade			
			Quantity Required: 0.1667 blade	/load: Unit Cost: <u>110</u> \$/ <u>b1</u>	<u>ad</u> eCost:	<u> 18.33</u> \$/ <u>load</u>
	2.3_					
			Quantity Required:	/: Unit Cost:\$/	Cost: _	\$/
	2.3_	Type:		· · · · · · · · · · · · · · · · · · ·		
			Quantity Required:	: Unit Cost:\$/	Cost:	\$/
	2.3					
			Quantity Required:		Cost:	<u>\$/</u>
				2.3 Subtotal Expendable T		18.33 s/ load
2.4	Energ	y				
	2.4]	Type:	Power consumption is 2 kW, running time is	35.7 h.	- 1	
			Quantity Required:71.4 kWh/1	oad : Unit Cost: 0.0319\$/kW	<u>h</u> Cost:	2.28 \$/ load
., 4	2.4_	Type:	Quantity Required:			
· · · · · · · · · · · · · · · · · · ·			Quantity Required:	: Unit Cost:\$/	Cost: _	\$/
				2.4 Subtotal Energy	Costs:	2.28 \$/ load
		<u></u>		2.5 Subtotal 2.2 to 2.4;		23.11 \$/ load
				2.6 Handling Charge: 5.26 % of	item 2.5	1.22_\$/ <u>load</u> _
				2.7 Subtotal Materials and Suppl (2.5 + 2.6)	Lies:	24.33 \$/ <u>load</u>

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Process No. 2 4 0 2 0 3		Revision	Form 6 Page <u>1</u> of <u>1</u> Date <u>8/78</u>
3.1 Direct Labor:			
3.1_] Category: <u>Semiconductor Assembler</u>	Activity:	Machine mounting/demounting	
(SAMICS B3096D) Amount Required: 0.5 h/ load	; Rate: \$ <u>3,89</u>	_/h; Load36.0%; Cost:	2.65 \$/ <u>load</u>
3.1_2 Category: <u>Semiconductor Assembler</u>	Activity:	Machine_supervision	
(SAMICS B3096D) Amount Required: 2.5 h/ load			\$/_load
3.1 ³ Category: <u>Maintenance Mechanic</u>	Activity:	Cutting tool change	
(SAMICS B3736D) Amount Required: 0.5 h/ load			3.86\$/_load
		3.1 Direct Labor Subtotal:	19.74 \$/load
3.2 Indirect Labor: Taken as 25% of direct			
3.2_ Category:	Activity:		
Amount Required:h/	; Rate: \$	/h; Load%; Cost:	\$/
3.2_ Category:	Activity:		
Amount Required:h/	; Rate: \$	/h; Load%; Cost:	\$/
3.2_ Category:	Activity:	······	
Amount Required:h/			\$/
		3.2 Indirect Labor Subtotal:	4.93\$/_load
		3.3 Subtotal 3.1 and 3.2	24.67 \$/ load
		3.4 Overhead on Labor: 5.26 %	\$/_load
		3.5 Subtotal Labor	\$/_load

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Process No. 2 . 4 . 0 2 - 0 3	vision	Form 7 Page <u>1</u> of <u>1</u> Date <u>8/78</u>
4.1 Equipment	1	
4.1_] Type: <u>STC ID slicing machine</u>		
Cost: 40,000 \$; Installation Cost:\$; Throughput: 224 loads /k	;y	
Plant Oper'g Time8280h/y; Machine Avail'ty:99_%; Machine Oper'g Time8197.2	h/y	
Servicing Costs: Labor52h/y at_8.12\$/h;Parts or Outside Service:300\$/;	у	
Useful Life: 7 y; Charge Rate: 21.35 % of Cost/y; Capital Cost: 9262.25	\$/y	41.34 \$/ 10ad
4.1_ Type:		
Cost:\$; Installation Cost:\$; Throughput:/h	;	
Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y	
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:\$/	у	
Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:		\$/
4.1_ Type:		
Cost:\$; Installation Cost:\$; Throughput:/h	ı ;	
Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y	
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:\$/	У	
Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:		\$/
4.1 Subtotal Equipment C	Cost:	41.34 \$/_load

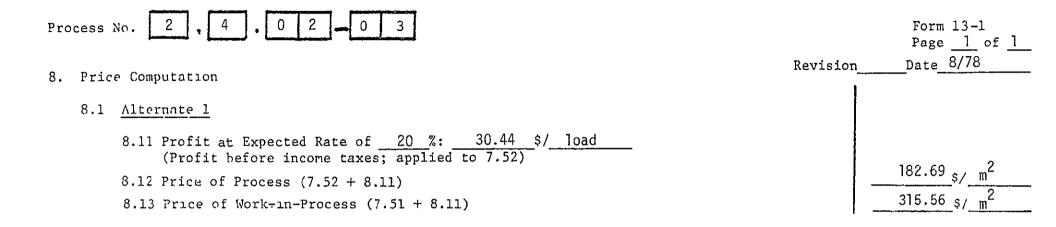
Proc	ess No. 2.4.	02-03						Form 8 Page] of]
4.2	Facilities:						Revision_	Date <u>8/78</u>
	4.2 <u>1</u> Type: <u>ID machin</u>	e area	_ Floor Area:	7.5	m ² ; Throughput:	224 loads	/y	
	Charge Rate:	179.13* Energy Use:	-		Maintenance Costs: h/y at	\$/	h	
	Heating	/y at	\$/ \	S	Supplies:	\$/	y	
	Air Cond'g	/y at	\$/	С	utside Services:	\$/	у	
	Lighting	/y at	\$/ I	· · · · · · · · · · · · · · · · · · ·	Total Cost:	1343.48	\$/y	6.00 \$/load
	4.2_ Type:		_ Floor Area:		_m ² ; Throughput:		_/y	
	Charge Rate:		_\$/(m ² ·y);	 M	laintenance Costs:			
		Energy Use:		Labor:	h/y at _	\$/:	h	
	Heating	/y at	\$/	S	upplies:	\$/	у	
	Air Cond'g	/y at	\$/ i	C	utside Services: _	\$/	у	
	Lighting	/y at	\$/ I		Total Cost:		\$/y	\$/
	4.2_ Type:		_ Floor Area: _		_m ² ; Throughput:	······	/ y	
	Charge Rate:		\$/(m ² ·y);	• • M	laintenance Costs:			
	Heating	Energy Use:	11	Labor:	h/y`at	\$/1	n	
		/y at/y at		S	upplies:	\$/	y	
	Lighting	/y at/y at	ļ	0	utside Services:	\$/	у	
		/y at	?/ 1		Total Cost:		_\$/y	\$/
	* Includes energy us	se			4.2 Sub	total Facilit	ies:	6.00 ş/load
				4.	3 Equipment and Faci	lities Subtot	al:	47.35 \$/load

				Form	9-1	
				Page	<u>]</u> of	1
Process	No. $2 \cdot 4 \cdot 0 \cdot 2 - 0 \cdot 3$		Revision		Date	8/78
5. Salv	aged Material (Work-in-process)					
5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	5.453	kg	/load		
5.21	Input Work-in-process 1. Not Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	5.574	kg	/load		
5.22	Net Amount of 5.21 which is sold for Credit As-Is or After Applying Re-Process			/		
5.23	Credit for 5.22 at the Market Value of\$/:		\$	/		
5.24	Cost of Reprocessing Material of 5.22 At the Average Reprocessing Cost of\$/:	<u> </u>	\$	/		
5.25	Net Credit for 5.22 (5.23 minus 5.24):					\$/
5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)	5.574	kg_/	load		an a
5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)					833.03 \$/ load
5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)	-				814.95 _s/_load
Salv	aged Materials Summary:		- A 19 Area	2019 Aur 191		
5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)					\$/

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		rm 12 ge_l_of_l
ocess No. 2.4.02-03		te
Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6	.)97.65.\$/_load
	7.22 Other Indirect Costs: $% \text{ of } 7.11$	2.98 _{\$/_} load
	7.21 Total Operating Add-on Costs of Process:	_100.63 \$/ load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	_100.63 \$/ load
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	<u>833.03</u> \$/ load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)933.66 \$/load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	814.95 \$/ load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	1748.61 \$/ load
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu	Rate, if output units of	na California de California
7.42 Practical Yield	%	
7.43 Effective Yield (7.41 x 7.42)	0.556 m ² / kg	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	ork-in-Process per6.133 m ² / load	
	7.51 Cost of Unit of Good Outpu t Work-in- Process (7.37 ÷ 7.44)	\$/_m ²
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	$\frac{285.11 \text{ s/ } \text{m}^2}{152.24 \text{ s/ } \text{m}^2}$
		1



Procéss No. 2 4 02 0 3 Revision_____Date__8/78

8.2 <u>Alternate 2</u> (SAMICS Methodology):	
8.21 Profit Computation:	
0.9274* 41.34 \$/ load from Subtotal 4.1 =	
1.946* 6.00 \$/ load from Subtotal 4.2 = 11.68 \$/ load	
Subtotal = 50.02 \$/ load	
8.22 Costs of Amortization of the One-Time Cost:	
0.192* 24.33 \$/ load from Subtotal 2.7 = 4.67 \$/ load	
0.192* 25.47 \$/ load from Subtotal 3.5 = 4.98 \$/ load	
0.2958* 41.34 \$/ load from Subtotal 4.1 = 12.23 \$/ load	
2.77* 6.00 \$/ load from Subtotal 4.2 = <u>16.62</u> \$/ load	
Subtotal = 38.50 \$/ load	1
8.23 Total Net Cost of Equity $(8.21 + 8.22)$:	88.52 \$/ load
8.24 Profit and Amortization of Start-up Costs per Unit of Good Output Work-in-Process: (Divide Subtotal 8.23 by <u>6.133</u> m ² / load from 7.44) 14.43 \$/ m ²	-
8.25 Price of Process (7.52 + 8.24)	166.67 \$/ m ²
8.26 Price of Work-in-Process (7.51 + 8.24)	\$/_m ²

Form 13-2 Page <u>1</u> of <u>1</u>

Process No.	2, 4, 02 - 01		Form 10 Page <u>]</u> of <u>]</u>
6. Byprodu	cts and Wastes	Revision	Date3/78 ,
6.1 Sol	ld Byproducts/Wastes		
6.1] Type (Composition): Silicon chips Quantity Prod	uced: <u>0.14 kg</u> / <u>load</u>	
	Physical Shape/Size Energy Conten	t:kWh/	
	Density: 2.34 g/cm ³ ; Water Solubilityg/l at	°C: pH:	
	ToxicityBiodegradable:Other Remarks:		
	Type of Disposal.		
	Input Material for Cost/(Credit)		\$/
6.2 Liq	and Byproducts/Wastes (inorganic):		
6.2] Type (Composition): <u>PC 011 with abrasive</u> Quantity Prod	uced: <u>7.6 ^{&}/_load</u>	
	Density: <u>~0.95</u> g/cm ³ ; Suspended Solids: <u>SiC abrasive</u> Amount:	_mg/1 pH:	
	Toxicity: Heavy Metal Content:mg/1 Other Re Slurry oil also contains Si kerf at a concentration of 145 g/g	marks:	
	Type of Disposal:		
	Input Material for:Cost/(Credit)		\$/
	_	Carry:	\$/

	Form Page	12 of
Process No. 2 . 4 . 0 2 - 0 1	RevisionDate	3/78
7. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	<u>113.91 \$/ load</u>
	7.22 Other Indirect Casts: (4.2) of 7.11	<u> 1.39 \$/ load </u>
	7.21 Total Operating Add-on Costs of Process:	115.30 \$/ load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	<u>115.30 s/ load</u>
	7.32 Credit for Salvaged Material (5.8)	\$/\$/
	7.33 Cost of Work-in-Process Lost (5.3)	<u>191.95 \$/ load</u>
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	307.25 \$/ load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	245.18 \$/ load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	552.42 \$/ load
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu	Rate, if output units of	
7.42 Practical Yield	<u>95</u> %	
7.43 Effective Yield (7.41 x 7.42)	<u> 0.6 m² / kg</u>	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	rk-in-Process per <u>1.63 m² / load</u>	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	<u>33891 \$/m²</u>
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	188-50 \$/_m ²
		1

Process No. 2 4 0 2 - 0 3		Form 15 Page <u>1</u> of <u>1</u>
	Revision	Date8/78
). Output Specification:		
Name of item:		
Dimensions: 10 cm diameter, 380 µm thick,		-
Material:		
Other Specifications. 350 μ m kerf, 822 wafers/load		
	······································	
		······································
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University of Pennsylvania

PROCESS CHARACTERIZATION

(ŨPPC)

Process: Sheet generation

Subprocess: Ingot Slicing

Option: ID fixed abrasive slicing of 10.16 cm

diameter ingots as performed by OCLI and projected for 1982

INDEX

Form	Pages	Rev.	Date	Remarks
1			3/78	<u>All forms have same date.</u>
2	1 to <u>1</u>			
3	1 to <u>0</u>			
4	1 to <u>1</u>			
5	1 to]		·`	· · · · · · · · · · · · · · · · · · ·
6	1 to <u>1</u>			
7	1 to <u>1</u>			
8	1 to <u>1</u>			
9-1	1 to <u>1</u>			
9-2	1 to]			
9-3	1 to <u>0</u>			
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13-1	1 to <u>1</u>			
13-2	l to <u>1</u>			
14	1 to <u>1</u>			
15	1 to <u>1</u>			
16 <i>,</i>	1 to <u>0</u>			

Form	2
------	---

				Page <u>l</u> of <u>l</u>
			Revision	Date <u>3/78</u>
Process N	o. 2.	4 . 0 2 - 0 3	0.1 Value Added:	<u> </u>
Process]	Description:	Inner diameter slicing,		
<u>.</u>		as demonstrated by OCLI using a STC-22 diamond impre	egnated blade	
		(55.88-cm OD, 20.32-cm ID, 0.15 mm thick core with a	a 0.3336 mm total thic	kness),
<u>, , , , , , , , , , , , , , , , , , , </u>	······································			
. Inpu	t Specificat	ion:		
Name	of Item:	Prepared machine load from 2.4 : 01 : 03		
Dime	nsions:	10.16 cm in diameter, 25 cm long, 4.74 kg silicon cryst	tal ingots	
	rial:	High purity silicon.		
		cions:Single_crystal_ingot		
o cire.	I OPECIFICA			
<u></u>				

, , 				
s;				
هن 		1.1 Quantity Required: <u>4.74 kg / loac</u>	d Unit Cost:	72.22 \$/ <u>kg</u>
s); 		1.1 Quantity Required: <u>4.74 kg / loac</u>	d Unit Cost: 1.2 Input Value:	72.22 \$/ <u>kg</u>

Note to Item 1.3: Use price, if input produced in own plant.

ocess No.	$2 \cdot 4 \cdot 0 \cdot 2 - 0 \cdot 3$					Form 4
	ect Materials (incl. supplies and non-energy	gy utilitia	≥s):	Derrig	ian	Page 1 of 1
	Type: Blade dressing materials.					Date <u>3/78</u>
<u> </u>	Specification: <u>Alumina stick</u> .				-	
	Quantity Required:				Cost:	<u>2.02 \$/ 10ac</u>
2.2_2	Type: <u>Coolant</u>		<u></u>		-	
	Specification: Rust lick	. <u></u>	<u></u>		_	
	80:1 water to Rust-lick				-	
	Quantity RequiredQ.66_gallor				Cost:	2.414 \$/load
2.2_	Туре:				-	
	Specification:					
					-	<u> </u>
			f			<u>4.44</u> \$/ <u>loa</u>

Proc	ess No	. 2	4.02-03					Form 5 Page 1 of 1
2.3	Expen	dable T	ooling:				D . 1	
	2.3 <u>1</u>	Type:	Model STC-22, ID diamond-plated blade	·····			Kevisi	on Date <u>3/78</u>
		<u>_</u>	Quantity Required: 0.07	blade/ load	Unit Cost	: <u>150</u> \$/ <u>b1</u>	adeCost:	<u>10.49</u> \$/ <u>load</u>
	2.3_	Туре:	v	,,,,,,,,,				
			Quantity Required:	/:	Unit Cost	\$/\$/	Cost:	\$/\$
	2.3_	Type:						
			Quantity Required:	/:	Unit Cost	::\$/	Cost:	\$/
	2.3_	Type:						
			Quantity Required:	/:	Unit Cost	::\$/	Cost:	\$/
				2.3	Subtotal	Expendable T	ooling:	<u>10,49 \$/ load</u>
2.4								
2.4	Energ							
	2.4 <u>1</u>	Туре:	Electrical, 2kW main and auxiliary mo	tors	<u></u>			
			Quantity Required:29.4	<u>kWh/load</u> :	Unit Cost	:: <u>0.0319</u> \$/_k	<u>Wh</u> Cost:	<u>0.94</u> \$/ <u>load</u>
	2.4_	Туре:						
4		<u></u>	Quantity Required:	:	Unit Cost	::\$/	Cost:	\$/
,					2.4 Sub	ototal Energy	Costs:	\$/_load
				2.5 Subtor	tal 2.2 to	2.4.		15.87 \$/load
				2 6 Uand1.	ing Charge	• E 26 % of	item 2.5	0.84 \$/load

 2.6 Handling Charge: <u>5.26</u>% of item 2.5
 0.84
 \$/load

 2.7 Subtotal Materials and Supplies: (2.5 + 2.6)
 16.71
 \$/load

Process No. 2 4 0 2 - 0	<u>]</u> 3	Revision	Form 6 Page <u>1</u> Date <u>3</u>	
3.1 Direct Labor:				
		Mounting and loading		
(SAMICS B3096D) Amount Required: 0.525		/h; Load <u>36.0</u> %; Cost:	2.78	\$/ <u>load</u>
3.1_2 Category: Semiconductor /	AssemblerActivity:	Machine supervision		
(SAMICS B3096D) Amount Required: 0.23		/h; Load <u>36.0</u> %; Cost:	1.22	\$/ <u>load</u>
3.1_3 Category: <u>Maintenance Mec</u>	chanicActivity:	Blade_head_changing		
(SAMICS B3736D) Amount Required: 0.875	_h/_load; Rate: \$_5.67	/h; Load <u>36.0</u> %; Cost:	<u> </u>	\$/_ <u>load</u>
		3.1 Direct Labor Subtotal:	10.75	\$/ load
3.2 Indirect Labor: Taken as 25% of c	lirect			
3.2 Category:	Activity:			
Amount Required:	_h/; Rate: \$	/h; Load%; Cost:	<u>-,,-,-,-</u> ,-,-	\$/
3.2 Category:	Activity:			
Amount Required:	_h/; Rate: \$	/h; Load%; Cost:		\$/
3.2 Category:	Activity;			
Amount Required:	_h/; Rate: \$	/h; Load%; Cost:		\$/
		3.2 Indirect Labor Subtotal:	2.59	\$/ <u>load</u>
	<u></u>	3.3 Subtotal 3.1 and 3.2	13.44	\$/ <u>load</u>
		3.4 Overhead on Labor: <u>5.26</u> %	0.71	\$/ <u>load</u>
		3.5 Subtotal Labor	<u>14.15</u>	\$/10ad

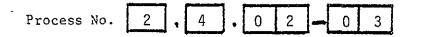
Proc	ess No	. 2 . 4 . 0 2 - 0 3	Revision	-	_of <u>1</u> 3/78
4.1	Equip	ment	<u> </u>	•••••••••••••••••••••••••••••••••••••••	
	4.1_]	Type: ID saw slicing machine			
		Cost: 40,000 \$; Installation Cost: \$; Throughput: 480	_/カx;y	•	
		Plant Oper'g Time8280 h/y; Machine Avail'ty:95_%; Machine Oper'g Time78	<u>66 h</u> /y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:285.71	\$/y		
		Useful Life:y, Charge Rate:21.4 _% of Cost/y; Capital Cost:8560	\$/y	18.43	\$/ <u>load</u>
	4 1	Туре:			
	ч,⊥ <u>_</u>				
		Cost:\$; Installation Cost:\$; Throughput:	_ ^{/h;}		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		\$/
	4.1	Туре:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	1		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:			
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:		<u></u>	_\$/
		4.1 Subtotal Equipmen	t Cost:	18.43	ş/load

Process No. 2. 4. 0 2	- 0 3				Form 8 Page <u>1</u> of <u>1</u>
4.2 Facilities:				Revis	sion Date
4.2 <u>1</u> Type: <u>Machine are</u>	ea Floor	r Area: <u>c</u>	3.0 m ² ; Throughput:	480 <u>loads</u> /y	
Charge Rate: 179.13	3*\$/(m ²		Maintenance Costs:		-
Heating		•	r:h/y at Supplies:	\$/n	
Air Cond'g	/y at\$/	· · · · · · · · · · · · · · · · · · ·	Outside Services:	\$/y	
Lighting	/y at\$/		Total Cost:	1612 \$/y	3.36 \$/load
4.2_ Type:	Floo:	r Area:	m ² ; Throughput:	/y	
Charge Rate:	\$/(m	² ·y);	Maintenance Costs:	anna dana dana .	
	nergy Use:	E C	r:h/y at	\$/h	
Heating	/y at\$/	I	Supplies:	\$/y	
Air Cond'g	/y at\$/	4	Outside Services:	\$/y	
Lighting	/y at\$/		Total Cost: _	\$/y	\$/
4.2_ Type:	Floo:	r Area:	m ² ; Throughput:	/у	
Charge Rate:	\$/(m	² ·y);	Maintenance Costs:	والبيابة الموادية المتلفين المتلاح و	-
Heating	nergy Use: /y at\$/	Labo	r:h/y at	\$/h	
Air Cond'g	/y at\$/	ł	Supplies:	\$/y	
Lighting	/y at\$/_	1	Outside Services: Total Cost: _	\$/y	\$/
* Includes energy use			4.2 Subto	tal Facilities:	\$/_load
			4.3 Equipment and Facili	ties Subtotal :	21.79 \$/load

				Form	9-1	
				Page	_ <u>_</u> of	<u>1</u>
Process	No. $2 \cdot 4 \cdot 0 \cdot 2 - 0 \cdot 3$		Revision		Date	3/78
5. Sal	vaged Material (Work-in-process)					
5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	2.40	<u>kg</u> _/	<u>load</u>		
5.2	l Input Work-in-process l. <u>Not</u> Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	2.34	kg/	/ <u>load</u>		
5.2	Net Amount of 5.21 which is sold for Credit As-Is or			/		
5.2	G Credit for 5.22 at the Market Value of\$/:		\$,	/		
5.2	A Cost of Reprocessing Material of 5.22 At the Average Reprocessing Cost of\$/:		\$,	/	·····	
5.2	5 Net Credit for 5.22 (5.23 minus 5.24):				ľ	\$/
5.2	5 Material of Type 1. Lost in Process (5.21 minus 5.22)	2.34	<u>_kg</u> _/	load		
5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)					168.99 \$/load
5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)					173.33 _{\$/} load
Sal	vaged Materials Summary:					
5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)				_	\$/

Prod	cess No.2	402-03			Form 10 Page <u>1</u> of <u>1</u>
б.	Byproducts	and Wastes	Rev	vision	
	6.1 Solid	Byproducts/Wastes			
	6.1_]	Type (Composition):	Quantity Produced:0 <u>, k</u>	<u>load</u>	
		Physical Shape/Size:	Energy Content:1	«Wh/	
		Density: 2.34 g/cm ³ ; Water Solubility:	_g/lat ^O C; pH:_		
		Toxicity:Biodegradable:	Other Remarks:		
		Type of Disposal: Input Material for:		_; Cost:	\$/
	6.2 Liquid	l Byproducts/Wastes (inorganic):			
	6.2_]	Type (Composition): 80:1 water: rust lick Density:g/cm ³ ; Suspended Solids: <u>silicon kerf</u> Toxicity: Heavy Metal Content:	Amount: <u>19</u> g/1 pH:_		
		Type of Disposal: <u>Can be stored in drums</u>			
		Input Material for:	Cost/(Credit)\$/	Cost:	\$/
				Carry:	\$/

	Form Page	12 2of
ocess No. 2.4.02-03	RevisionDate	<u>a 3/78</u>
Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	<u>52.64</u> \$/load
	7.22 Other Indirect Costs:% of 7.11 (0.059*(4.1)+0.108*4.2)	<u> 1.45 </u> \$/load
	7.21 Total Operating Add-on Costs of Process:	\$/_load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	54.09 \$/load
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Frocess Lost (5.3)	\$/_load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	_223.08 \$/load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	\$/_load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	<u>_396.40 \$/ load</u>
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu		
7.42 Practical Yield	<u> 100 </u> %	
7.43 Effective Yield (7.41 x 7.42)	<u>0.6 m²/ kg</u>	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	rk-in-Process per2.84 m²/ load	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	<u>139.58</u> \$/ m ²
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	\$/m ²
		1

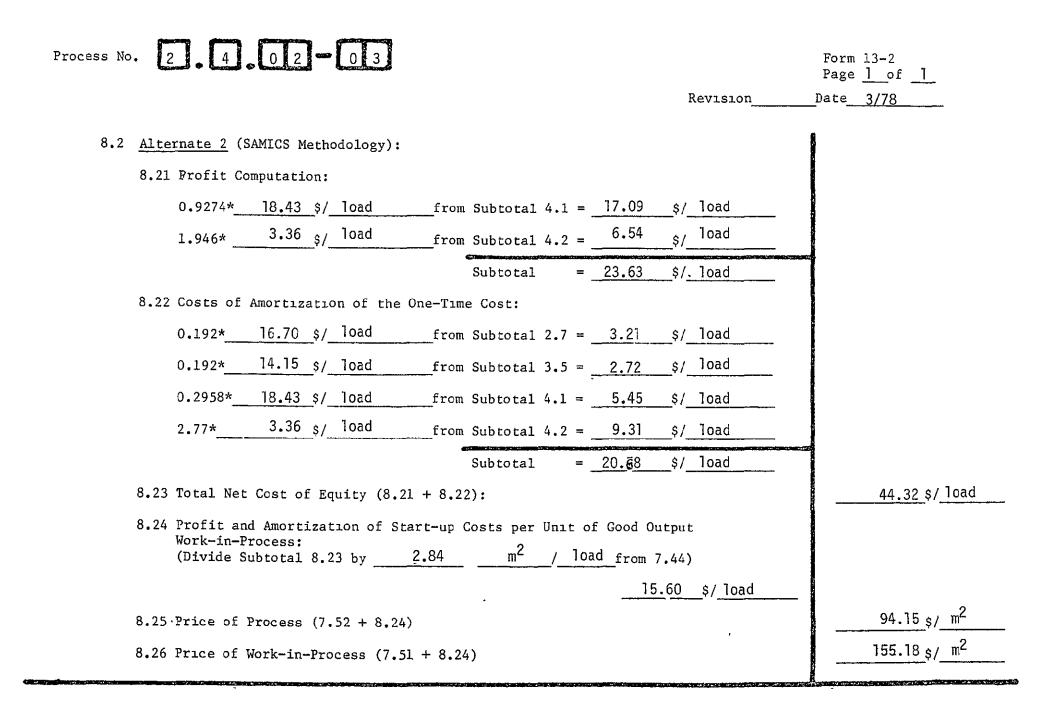


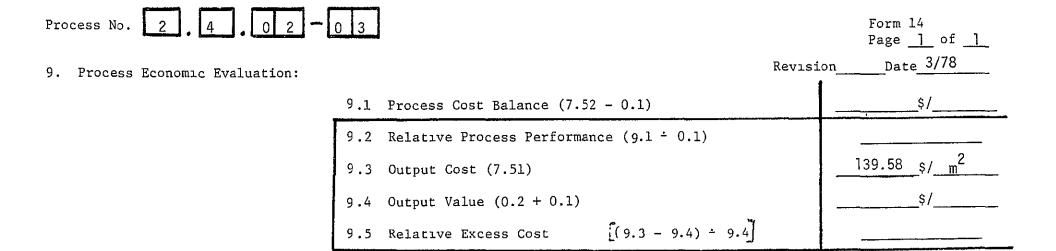
- 8. Price Computation
 - 8.1 <u>Alternate 1</u>
 - 8.11 Profit at Expected Rate of <u>20 %: 15.71 \$/ m²</u> (Profit before income taxes; applied to 7.52)

8.12 Price of Process (7.52 + 8.11)

8.13 Price of Work-in-Process (7.51 + 8.11)

Revision	Page	13-1 <u>]</u> of <u>1</u> 3/78
	94.76	
	155.29	\$/ m ²





Proce	ess No. 2 4 0 2 0 3		Form 15 Page <u>1</u> of <u>1</u>
1 0	Dutput Specification:	Revision	Date3/78
N	ame of item:Silicon wafers, 95 cut		
D	imensions:10.16 cm in diameter, 0.36 <u>+</u> 0.02 mm thick		
М	aterial:High purity silicon		
0	ther Specifications: Kerf thickness is 0.35 mm		
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			<u>. </u>
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		<u></u>	
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<u> </u>			

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet Generation

Subprocess: Ingot Slicing

Option:

n: Multiblade Slurry Slicing of 10-cm diameter

ingots with 234 blades per pack as demonstrated

experimentally by Varian in Exp. P-005. INDEX

Form	Pages	Rev.	Date	Remarks
1			_5/78	<u>All forms have same dates</u>
2	1 to <u>1</u>			·
3	1 to _0			······
4	l to <u>1</u>			
5	1 to <u>1</u>			
6	1 to <u>1</u>	[•
7	l to _1			
8	l to <u>1</u>			
9-1	l to <u>1</u>			
9-2	1 to <u>0</u>			
9-3	1 to _0	[·	
10	1 to <u>1</u>			·
11	1 to <u>0</u>			
12	1 to <u>1</u>			
13-1	l to <u>1</u>			· · · · · · · · · · · · · · · · · · ·
13-2	1 to <u>1</u>			
14	1 to <u>1</u>			
15	1 to <u>1</u>			
16	1 to <u>0</u>			

Form 2

		Page <u>1</u> of <u>1</u>
	Revision	Date 5/78
pcess No. $2, 4, 02 - 04$	0.1 Value Added:	\$/
ocess Description: <u>Multiblade slurry slicing as performed exp</u>	erimentally by Varian	
using a blade-head with 234 blades.		
Input Specification:		
Name of Item:	1-01	
Dimensions: <u>10-cm in diameter, 11.9 cm long, mass is 2.19 kg</u>		
Material: high purity silicon		
Other Specifications: <u>Silicon single crystal ingot</u>	mounted on ceramic block.	
Other Specifications,		
		
1.1 Quantity Required: 2.19	kg / load Unit Cost: 15	<u>50.56</u> \$/ <u>kg</u>
	1.2 Input Value:	\$/
	1.3 Input Cost:	329.73 \$/ loa
	• • • • • • • • • • • • • • • • • • • •	

Note to Item 1.3: Use price, if input produced in own plant.

Proc	ess No	2.4.02-04				Form 4	L
2.2	Indir	cect Materials (incl. supplies and non-energy utilities):					1 of 1
		Type: <u>PC oil</u>		Revis	sion	Dat	e_ <u>5/78</u>
	—	Specification: PC oil for abrasive vehicle			,		
				······································	—		
	2,2 <u>2</u>	Quantity Required: 7.6 <u>l/load</u> ; Unit Cost: 0.66 Type: <u>Abrasive</u>	_\$/_&				\$/load_
		Specification: 600 grit SiC abrasive; concentration in PC oil is 0.36 kg/l;					
		mass consumed per load is 2.736 kg.		-			
	. 2.2_	Quantity Required: 2.736 kg /load: Unit Cost: 4.29 Type:	_\$/ <u>kg</u> _	;	 Cost:	7.03	\$/load
		Specification:	····		-		
					-	-	
		Quantity Required:/; Unit Cost:	_\$/	;	Cost:		\$/
		2.2 Subtotal	Indirec	t Mate	rials:	12.05	\$/ <u>load</u>

Proc	ess No	. 2	. 4 . 02 - 0 4						Form 5 Page 1	5 1. of 1
2.3	Expen	dable T	coling:				-		-	
	2.3 <u>1</u>	Type:	Blade pack with 300 blades of 1095 steel, 0	.15 mm thic	<u>k, 6.</u>	<u>35 mm hı</u>	gh	evisi -	on	_ Date_5/78
			Quantity Required: 1 pa	ick / load:	Unit	Cost: <u>5</u>	50\$/pack_	Cost:	50	\$/ <u>load</u> _
	2.3_					in		-		
			Quantity Required:	/:	Unit	Cost: _	\$/	Cost:		\$/
	2.3_	Type:								
			Quantity Required:	:	Unit	Cost: _	\$/	Cost:		\$/
	2.3									
			Quantity Required:			Cost:	\$/	Cost:		_\$/
				2.3	Subto	tal Exp	endable Too	ling:	50	\$/ <u>load</u>
				<u> </u>		,			<u> </u>	
2.4	Energy	7								
	2.4 <u>1</u>	Type:	Electricity for 1 kW main and auxiliary	<u>motors</u>				. I		
			Quantity Required: 32 KWh / lo	ad:	Unit	Cost: 0_	<u>0319</u> \$/kWh_	Cost:	_1.02	\$/ <u>load</u>
	2.4	Type:								
			Quantity Required:	:	Unit	Cost: _	\$/	Cost:		_\$/
					· · · · · · · · · · · · · · · · · · ·		al Energy C			
				2.5 Subtot	al 2.1	L to 2.4	4		63.07	\$/ load

2.6 Handling Charge: 5.26 % of item 2.5

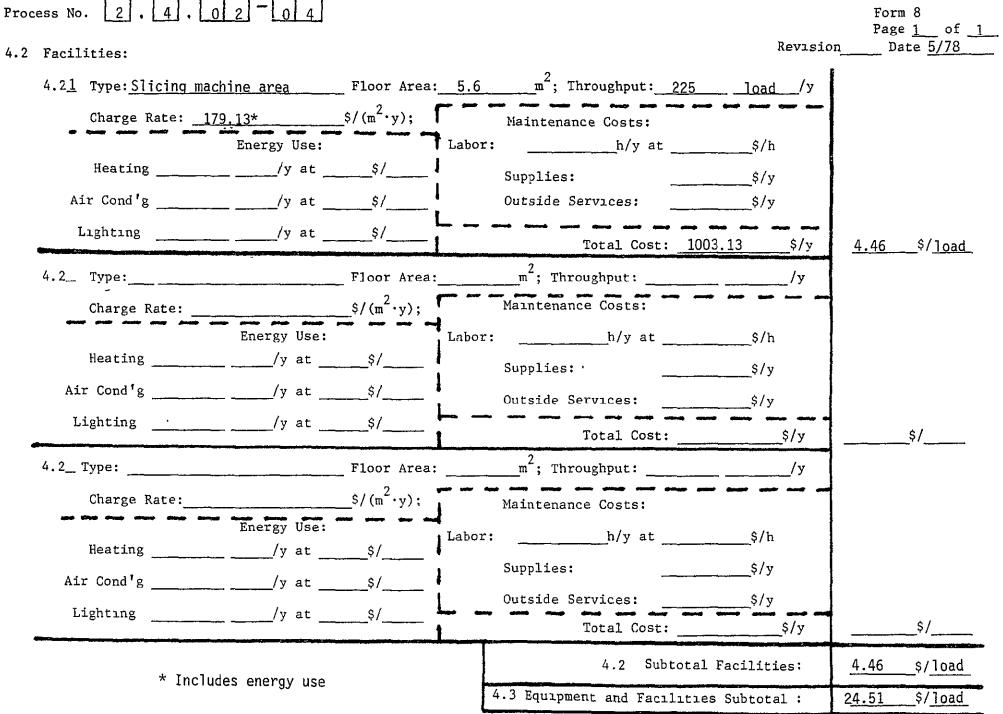
2.7 Subtotal Materials and Supplies: (2.5 + 2.6) 3.32 \$/ load

\$/<u>load</u>

66.39

Process No. 2.4.02-04		form 6 Page <u>1</u> of <u>1</u> Date <u>5/78</u>
3.1 Direct Labor:		
3.1_1 Category: <u>Semiconductor assembler</u> Activity: <u>Machi</u>	ine loading	
(SAMICS B3096D) Amount Required:0,5 h/ load ; Rate: \$3.90 /h;	Load_ <u>36,0</u> _%; Cost:	2.65 \$/10ad
3.12 Category: <u>Semiconductor assembler</u> Activity: <u>machine</u>	supervision	
(SAMICS B3096D) Amount Required: <u>0.67</u> h/ <u>load</u> ; Rate: \$ <u>3.90</u> /h;	Load <u>36.0 </u> %; Cost:	3.55 \$/load
3.1 <u>3</u> Category: <u>Maintenance mechanic</u> Activity:_Adjustm	ents, blade head changing	
(SAMICS B3736D) Amount Required: 0.67 h/ load ; Rate: \$ <u>5.67</u> /h;	Load 3.60 %; Cost:	5.17 \$/load
3.1 3.1	Direct Labor Subtotal:	11.37 \$/load
3.2 Indirect Labor: 25% of direct		
3.2 Category:Activity:		
Amount Required:h/; Rate: \$/h;	Load%; Cost:	\$/
3.2_ Category:Activity:		
Amount Required:h/; Rate: \$/h;	Load%; Cost:%	\$/
3.2_ Category:Activity:		
Amount Required:h/; Rate: \$/h;	Load%; Cost:	\$/\$/
3.2	Indirect Labor Subtotal:	2.84 \$/load
3.3	Subtotal 3.1 and 3.2	14.21 \$/load
3.4	Overhead on Labor: 5.26 %	0.75 \$/ <mark>load</mark>
3.5	Subtotal Labor	14.96 \$/load

Proc	ess No	2 4 0 2 - 0 4		Form 7 Page <u>1</u>	of
4.1	Equipi	ment	Revision_	Date	5/78
	4.1 <u>1</u>	Type: Multiblade slicing machine			
		Cost: 20,000 \$; Installation Cost: - \$; Throughput: 225 loads	_/x;y		
		Plant Oper'g Time <u>8280</u> h/y; Machine Avail'ty: <u>90</u> %; Machine Oper'g Time <u>7452</u>	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:1592.3	_\$/y		
		Useful Life· 7 y; Charge Rate: 21.35 % of Cost/y; Capital Cost: 4270	\$/y	20.05	_\$/ <u>load</u>
	4.1_	Type:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h,		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		_\$/
	4.1_	Type:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y	<u></u> ,,.,,,.	_\$/
		4.1 Subtotal Equipmen	t Cost:	20.05	\$/ <u>load</u>



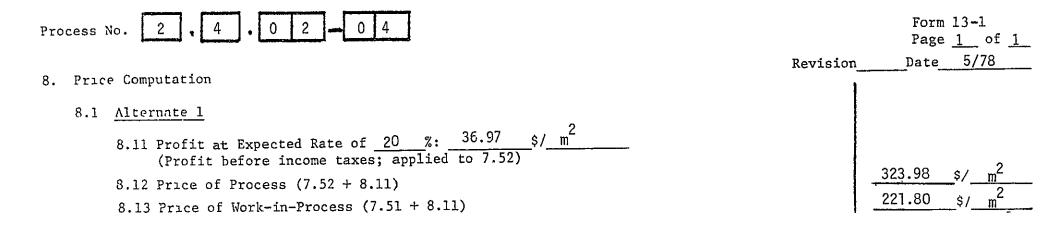
4.2 Facilities:

		F	orm 9-1
		Pa	age <u>1</u> of <u>1</u>
Process N	0.2.4.02-04	Revision	Date <u>5/78</u>
5. Salva	ged Material (Work-in-process)		
5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	<u>1.035 kg / loa</u>	ad
5.21	Input Work-in-process 1. <u>Not</u> Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	<u> 1.158 kg / loa</u>	ad
5.22	Net Amount of 5.21 which is sold for Credit As-Is or After Applying Re-Process	//	
5.23	Credit for 5.22 at the Market Value of\$/:	\$/	
5.24	Cost of Reprocessing Material of 5.22 at the Average Reprocessing Cost of\$/:	\$/	
5.25	Net Credit for 5.22 (5.23 minus 5.24):		\$/
5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)	<u>1.158 kg / loa</u>	<u>اط</u>
5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)		<u>174.35</u> \$/ <u>load</u>
5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2' Times Unit Cost from 1.1)		<u>155.83</u> \$/load_
Salva	ged Materials Summary:		and a second
5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)		·\$/

•

Pro	cess No.	2, 4, 02 - 04			Form 10 Page <u>1</u> of <u>1</u>
6.	Byproduct	s and Wastes		Revision	Date 5/78
	6.1 Solid	Byproducts/Wastes			
	6.1 <u>1</u>	Type (Composition): Silicon chips with dust	Quantity Produced: 0.	21 kg/_load	
		Physical Shape/Size:	Energy Content:	kWh/	
		Density: <u>2.34</u> g/cm ³ ; Water Solubility: <u>0</u>	_g/lat°C;	pH:	
		Toxicity:Biodegradable:	Other Remarks:		
		Type of Disposal:]	
		Input Material for:	Cost/(Credit)\$/	; Cost:	\$/
	6.2 Liqui	d Byproducts/Wastes (inorganic):			
	6.2 <u>1</u>	Type (Composition): Abrasive oil slurry with kerf	Quantity Produced: 7.6	_l/_load	
		Density: <u>~0.95g</u> /cm ³ ; Suspended Solids: <u>Sic_abrasive</u>	Amount:0,36 kg	H:	
		Toxicity: Heavy Metal Content:	ng/1 Other Remarks:		
		<u>contains 0.95 kg of kerf (0.12 kg/l - slurry)</u>			
		Type of Disposal:			
		Input Material for:	Cost/(Credit)\$/	Cost:	\$/\$/
			Carlotta an an		
				Carry:	\$/

	Form Page	12 _1of1
Process No. $2 \cdot 4 \cdot 02 - 04$	RevisionDate_	5/78
7. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	<u>105.86</u> \$/load
	7.22 Other Indirect Costs: % of 7.11 0.59 x (4.1) + 0.108×(4.2)	<u> 1.66 \$/load </u>
	7.21 Total Operating Add-on Costs of Process:	<u>107.52 \$/load</u>
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	<u>107.52</u> \$/ <u>load</u>
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	_174.35_\$/load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	_281.87_\$/load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	155.83 \$/load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	437.70 \$/load
7.41 Theoretical Yield (or Conversion work-in-process do not equal inp		
7.42 Practical Yield	<u>83 %</u>	
7.43 Effective Yield (7.41 x 7.42)	0.695 m ² / kg	
7.44 Number of Units of Good Output W Computation Unit Used up to 7.35	ork-in-Process per	
	7.51 Cost of Unit of Good Outpu t Work-in- Process (7.37 ÷ 7.44)	<u>287.02 \$/ m²</u>
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	<u>184.83 s/ m²</u>



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Process No. 2.4.02-04	Form 13-2 Page <u>1</u> of <u>1</u>
Revision	Date5/78
8.2 <u>Alternate 2</u> (SAMICS Methodology):	
8.21 Profit Computation:	
0.9274* <u>20.05</u> \$/ <u>load</u> from Subtotal 4.1 = <u>18.59</u> \$/load	
1.946* 4.46 \$/ load from Subtotal 4.2 = 8.68 \$/load	
Subtotal = 27.27 \$/load	
8.22 Costs of Amortization of the One-Time Cost:	
0.192*_66.39 \$/_loadfrom Subtotal 2.7 = 12.75 _\$/load	
0.192* <u>14.96</u> \$/ <u>load</u> from Subtotal 3.5 = <u>2.87</u> \$/ <u>load</u>	
0.2958*20.05 \$/load from Subtotal 4.1 = 5.93 \$/load	
2.77* 4.46 \$/ load from Subtotal 4.2 = 12.35 \$/load	
• Subtotal = 33.90 \$/load	
8.23 Total Net Cost of Equity (8.21 + 8.22):	<u>61.17 \$/load</u>
8.24 Profit and Amortization of Start-up Costs per Unit of Good Output Work-in-Process: (Divide Subtotal 8.23 by <u>1.525</u> <u>m²</u> /load from 7.44) <u>40.11 \$/m²</u>	
8.25 Price of Process (7.52 + 8.24)	- 224.94 ş/m ²
8.26 Price of Work-in-Process (7.51 + 8.24)	<u>327.13</u> \$/ m ²

Process No. 2. 4. 02-04		Form 15 Page <u>1</u> of <u>1</u>
	Revision	Date5/78
0. Output Specification:		
Name of item:Wafer, as-cut		
Dimensions: 10-cm diameter, 0.294 ± 0.04 mm thick		
Material: high purity silicon		
Other Specifications: Depth of subsurface damage 10-15 µm		
•		
		·····

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Process No.	2		4	_	0	2	-	04]
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University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

-	Sheet generation	
Process:	Sheet generation	

Subprocess: Ingot slicing

Option:

Multiblade slurry slicing using the

900	blac	le-ł	nead	machine	as	proposed	by	<u>Varia</u> n
for	use	in	198	5.				

INDEX

Form	Pages	<u>Rev.</u>	<u>Date</u>	<u>Remarks</u>
1			_5/78	All forms have same date
2	1 to <u>1</u>			
3	1 to _0			· · · · · · · · · · · · · · · · · · ·
4	1 to <u>1</u>		·	
5	l to <u> </u>			
[~] 6	l to _]		·	
7	l to <u>l.</u>			
8	l to <u> </u>			
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10	1 to <u>1</u>			
11	1 to <u>0</u>			
12	l to <u></u> '			
13-1	l to <u>1</u>			
13-2	l to]			
14	1 to <u>1</u>			
15	1 to _1			·
16	1 to <u>0</u>			

Form 2

			Page 10f 1
		Revision	Date <u>5/78</u>
rocess No. 2.	4 . 0 2 - 0 4	0.1 Value Added:	\$/
rocess Descriptio	m: Multiblade slurry slicing		
·····	Projection for Varian's slicing machine with 900 blades	per head,	
	Blades are 0.15 mm thick with 0.30 mm spacers		
<u></u>			
. Input Specific	ation:		
	ĩ		
Name of Item:	Prepared machine load from 2.4 : 01 : 04		
Dimensions:	12-cm in diameter, 40·5 cm long, 10·72 kg single crystal i	ngots	
Material:	High purity silicon		
Other Specific	ations: One silicon crystal mounted on ceramic block		
-			
		الباریا – با اور این از این اور این اور این اور این	
		مور بین می اور و بین می اور و بین می و بین می اور و اور و بین می و اور و او مور و اور	
	1.1 Quantity Required: 10.72 kg / load	. Unit Cost: 70).98 \$/ kq Si
		1.2 Input Value:	<u> </u>
		1.3 Input Cost:	760.94 \$/ load
	ι,	1.5 1.900 00000	

Note to Item 1.3: Use price, if input produced in own plant.

Proce	ess No	[2], [4], [0], [0], [0], [4]			Form 4
		ect Materials (incl. supplies and non-energy utilities):			Page <u>l</u> of <u>l</u>
<i></i>					Date <u>5/78</u>
	2.2_(Type: <u>Abrasive slurry</u>			•
		Specification: PC oil with 600 grit abrasive		-	
		Concentration 0.24 kg/2	<u></u>	- 1	
				-	
		Ouantity Required: 15 /load; Unit Cost:\$/_\$	<u>.</u>	Cost:	<u>27.75</u> \$/ <u>load</u>
	2.2_2	Type: Misc. materials	<u></u>		
		Specification: <u>Not given; estimated</u>		-	
				. (
				~	
		Quantity Required:; Unit Cost:\$/;	;	Cost:	9.48 s/load
	2.2_	Type:		.	
		Specification:			
				-	
			<u></u>		
		Quantity Required: / _; Unit Cost:\$/	;	Cost:	\$/
		2.2 Subtotal Indire	ect Mate	rials:	37.23 \$/load

'roc	ess No.	. 2	. 4 . 0 2 -	0 4						Form 5
			fooling:							Page 1 of 1
	2.3_1	Type:	900-blade drill	pin pack const	isting_of_0	.15 mm thick,	1095 stee1_	blades	Revisi	on Date
			Quantit						k Cost:	<u>19.73</u> \$/ <u>load</u>
	2.3_	Туре:	•••••		<u> </u>				_	
			Quantit	y Required:		/:	Unit Cost:	\$/	_ Cost:	\$/
	2.3_	Туре:					 			
			Quantit	y Required:		/:	Unit Cost:	\$/	_ Cost:	\$/
	2.3_	Type:			<u></u>				_	
		<u></u>	Quantit	y Required:		/:	Unit Cost:	\$/	_ Cost:	\$/
						2.3	Subtotal E	xpendable To	oling:	19.73 \$/pack
						المودني البريين الانتباغ فيستناعيه		ملائدات مبعيا الكريج بمستهدية الكمانية الأكرامي		د والشایف کارک این این اکار بر بر اینک اور این این این این این این این این این این

.4 Energy

2.4] Type: _ Electrical, 1.67 kW in main and auxiliar	y motors	
Quantity Required:49.3	<u>kWh/load</u> : Unit Cost: <u>0.032</u> \$/ <u>kWh</u> Cost:	<u>1.57</u> \$/load
2.4 Type:		
Quantity Required:	: Unit Cost:\$/ Cost:	\$/
	2.4 Subtotal Energy Costs:	1.57 \$/load
	2.5 Subtotal 2.1 to 2.4;	58.53_\$/load
	2.6 Handling Charge: <u>5.26 %</u> of item 2.5	<u>3.07\$/load</u>
	<pre>2.7 Subtotal Materials and Supplies: (2.5 + 2.6)</pre>	61.60 ş/load

Process No. 2.4.02-04 Revision	Form 6 Page <u>1</u> of <u>1</u> nDate <u>5/78</u>
3.1 Direct Labor:	
3.1] Category: Semiconductor AssemblerActivity:loading/unloading	-
(SAMICS B3096D) Amount Required: 0.67 h/load ; Rate: \$_3.90 /h; Load 36.0 %; Cost:	<u>3.55</u> \$/_load
3.1 Category: Semiconductor Assembler Activity: Machine supervision	
(SAMICS B3096D) Amount Required: 0.67 h/ load ; Rate: \$ 3.90 /h; Load 36.0 %; Cost:	\$/_load
3.1_ Category: <u>Maintenance Mechanic</u> <u>Activity: blade head changing and adjusti</u>	ng
(SAMICS B3704D) Amount Required:0.67_h/_load; Rate: \$ <u>_5.67</u> _/h; Load_ <u>36.0</u> _%; Cost:	\$/load
3.1 Direct Labor Subtotal:	<u>12.27 \$/ load</u>
3.2 Indirect Labor: 25% of direct	
3.2 Category:Activity:	<i>-</i>
Amount Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2_ Category:	_
Amount Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2_ Category:Activity:	_
Amount Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2 Indirect Labor Subtotal:	<u> 3.07 \$/ load </u>
4 3.3 Subtotal 3.1 and 3.2	15.34 . \$/ load
3.4 Overhead on Labor: 5.26	%\$/_load
3.5 Subtotal Labor	<u>16.15</u> \$/ <u>load</u>

Proc	ess No	$\cdot 2 \cdot 4 \cdot 0 \cdot 2 - 0 \cdot 1$		Form 7 Page <u>1</u>	
4.1	Equip	ment	Revision	Date _	5/78
	4.1_1	Type: <u>Multiblade slicing machine</u>			
		Cost: 30,000 \$; Installation Cost: \$; Throughput: 245	_/'n; y		
		Plant Oper'g Time 8280 h/y; Machine Avail'ty: 90 %; Machine Oper'g Time 745	<u>2</u> h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:1592.3	_\$/y		
		Useful Life: 7_y; Charge Rate: 2].35_% of Cost/y; Capital Cost: 6420	\$/y	32.70	\$/ <u>load</u>
	4.1_	Type:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y	<u> </u>	\$/
	4.1_	Type:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		\$/
		4.1 Subtotal Equipmer	t Cost:	32.70	\$/ <u>load</u>

Proc	ess No. 2, 4.	0 2 - 0 4						Form 8 Page <u>1</u> of <u>1</u>
4.2	Facilities:						Revision	Date <u>5/78</u>
	4.2_1 Type: <u>Slicing m</u>	achine_area	_ Floor Area:	5.6	m ² ; Throughput:	245_1 <u>oads</u>	/y	
	Charge Rate:	179.13*	_\$/(m ² •y);		Maintenance Costs:			
	المستنق المسام ستدنية ويسوا الله	Energy Use:	• ••••• •••••	Labor	:h/y at	\$/i	ı	
	Heating	/y at	\$/I		Supplies:	\$/3	,	
	Air Cond'g	/y at	\$/	, 	.Outside Services:			
	Lighting	/y at	\$/		Total Cost:	1003.13	\$/y	4.09 \$/ load
	4.2_ Type:		Floor Area:		m ² ; Throughput:		_/y	
	Charge Rate		$(m^2 \cdot y);$,	Maintenance Costs:	مست جمع کنسته ا		
		Energy Use:		Labor	:h/y at	\$/H		
	Heating	/y at	\$/	j	Supplies:	\$/y		
	Air Cond'g	/y at	\$/	5	Outside Services:	\$/y		
	Lighting	/y at	\$/	 	Total Cost: _		\$/y	\$/
-	4.2_ Type:		_ Floor Area:		² ; Throughput:	······································	_/y	
	Charge Rate:		\$/(m ² ·y),		Maintenance Costs:			
	and district analy states and	Energy Use:		l Labor	: h/y at	\$/h		
	Heating	/y at	\$/)		\$/y		
	Air Cond'g	/y at	\$/					
	Lighting	/y at	\$/		Outside Services: Total Cost:	\$/y	ş/y	\$/
•	*Includes ener					tal Facilit		4.09 _{\$/} load
	The fuces eller	gy use		•				······································
				l	4.3 Equipment and Facili	ties Subtot	a⊥ :	<u>35.79</u> \$/ load

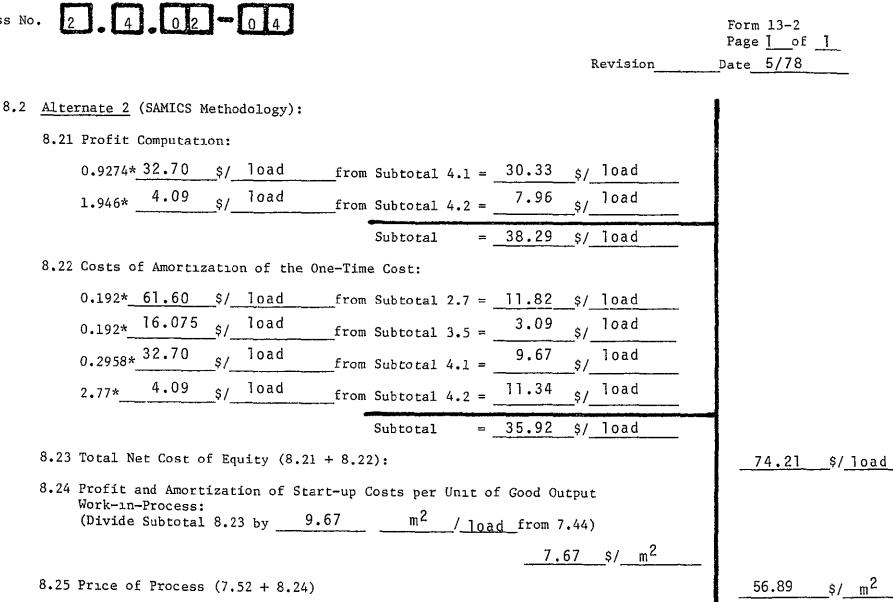
					Form	9-1	
				 • •		<u>]</u> of	
Pro	cess No	2 4 0 2 - 0 4	1	Revision	· ·····	_Date	<u> </u>
5.	Salvaç	ed Material (Work-in-process)					
	5.1	Quantity of Work-in-Process L. Contained in Good Output Work-in-Process (per Computation Unit)	5.66	kg	/ load		
	5.21	Input Work-in-process 1. <u>Not</u> Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	5.06	kg	/load		
	5.22	Net Amount of 5.21 which is sold for Credit As-Is or					
		After Applying Re-Process	.	_ . <u>_</u>	/	_	
	5.23	Credit for 5.22 at the Market Value of\$/:		\$	/		
	5.24	Cost of Reprocessing Material of 5.22 at the Average Reprocessing Cost of\$/:	·	\$	/		
	5.25	Net Credit for 5.22 (5.23 minus 5.24):					\$/
	5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)	5,06	<u>_kg_</u> /	load		
	5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)					359.18 \$/ load
	5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)					401.76 s/ load
-	Salvaç	ed Materials Summary:					
	5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)					\$/

Process No. 2, 4, 02 - 04	Form 10 Page <u>1</u> of <u>]</u>
6. Byproducts and Wastes Revision	Date5/78
6.1 Solid Byproducts/Wastes	
6.1_1 Type (Composition): <u>Silicon chips and dust</u> Quantity Produced: <u>0.536 kg/ load</u>	
Physical Shape/Size: Energy Content:kWh/	
Density: 2.34 g/cm ³ ; Water Solubility:g/l at°C. pH:	
Toxicity:Biodegradable:Other Remarks:	
Type of Disposal:	
Input Material for: Cost/(Credit)\$/; Cost:	\$/
6.2 Liquid Byproducts/Wastes (inorganic):	
6.2_] Type (Composition): PC oil slurry Quantity Produced: 15 & / load	
Density: 0.95 g/cm ³ ; Suspended Solids: SiCabrasive Amount: 0.24 kg/1 pH:	
Toxicity: Heavy Metal Content:mg/1 Other Remarks:	
Oil also contains 4.76 kg of kerf/load; concentration is 0.32 kg/l.	
Type of Disposal:	
Input Material for:Cost/(Credit)\$/Cost:	\$/
Carry:	\$/

	Form Page	_12 _1of1
rocess No. 2 . 4 . 0 2 - 0 4	RevisionDate_	5/78
. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	114.46 \$/load
	7.22 Other Indirect Costs:% of 7.11 (0.59*(4.1) + .108(4.2)	\$/load
	7.21 Total Operating Add-on Costs of Process:	<u>_116.83_\$/10ad</u>
	7.22 G & A% of 7.21	\$/\$/
	7.31 Total Gross Add-On Cost of Process	<u>116.83</u> \$/ <u>load</u>
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	<u> 359.18 </u> \$/load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	476.01 \$/load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	<u>398.40</u> \$/load
	7.36 Loading on Item 7.35 at Rate% .	\$/\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	<u>874.41</u> \$/ load
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu		
7.42 Practical Yield	<u>95</u> %	
7.43 Effective Yield (7.41 x 7.42)	<u> 0.9 m² / kg </u>	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	prk-in-Process per9.67 m ² 1oad	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	49.22 s/ m ²
		F

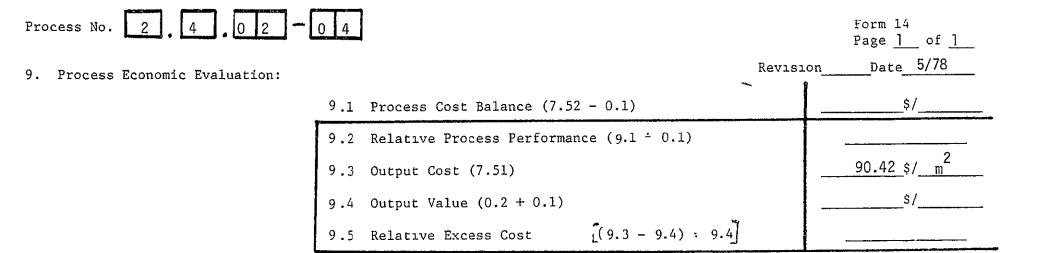
Process No. 2, 4, 0 2 - 0 4	Form 13-1 Page <u>1</u> of <u>1</u>
8. Price Computation	Revision Date 5/78
8.1 <u>Alternate 1</u>	
8.11 Profit at Expected Rate of <u>20 %: 9.85</u> \$/ m ² (Profit before income taxes; applied to 7.52)	
8.12 Price of Process (7.52 + 8.11)	<u> </u>
8.13 Price of Work-in-Process (7.51 + 8.11)	<u> 100.28 \$/ m² </u>

Process No.



8.26 Price of Work-in-Process (7.51 + 8.24)

\$/_m²



								<u></u>		
Process	No.	2	•	4	0	2	-	0	4	

	Form 1	5
	Page _	of
Revision	Date	5/78

0. Output Specification:

Name of item:	icon wafer, as cut
Dimensions: 12 c	in dia., 0.25 mm thickness
Material:Hig	n purity silicon
Other Specifications:	Kerf thickness 0.2 mm

Process No. 2 4 02 - 06

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet generation

Subprocess: Wafer generation

Option:

Crystal Systems' Fixed

Abrasive Multiwire Slicing

INDEX

Form	Pages	<u>Rev.</u>	Date	<u>Remarks</u>
1			7/78	All forms have same date
2	1 to <u>1</u>			·
3	1 to _0_			
4	1 to _]			
5	1 to _1			
6	l to _]	_		
7	l to _]	 		
8	l to _]			
9-1	1 to _1	· · · · · ·		
9-2	1 to <u>0</u>			
9-3	1 to _0_			
10	1 to <u>1</u>			
11	1 to <u>0</u>			
12	1 to _1			
13-1	1 to <u>1</u>			
13-2	1 to _1			
14	1 to _]			
15	l to <u> </u>			
16	1 to			

Form 1

Form 2

			Page <u>lof</u> l
		Revision	Date <u>7/78</u>
cocess No. 2	4 0 2 0 6	0.1 Value Added:	\$/
cocess Descript	tion: <u>Multiwire fixed abrasive slicing as projected by Cry</u>	stal_Systems	
<u> </u>			······································
<u></u>			
Input Speci	fication:		
Name of Ite	m: <u>Sectioned from a 30 x 30 x 30 cm boule, grown by heat e</u>	xchange_ingot-casting	
	Two 30 x 10 x 10 cm ingots, each weighing 7.02 kg		
Material:			
	fications:		
Other opeca			
······		ىلە ^{ىلى} بەركەر يېرىكە ئەركە يۈركە ^ن ۋە يەتلە ^ر لىق مۇرىغان بەركەر يەركە يېرىخ	
<u></u>			
	1.1 Quantity Required: 14.04 kg / load	Unit Cost:	<u>27.75</u> \$/ <u>kq</u>
		1.2 Input Value:	\$/
		1.3 Input Cost:	389.56 \$/ load
		1 3	

Note to Item 1.3: Use price, if input produced in own plant.

•

Proces	ss No	2.4.02-06			Form 4
2.2 I	Indir	ect Materials (incl. supplies and non-energy utilities):	Revis:	ion	Page 1 of 1 Date 7/78
2	2.2 <u>1</u>	Type: Coolant water		.;	
		Specification: Filtered domestic water flowing at a rate of about 20 l/h		1	
		(SAMICS C1016B)		-	
		Quantity Required:	1000 e ;		0.04 \$/_load
2	2.2 <u>2</u>	Type: <u>Misc. materials: eg. slicer parts, etc.</u> Specification:			
			<u></u>	-	
		Quantity Required:/_; Unit Cost: 0.30 \$/1		Cost:	0.30_s/_load
2	2.2_	Type:			
		Quantity Required:/; Unit Cost:\$/		-	\$/
		2.2 Subtotal Indi	rect Mate	rials:	0.34_\$/load

Process No. 2.4.02-06	Form 5
	Page <u>1</u> of <u>1</u>
2.3 Expendable Tooling:	Revision Date 7/78
2.3_1 Type: _2, 750 wire-blade package sets	
Quantity Required: 0.2	
2.3_ Type:	
Quantity Required:	: Unit Cost:\$/ Cost:\$/
2.3 Type:	
	: Unit Cost:\$/ Cost:\$/
2.3 Type:	
	: Unit Cost:\$/Cost: ·\$/
	2.3 Subtotal Expendable Tooling: <u>5</u> \$/ load

2.4 Energy

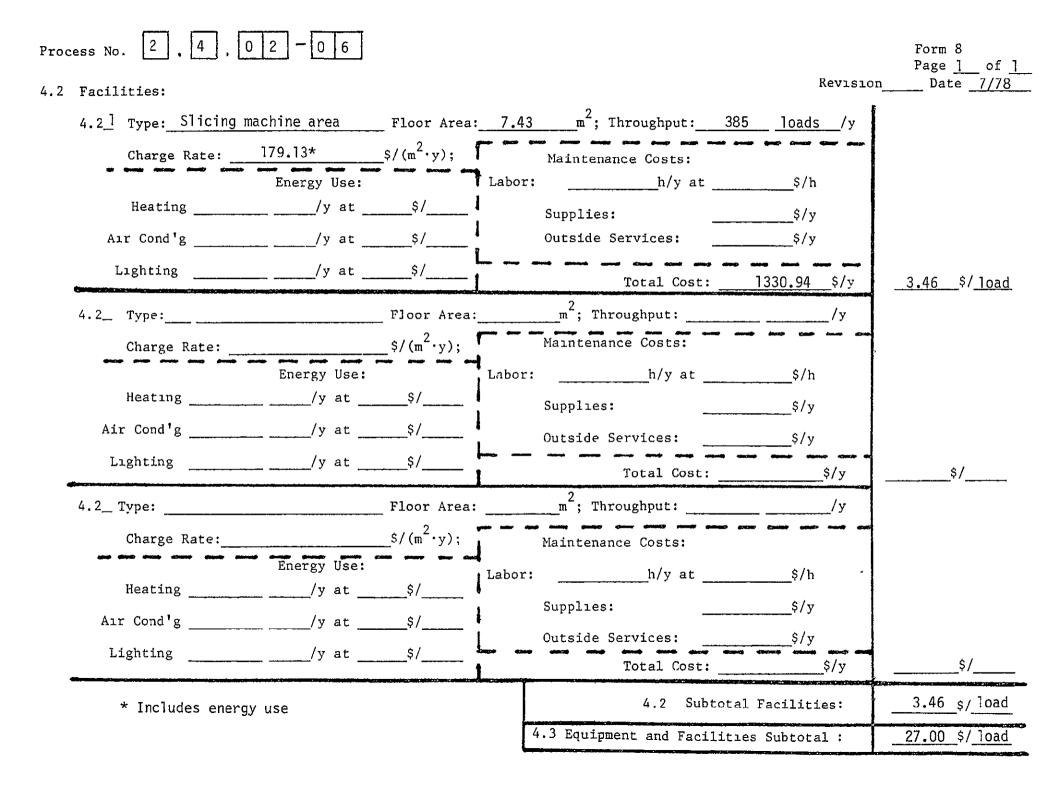
2.4] Type: 2 kW motors		
Quantity Required: 33.3	kWh/load : Unit Cost: 0.0319\$/ kWh Cost:	<u>1.06</u> \$/ <u>load</u>
2.4 Type:		
Quantity Required:		\$/
	2.4 Subtotal Energy Costs:	<u>1.06</u> \$/ <u>load</u>
	2.5 Subtotal 2.2 to 2.4; 2.6 Handling Charge: <u>5.26%</u> of item 2.5	6.40 \$/ load 0.34 \$/ load
	<pre>2.7 Subtotal Materials and Supplies: (2.5 + 2.6)</pre>	6.7,4 \$/ <u>load</u>

1

-

Process No. 2.4.02-06 Revision	Form 6 Page <u>1</u> of <u>1</u> Date <u>7/78</u>
3.1_] Category: <u>Semiconductor Assembler</u> Activity: <u>machine loading and unloading</u>	
3.1_1 Category: <u>Semiconductor Assemble</u> (SAMICS B3096D) Amount Required: <u>0.50 h/load</u> ; Rate: \$ <u>3.90</u> /h; Load <u>36.0</u> %; Cost:	2.65 \$/ load
3.1 ² Category: <u>Semiconductor Assembler</u> Activity: <u>Machine supervision</u>	
(SAMICS B3096D) Amount Required: 1.1 h/ load ; Rate: \$ 3.90 /h; Load 36.0 %; Cost:	5.83 ^{\$/} _load
3.1_3 Category: <u>Maintenance Mechanic II</u> <u>Activity: Service and repair, cutting tool</u> ch	nange
(SAMICS B3704D) Amount Required: 1.0 h/ load ; Rate: \$ 5.67 /h; Load 36.0 %; Cost:	\$/_load
3.1 Direct Labor Subtotal:	16.19 \$/load
3.2 Indirect Labor: 25% of direct	
3.2_ Category:Activity:	
Amount Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2 Category:Activity:	
Amount Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2_ Category:	
Amount Required:h/; Rate: \$/h; Load%; Cost:	\$/
3.2 Indirect Labor Subtotal:	4.05 \$/load
3.3 Subtotal 3.1 and 3.2	20.24 \$/ <u>load</u>
3.4 Overhead on Labor: 5.26 %	1.06 \$/load
3.5 Subtotal Labor	21.30 \$/load

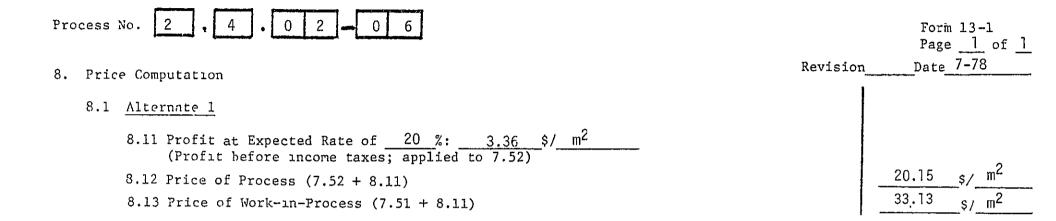
Process No. 2 . 4 . 0 2 - 0 6 A.1 Equipment	Form 7 Page 1 of 1 n Date 7/78
4.1_1 Type: FAM slicing machine with two blade heads	-
Cost: <u>35,000</u> \$; Installation Cost:\$; Throughput: <u>385 loads</u> /½;y	
Plant Oper'g Time <u>8280</u> h/y; Machine Avail'ty: <u>85</u> %; Machine Oper'g Time <u>7038</u> h/y	,
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:1592.3_\$/y	
Useful Life: 7y; Charge Rate: 21.35 % of Cost/y; Capital Cost: 7472.50 \$/y	/ <u>23.54</u> \$/ load
4.1_ Type:	-
Cost:\$; Installation Cost:\$; Throughput:/h;	
Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Timeh/y	7
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:\$/y	
Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:\$/y	\$/
4.1_ Type:	_
Cost:\$; Installation Cost:\$; Throughput:/h;	
Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Timeh/y	7
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:\$/y	
Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:\$/y	y\$/
4.1 Subtotal Equipment Cost:	_23.54 \$/_load



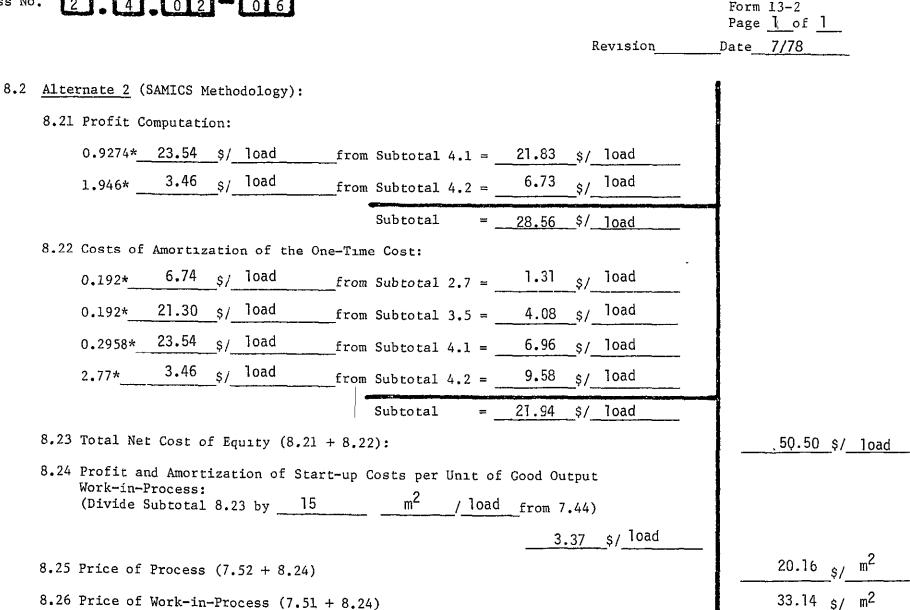
					Form 9-1		
					Page <u>]</u> o	£ <u>]</u>	
Pro	cess No	$2 \cdot 4 \cdot 0 \cdot 2 - 0 \cdot 6$	Rev	vision	Dat	e <u>7/78</u>	.
5.	Salvag	ed Material (Work-in-process)					
	5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	7.02	kg /	load		
	5.21	Input Work-in-process l. <u>Not</u> Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	7.02	kg / 1	load		
	5.22	Net Amount of 5.21 which is sold for Credit As-Is or					
		After Applying Re-Process	<u> </u>	/	· <u> </u>		
	5.23	Credit for 5.22 at the Market Value of\$/:		\$/			
	5.24	Cost of Reprocessing Material of 5.22 at the Average Reprocessing Cost of\$/:	7.02	kg \$/_]	oad		
	5.25	Net Credit for 5.22 (5.23 minus 5.24):					_\$/
	5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)		/		 	
	5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)				194.78	\$/ <u>loaki</u>
-	5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)				194.78	_ _{\$/} _load
•	Salvaç	ed Materials Summary:					
	5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)		999-9999-9999-9999-9999-9999-9999-9999-9999			\$/

Pro	cess No.	2, 4, 02 - 06			Form 10 Page <u>1_</u> of <u>1</u>
6.	Byproduct	s and Wastes		Revision	Date
	6.1 Solıd	Byproducts/Wastes			
	6.1_]	Type (Composition): <u>Silicon-broken wafers</u>	Quantity Produced:	<u>0 / load</u>	
		Physical Shape/Size:	Energy Content:	kWh/	
		Density:g/cm ³ , Water Solubility:	_g/l at°C:	pH:	
		Toxicity:Biodegradable:	Other Remarks:		
		Type of Disposal:	<u></u>		
		Input Material for:	Cost/(Credit)\$/	; Cost:	\$/\$
	6.2 Liqui	d Byproducts/Wastes (inorganic):			
	6.2_1	Type (Composition): water and silicon kerf	Quantity Produced: 33	3 &/ load_	
		Density: <u>1</u> g/cm ³ ; Suspended Solids: <u>silicon</u>	Amount: 2].08 g/1	pH:_>7	
		Toxicity: Heavy Metal Content:21.08	g/l Other Remarks:		
		Possible to separate the silicon from water and rec	cycle it.		
		Type of Disposal: Silicon filtered out and water re	ecycled thru cooling tow	ver	
		Input Material for:	Cost/(Credit)\$/	Cost:	\$/
				Carry:	\$/

	Form	12] of]
Process No. 2.4.02-06	-	<u>. 7/78</u>
7. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	55.04 \$/load
	7.22 Other Indirect Costs: % of 7.11 (0.059*(4.1) + 0.108*4.2)	\$/
	7.21 Total Operating Add-on Costs of Process:	56.80 \$/ load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	<u>.56.80\$/load</u>
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	1 <u>94.78;</u> \$/load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	251.58 \$/load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	194.78 \$/load
	7.36 Loading on Item 7.35 at Rate% .	\$/\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	446.36 \$/load
7.41 Theoretical Yield (or Conversion) work-in-process do not equal inpu		
7.42 Practical Yield	100%	
7.43 Effective Yield (7.41 x 7.42)	<u>1.06 m² / kg</u>	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	rk-in-Process per <u>15 m² / load</u>	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	<u>29.77</u> \$/_m ²
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	\$/ ^{m²}
		b



Process No. 0 2 -2



Pro	ocess No. 2	4 0 2 - 0 6		Form 15 Page] of]
0.	Output Specifi	cation:	Revision	Date7/78
	Name of item:_			
	Dimensions:			
		Solar grade silicon		
	Other Specific	ations: 200 µm thick, 3 µm deep fissures		
				<u></u>
				······································
	<u> </u>			
			······································	
	. <u></u>			
		<u></u>	<u>4,</u>	<u></u>
•			· · · · · · · · · · · · · · · · · · ·	•
	<u> </u>			

Process	No.	2	4	0	2	 1	6	
			لسمتشميا	 ப்ப	6	1	<u> </u>	l

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet generation

Subprocess: Ingot slicing

Option: Multiwire slicing

Yasunaga YQ-100 (Experimental 1978)

INDEX

Form	Pages	Rev.	Date	Remarks
1			4/78	Dates for all forms are the same.
2	1 to <u>1</u>			
3	1 to _0			
4	l to <u>1</u>			
5	l to <u> </u>			· · · · · · · · · · · · · · · · · · ·
6	1 to _1			
7	1 to _1			
8	1 to _1			·
9-1	l to _1	·		
9-2	l to _0_			
9-3	1 to _0_			·
10	1 to <u>1</u>			
11	1 to <u>1</u>	•		
12	1 to _1			
13-1	1 to <u>1</u>			
13-2	1 to <u>1</u>	[
14	1 to _1			
15	1 to _1			
16	1 to _0			

		Form 2
		Page 1 of 1
rocess No. $2, 4, 02 - 16$	Revision	Date 4/78
	U.1 Value Audeu.	9/
rocess Description: <u>Multiwire slurry wafering</u> Data obtained from a JPL conducted demonstration run.		
215 slices were made per load and 0.4 mm pitch guides were used		
Input Specification:		
Input Specification:		
Name of Item: Prepared machine load from 2.4:01:16		
Dimensions: 7.6 cm-diameter, 8.8cm long, 0.94 kg/load		
Material: High purity silicon		
Other Specifications:Ingots are mounted on ceramic block		، بر بر ب
	· · · · · · · · · · · · · · · · · · ·	
1.1 Quantity Required: 1.061 kg / load	Unit Cost: 155.	.98 \$/ <u>kg</u>
	1.2 Input Value:	\$/
	1.3 Input Cost:	165.50 s/ load

Note to Item 1.3: Use price, if input produced in own plant.

Proc	ess No	-2.4.02-16	Form 4
2,2		Type, Abrasive	Page <u>1</u> of Date <u>4/78</u>
		Specification: 13 µm GC 1200 abrasive, concentration 1.5 kg/%; Is used twice. 5 kg needed per load or 2.5 kg consumed per load	
	2.2 <u>2</u>	Quantity Required: 2.5 kg/load; Unit Cost: 12.10 \$/ kg ; Cost: Type: Lapping oil vehicle for abrasive	<u>30.25</u> \$/ <u>2</u> loads
		Specification: <u>Is used for two loads;</u> <u>3.25 & used in each load and l.625</u> & consumed in each load	
	2.2_	Quantity Required;	; <u>2.031 s/ 2 loads</u>
		Specification:	
		Quantity Required:; Unit Cost:\$/; Cost	

Proc	ess No	. 2	4 0 2 - 1 6		Form 5 Page 1 of 1
2.3	Expen	dable 1	Cooling:		
	2.3 1	Type:	Steel wire, 0.16 mm dia. Can be used th	Revis	ion Date <u>4/78</u>
				$\underline{m} / 10ad$ Unit Cost: 5.7×10^{-3} / m Cost:	32.30 \$/ load
	2.3_	Type:			
				/: Unit Cost:\$/ Cost:	\$/
	2.3_	Type:			
				/: Unit Cost:\$/ Cost:	\$/
	2.3_	Type:			
				: Unit Cost:\$/ Cost:	\$/
				2.3 Subtotal Expendable Tooling:	<u>32.30</u> \$/ <u>load</u>
2.4	Energy		Flootnicel 0.6 kW total names for main		
	2.4 _	Type:	Electrical, 0.6 kW total power for main	and auxiliary motors	
			Quantity Required: 5.4	<u>kWh/load</u> : Unit Cost: 0.0319 \$/ <u>kWh</u> Cost:	0.172 \$/ load
	2.4_	Type:			
			Quantity Required:	: Unit Cost:\$/ Cost:	\$/\$/
				2.4 Subtotal Energy Costs:	
				2.5 Subtotal 2.1 to 2.4:	64.75 \$/load
				2.6 Handling Charge: <u>5.26 %</u> of item 2.5	5 3.40 \$/load

2.7 Subtotal Materials and Supplies: (2.5 + 2.6) 68.15 \$/load

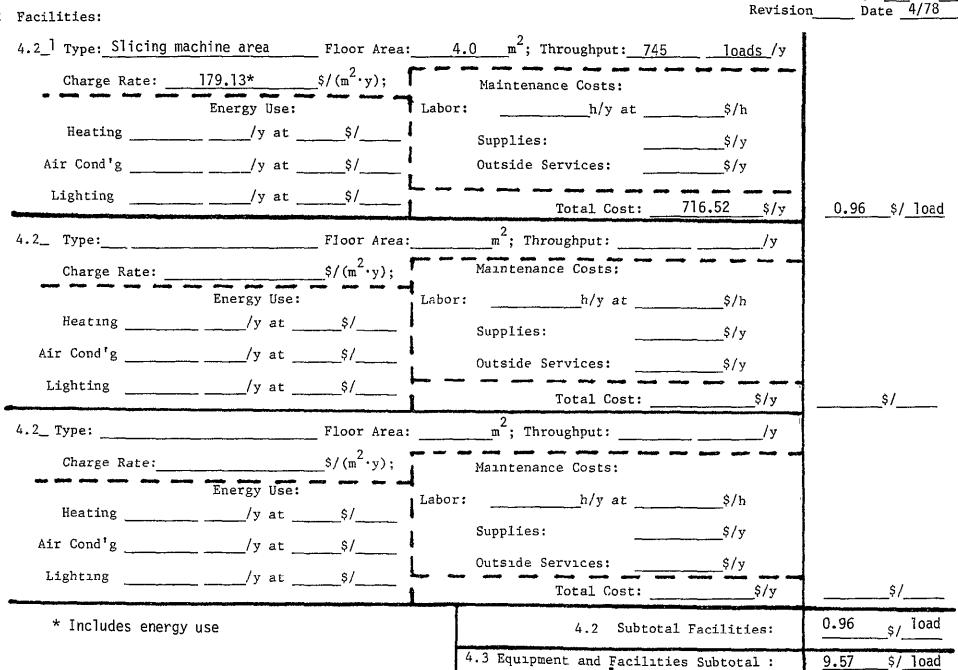
Process No.	2.4.02-16		Revision	Form 6 Page <u>1</u> of <u>1</u> Date 4/78
3.1 Direct				
3.1]	Category: <u>Semiconductor</u> Assembler	Activity:	Machine loading/unloading	
	(SAMICS B3096D) Amount Required: 0.25 h/ load	; Rate: \$ <u>3.89</u>	_/h; Load <u>36.0</u> %; Cost:	<u>].32</u> ^{\$/} load
3.12	Category: Semiconductor Assembler	Activity:_ma	chine supervision	
	(SAMICS B3096D) Amount Required: 0.33 h/ load	; Rate: \$ <u>3.89</u>	_/h; Load <u>36.0</u> %; Cost:	1.763 ^{\$/} _load
3.13	Category: <u>Maintenance Mechanic</u>	Activity:	re_changing/adjusting	
_	(SAMICS B3736D) Amount Required: 0.5 h/_load	; Rate: \$ <u>5,67</u>	_/h; Load <u>36.0</u> %; Cost:	
			3.1 Direct Labor Subtotal:	6.40 \$/load
3.2 Indire	ct Labor: 25% of direct			
3.2	Category:	Activity:		
	Amount Required:h/	; Rate: \$	_/h; Load%; Cost:	\$/
3.2_	Category:	Activity:		
	Amount Required:h/			\$/
3.2_	Category:	Activity:		
	Amount Required:h/			<u>\$/</u>
			3.2 Indirect Labor Subtotal:	<u>1.73</u> \$/ <u>load</u>
•			3.3 Subtotal 3.1 and 3.2	8.13_\$/_load
			3.4 Overhead on Labor: 5.26 %	0.43 \$/ load
			3.5 Subtotal Labor	<u>8.56</u> \$/ <u>load</u>

-

Process No. 2 4 0 2 - 1 6		Form 7 Page <u>]</u> of <u>]</u>
4.1 Equipment	Revision_	Date
4.1_] Type: <u>Yasunaga YQ-100_Slicing_machine</u>		
Cost: 30,000 _\$; Installation Cost:\$; Throughput:745 loads	/h;y	
Plant Oper'g Time_8280 h/y; Machine Avail'ty:_90_%; Machine Oper'g Time	<u>7452</u> h/y	
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:h.	<u>a</u> \$/y	
Useful Life:y; Charge Rate:2].4 _% of Cost/y; Capital Cost:6420	\$/y	<u>8.61</u> \$/ <u>load</u>
4.1_ Type:		
Cost:\$; Installation Cost:\$; Throughput:	/h;	
Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y	
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	\$/y	
Useful Life:y; Charge Rate:% of Cost/y; Capıtal Cost:	\$/y	\$/
4.1Type:		
Cost:\$; Installation Cost:\$; Throughput:	/h;	
Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y	
Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	\$/y	
Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y	\$/
4.1 Subtotal Equip	oment Cost:	8.61 _{\$/} load

Process No. 2 . 4 . 0 2 - 1

4.2 Facilities:



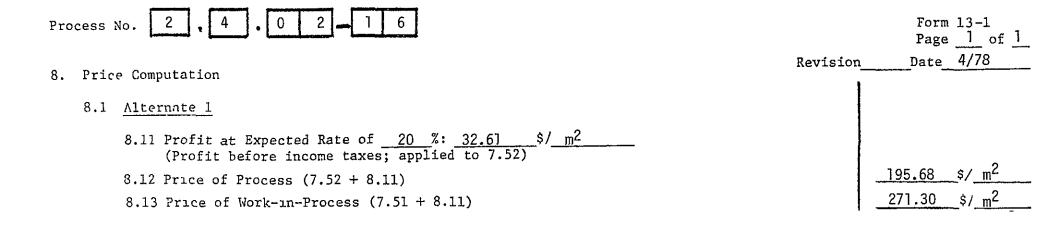
Form 8

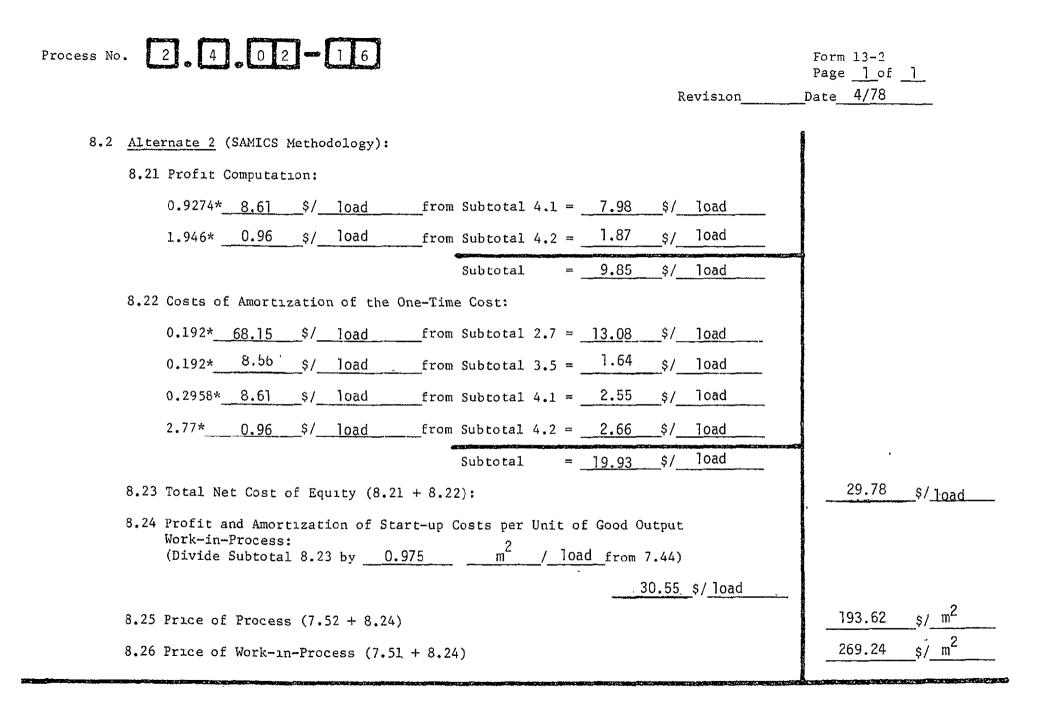
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		Form	9-1	
		Page	<u>]</u> of	1
Process	No. $2, 4, 02 - 16$	vision	Date	4/78
5. Sal	vaged Material (Work-in-process)			
5.3	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit) 0.479	kg / load		
5.2	<pre>1 Input Work-in-process 1. Not Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1) 0.456</pre>	kg / load		
5.3	2 Net Amount of 5.21 which is sold for Credit As-Is or After Applying Re-Process	/		
5.3	3 Credit for 5.22 at the Market Value of\$/:	\$/		
5.3	4 Cost of Reprocessing Material of 5.22 at the Average Reprocessing Cost of\$/:	\$/		
5.	5 Net Credit for 5.22 (5.23 minus 5.24):			\$/
5.	Material of Type 1. Lost in Process (5.21 minus 5.22) <u>0.456</u>	<u>kg / load</u>		
5.	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)			\$/_load
5.	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)	•		74.72 \$/load
Sa	vaged Materials Summary:		na sugar	
5.	3 Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)			\$/

Pro	cess No.	2, 4, 0, 2, -1, 6			Form 10 Page <u>1</u> of <u>1</u>
6.	Byprodu	ucts and Wastes	Revi	sion	Date4/78
	6.1 Sol	lid Byproducts/Wastes			
	6.1	L_ Type (Composition):	Quantity Produced:	/	
		Physical Shape/Size:	Energy Content:kW	h/	
		Density:g/cm ³ ; Water Solubility:0	g/l at ^O C; pH:		
		Toxicity:Biodegradable:	Other Remarks:		
		·			
		Type of Disposal:			
		Input Material for:	_ Cost/(Credit)\$/;	Cost:	\$/
	6.2 Liq	uid Byproducts/Wastes (inorganic):			
	6.2	2_] Type (Composition): GC oil slurry	Quantity Produced: <u>1.63 &/ 1</u>	oad	
		Density: <u>~0.95</u> g/cm ³ ; Suspended Solids: <u>GC_abrasive</u>	Amount: <u>1.5</u> kg/1 pH:		
•		Toxicity: Heavy Metal Content:	_mg/1 Other Remarks:		
		Slurry also contains silicon kerf at a concentration	on of 0.48 kg/l (790 g/load)		
		Type of Disposal:			
		Input Material for:		Cost:	\$/
			·		
			с	arry:	\$/
				İ	

	Form Page	12]_of_]_
rocess No. 2.4.02-16	RevisionDate_	4/78
. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	\$/_load
	7.22 Other Indirect Costs: 2)- % of 7.11	0.61 \$/ load
	7.21 Total Operating Add-on Costs of Process:	86,89 \$/ load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	86.89 \$/ load
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	<u>158.01</u> \$/ load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	74.72 \$/_load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	232.74 \$/load
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu		
7.42 Practical Yield	100 %	
7.43 Effective Yield (7.41 x 7.42)	0,936 kg/load	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	rk-in-Process per0.975 m ² / load	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	238.69 \$/ m ²
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	<u>163.07</u> \$/ ^{m2}





Process No. 2 . 4 . 0 2 -	1 6	Form 14 Page <u>1</u> of <u>1</u>
9. Process Economic Evaluation:		RevisionDate4/78
	9.1 Process Cost Balance (7.52 - 0.1)	\$/
	9.2 Relative Process Performance (9.1 - 0.1)	
	9.3 Output Cost (7.51)	<u>238.69</u> \$/ m ²
	9.4 Output Value (0.2 + 0.1)	\$/
	9.5 Relative Excess Cost (9.3 - 9.4) - 9.4	

Pro	ocess No. 2 4 0 2 - 1 6		Form 15 Page <u>1</u> of <u>1</u>
		Revision	Date <u>4/78</u>
0.	Output Specification:		
	Name of item:	<u> </u>	
	Dimensions: 7.6 cm in dia., 0.21 + 0.01 mm thickness	······································	
	Material:High purity silicon		
	Other Specifications: Kerf thickness, 0.2mm		
	Subsurface damage depth is approximately 15 µm		,
		,,,,,,,,,,	
	/		
			
		······································	
		<u></u>	
		<u></u>	
		<u> </u>	
		······	

Process No. 2 . 4 . 0 2 - 1 6

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet Generation

Subprocess: Ingot Slicing

Option: Multiwire Slicing - 1982 projection using

the Yasunaga YQ-100 Slicing System

INDEX

Form	Pages	Rev.	Date	<u>Remarks</u>
1			_4/78	<u>All forms have this date</u>
2	l to <u>1</u>			*
3	1 to <u>0</u>			
4	1 to <u>1</u>			
5	1 to <u>1</u>			•
6	1 to _1			
7	1 to <u>1</u>			
8	1 to _1	•		·
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9-2	1 to _0			1
9-3	1 to _0			
10	1 to <u>1</u>			
11	1 to <u>1</u>			
12	1 to <u>1</u>			۰.
13-1	1 to <u>1</u>			
13-2	1 to <u>1</u>			
14	1 to <u>1</u>			
15	1 to <u>1</u>			
16	l to <u>0</u>			

Form 1

(-3

Form 2

					Page <u>1</u> of <u>1</u>
				Revision	Date
Proc	cess No. 2.4	02-16		0.1 Value #dd#d:	<u>128 \$/ m²</u>
Prod	cess Description:	<u>Multiwire slurry wafering as p</u>	performed by the Yasunaga	slicing system	
		data projected from using a 0.3 mm	pitch roller,		
		(333 slices per load).			
1.	Input Specificati	lon:			
	Name of Item:	Prepared machine load from 2.4:0	1:0		
	Dimensions:	10-cm diameter, 10-cm long, 1.83	7 kg/load.		
	Material:	1 silīcon crystal mountec	on ceramic block		
	Other Specificati	.ons:			
		See 2.4:01:0			
	<u> </u>	<u></u>	*****		
	<u></u>				

		1.1 Quantity Required	1: <u>1.837 kg /load</u>	Unit Cost:	.73.31 \$/ kg
				1.2 Input Value:	\$/
				1.3 Input Cost:	134.07 \$/load

Note to Item 1.3: Use price, if input produced in own plant.

Process No. $2.4.02 - 16$		Form 4
2.2 Indirect Materials (incl. supplies and non-energy utilities):	Dominian	Page <u>1</u> of <u>1</u>
2.2 <u>1</u> Type: Abrasive slurry	;	Date <u>4/78</u>
Specification: 5 µm SiC abrasive, concentration is not available		
Estimated from materials cost given for slicing a 7.6 cm diameter ingot wi	<u>th</u>	
the Yasunaga saw by JPL and using the relationship $C_2 = C_1 \begin{pmatrix} -2 & -1 \\ -2 & -1 \end{pmatrix}$ (T = slicing time, A = water area). Quantity Required:	; Cost:	1 <u>07.55</u> \$/load
2.2 Type:		
Specification:		
Quantity Required:; Unit Cost:\$/;	; Cost:	\$/
2.2_ Type:		
Specification:		
	• 	
Quantity Required:/; Unit Cost:\$/	; Cost:	\$/
2.2 Subtotal Indi	rect Materials:	<u>107.55 \$/load</u>

Proc	ess No	. 2.4.	0 2 - 1 6			Form 5	
2.3	Expen	dable Tooling:	ν			Page <u>1</u> of <u>1</u>	
	2.3 <u>1</u>	Type: <u>Steel w</u>	vire; 0.08 mm diameter.	<u></u>	Revisi	on Date4/78	
		<u> </u>	Quantity Required: <u>12,000</u>	_m_/ <u>load</u> : Unit Cost: <u>0.004</u> \$/_m	Cost:	<u>47.83</u> \$/ <u>load</u>	
	2.3_	Туре:		······································			
			Quantity Required:	: Unit Cost:\$/	_ Cost:	\$/	
	2.3_	Туре:	·				
			Quantity Required:	/: Unit Cost:\$/	_ Cost:	\$/	
	2.3_	Туре:					
		<u></u>	Quantity Required:	: Unit Cost:\$/	_ Cost:	\$/	
				2.3 Subtotal Expendable To	oling:	<u>47.83</u> \$/ <u>load</u>	
2.4	Energ						
	2.4 <u>1</u>	Type: <u>Electri</u>	<u>cal, 0.6 kW total power for main and</u>	d.auxiliary motors	- 1		
			_Quantity Required: <u>18 kWh</u> / _	<u>load</u> : Unit Cost: 0.0319 \$/ <u>kW</u>	h_ Cost:	<u>0.57</u> \$/ <u>load</u>	
	2.4	Туре:		14	-		
			Quantity Required:	: Unit Cost:\$/	Cost:	<u>0.57 \$/load</u>	
				2.4 · Subtotal Energy	Costs:	0.57 \$/load	
	<u></u>			2.5 Subtotal 2.1 to 2.4:		155.44 \$/load	
				2.6 Handling Charge: 5.26 % of :	item 2.5	<u>8.18</u> \$/ <u>load</u>	
				2.7 Subtotal Materials and Suppl (2.5 + 2.6)	ies:	<u>163.61</u> \$/ <u>load</u>	

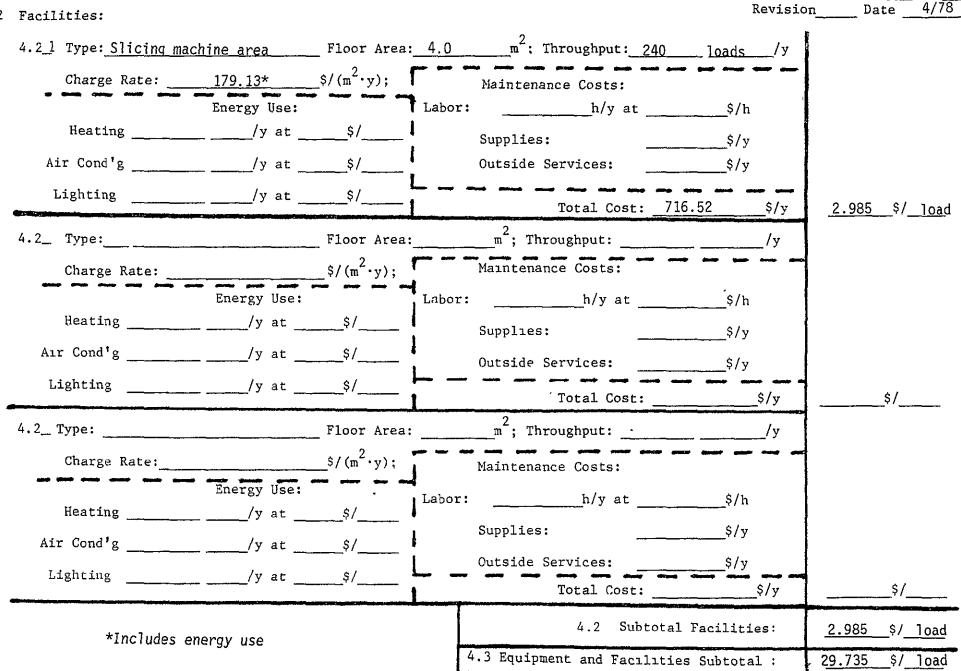
•

Process No. 2.4.02-16		Revision	Form 6 Page <u>1</u> of <u>1</u> Date <u>4/78</u>
<pre>3.1 Direct Labor: (Estimated) 3.1_1 Category: <u>Semiconductor Assembler</u> (SAMICS B3096D) Amount Required: 0.25 h/load</pre>	; Rate: \$ 3.90	Machine.loading/unloading/h; Load36.0 %; Cost:	<u> 1.32 \$/load </u>
3.12 Category: <u>Semiconductor Assembler</u> (SAMICS B3096D) Amount Required: <u>1.00</u> h/ <u>load</u>	; Rate: \$ <u>3.90</u>	achine supervision	<u>5.30</u> \$/ <u>load</u>
3.1_3 Category: <u>Maintenance Mechanic</u> (SAMICS B3704D) Amount Required:0.5h/_load_ 3.2 Indirect Labor: 25% of direct		/h; Load <u>36.0</u> %; Cost:	3.86 \$/load 10.48 \$/load
3.2 Indiffect Labor: 25% of diffect	Activity:		
Amount Required:h/	; Rate: \$	/h; Load%; Cost:	\$/
3.2_ Category:h/h/h/h/h/h/h/h/h/h/	; Rate: \$	/h; Load%; Cost:	\$/
3.2_ Category: Amount Required:h/			\$/
		3.2 Indirect Labor Subtotal:	2.62 \$/ <u>load</u>
		3.3 Subtotal 3.1 and 3.2	13.10 \$/load
		3.4 Overhead on Labor: <u>5.26 %</u>	0.69 \$/10ad
		3.5 Subtotal Labor	13.79 \$/ <u>load</u>

Proc	ess No	. 2 . 4 . 0 2 - 1 6		Form 7 Page <u>1</u>	
4.1	Equip	ment	Revision_	Date	4/78
	4.1 <u>1</u>	Type: Yasunaga YQ-100 Slicing Machine			
		Cost: 30,000	_/¤;y		
		Plant Oper'g Time_8280 h/y; Machine Avail'ty:_90_%; Machine Oper'g Time_745	2h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	\$/y		
		Useful Life: 7 y; Charge Rate: 21.4 % of Cost/y; Capital Cost: .6420	\$/y	26.75	\$/ <u>load</u>
	4.1_	Туре:			
		Cost:\$; Installation Cost·\$; Throughput:	_/h;		
	•	Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		\$/
	4.1_	Type:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y	, <u> </u>	\$/
		4.1 Subtotal Equipmen	t Cost:	26.75	\$/ <u>load</u>

Process No. 2 . 4 . 0 2 - 1 6

4.2 Facilities:



Form 8

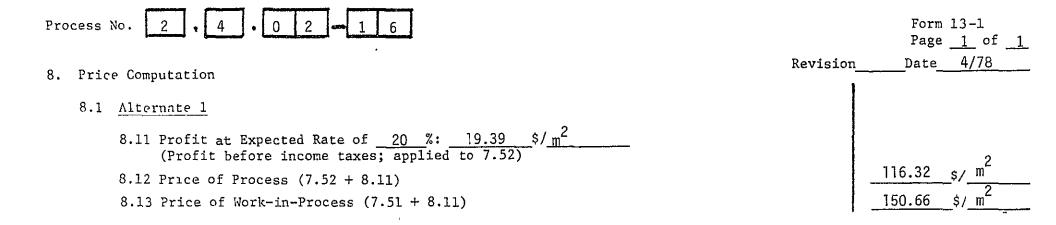
Page 1 of 1

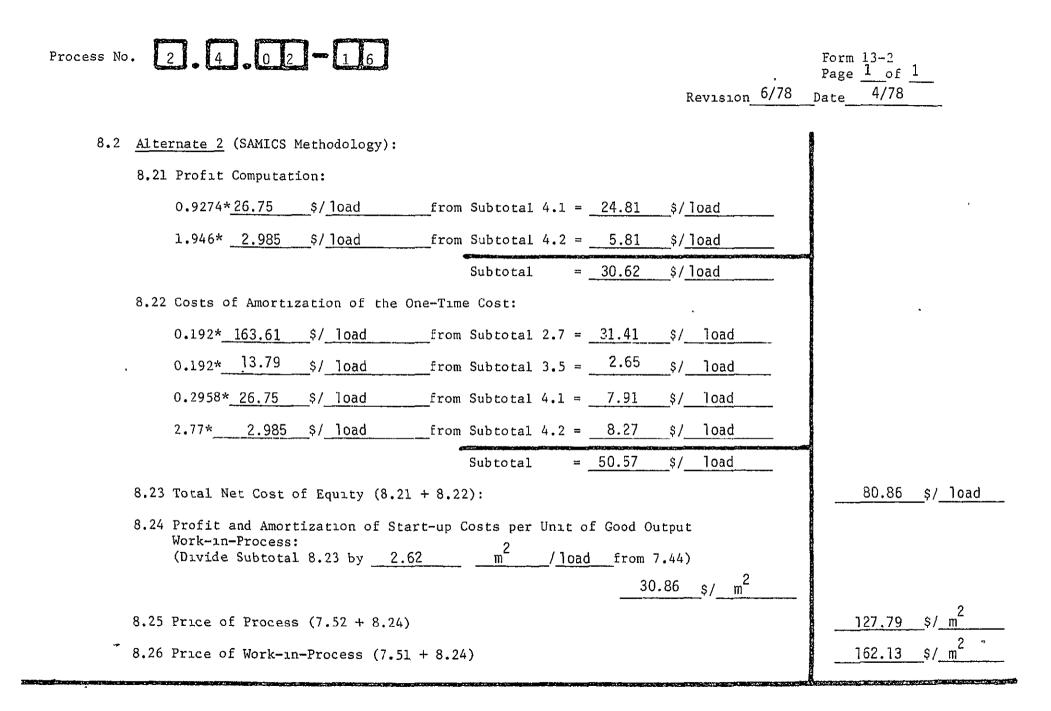
			Fc	orm 9-1		
			Pa	ige <u>1</u> oi	E <u>1</u>	
Pro	cess No	2.4.02-16	Revision	Date	e <u>4/78</u>	
5.	Salvag	ged Material (Work-in-process)				
	5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	<u>1.227 kg / loa</u>	ad		
	5.21	Input Work-in-process 1. <u>Not</u> Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	0.613 kg / loa	1d		
	5.22	Net Amount of 5.21 which is sold for Credit As-Is or After Applying Re-Process	/			
	5.23	Credit for 5.22 at the Market Value of\$/:	\$/			
	5.24	Cost of Reprocessing Material of 5.22 At the Average Reprocessing Cost of\$/:	\$/			
	5.25	Net Credit for 5.22 (5.23 minus 5.24):		:	 	_\$/
_	5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)	<u>0.613 kg / load</u>			
	5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)			_44.94	\$/ <u>load</u>
	5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)			89.95	\$/ <u>load</u>
-	Salvag	ed Materials Summary:		-		
	5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)				\$/

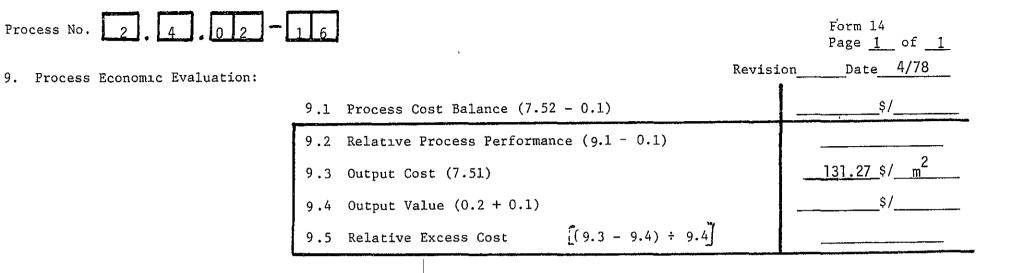
Pro	cess No.	2, 4, 02 - 16			Form 10 Page <u>1</u> of <u>1</u>
6.	Byproduct	s and Wastes		Revision	Date 4/78
	6.1 Solid	Byproducts/Wastes			
	6.1 <u>1</u>	Type (Composition): Silicon chips and dust	Quantity Produced:	<u>0 kg / load</u>	
		Physical Shape/Size:	Energy Content:		
		Density: 2.34 g/cm ³ ; Water Solubility: 0	_g/lat ⁰ C	; pH:	
		Toxicity:Biodegradable:NO	Other Remarks:		
		Type of Disposal:			
		Input Material for:	Cost/(Credit)	\$/; Cost:	\$/
	6.2 Liqui	d Byproducts/Wastes (inorganic):			
	6.21	Type (Composition): Abrasive suspended in PC oil	Quantity Produced:	5.4 & / load	
		Density:g/cm ³ ; Suspended Solids: abrasive and k	erfAmount:mg/1	рН:	
		Toxicity: Heavy Metal Content:	mg/1 Other Remarks	:	
		abrasive concentration is approximately 1.5 k	g/ L	<u> </u>	
		Type of Disposal:			
		Input Material for:			\$/
			<u></u>	Carry:	\$/

Form 12 Page<u>1</u> of <u>1</u>

Process No. 2.4.02-16	RevisionDate	4/78
7. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	207.135_\$/load
	7.22 Other Indirect Costs:% of 7.11	\$/_load
	7.21 Total Operating Add-on Costs of Process:	209.03 \$/_load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	209.03 \$/_load
	7.32 Credit for Salvaged Material (5.8)	\$/\$/
	7.33 Cost of Work-in-Process Lost (5.3)	\$/_load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	<u>253.97</u> \$/ <u>load</u>
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	\$/_load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	<u>343.92 \$/ load</u>
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu	Rate, if output units of 2	
7.42 Practical Yield	<u>100</u> %	
7.43 Effective Yield (7.41 x 7.42)	1.42 m^2 / kg	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	rk-in-Process per <u>2.62 m² / load</u>	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	<u>131.27</u> \$/ m ²
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	\$/m ²
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Process No. 2 4 0 2 - 1 6		Form 1:5 Page <u>1</u> of <u>1</u>
	Revision	Date <u>4/78</u>
0. Output Specification:		
Name of item: <u>Silicon wafers, as-cut</u>		
Dimensions: 10 cm in dia., 0.2mm Thickness	<u></u>	
Material: high purity silicon		
Other Specifications: 0.1 mm kerf Thickness		······································
333 wafers sliced per load		
	,	
	<u> </u>	
τ		
		*** <u></u> ** <u>_</u> **

University of Pennsylvania

PROCESS CHARACTERIZATION

(UPPC)

Process: Sheet generation

Subprocess: Wafer generation

Option: Inner-diameter slicing of a rotating

crystal as proposed by STC for 1982.

INDEX

Form	Pages	Rev.	Date	Remarks
1			8/78	Date same for all forms
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4	1 to _1			
5	l to _1_			
6	l to			
7	l to _]_			
8	l to <u> </u>			
9-1	1 to <u>1</u>		·	
9-2	1 to _0_			
9-3	1 to _0_]		
10	1 to <u>0</u>			
11	1 to <u>0</u>			
12	1 to <u>1</u>			
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13-2	1 to <u>1</u>		'	
14	1 to _0			
15	1 to _]			
16	1 to _0_			

Form 1

Form	2
TOTH	<u> </u>

		Page <u>l</u> of <u>l</u>
	Revision	Date <u>8/78</u>
Process No. $2, 4, 02 - 17$	0.1 Value Added:	\$/
Process Description: Inner-diameter slicing of a rotating crystal as project	ed by STC for 1982.	······································
1. Input Specification:		
Name of Item,		
Dimensions: <u>10-cm diameter, 100-cm long and mass is 18.378 kg</u>		
Material:High purity silicon		
Other Specifications: <u>Grounded ingot, see 2,4-0]-0]</u>		
		۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ - ۲۰۰۰ -
1.1 Quantity Required: 18.378 kg / load	Unit Cost: 7	71.75_\$/ <u>kg</u>
	1.2 Input Value:	ş/
	1.3 Input Cost:	1318.66 \$/load
	110 miles 00001	

Note to Item 1.3: Use price, if input produced in own plant.

Process No	. 2.4.02-17			Form 4
				Page 1 of 1
2.2 Indir	ect Materials (incl. supplies and non-	energy utilities):	Revision	Date <u>8/78</u>
2.2	Type: <u>Alumina dress stick, etc.</u>		;	
-	Specification:			
		•		
	Quantity Required:	; Unit Cost:\$/	; Cost:	<u>n.a.</u> \$/ load
2.2_	Туре			
			<u></u>	
	Quantity Required:	/; Unit Cost:\$/	; Cost:	\$/
2.2	Туре:			
_				
	Quantity Required:	; Unit Cost:\$/	; Cost:	\$/\$/
			· · · · · · · · · · · · · · · · · · ·	
		2.2 Subtotal Ind:	rect Naterials:	\$/_load
		L	<u></u>	

Proc	ess No	o. [2]	. 4 . 0 2 - 1 7					Form	5
2.3	Exper	ndable I	Cooling:					Page	1_of1_
	2.3 <u>]</u>	Type:	STC-16 ID diamond-coated blade				Revisi	on	
	2.3_		Quantity Required: 0.5			<u>50</u> \$/ <u>b]a</u>	<u>de</u> Cost:		\$/
			Quantity Required:	/:	Unit Cost: _		Cost:		\$/
		<u></u>	Quantity Required:	/:	Unit Cost: _		 Cost:		\$/
•			Quantity Required:		Unit Cost:				\$/ \$/_load
2.4	Energy 2.4 <u>1</u>	Type: _	Power requirement 1s 2 kW	P					
	2.4_		Quantity Required: <u>102 kWh/lo</u> ad			<u>0319</u> \$/ <u>kWh</u>	Cost:	3,25	\$/ <u>load</u>
			Quantity Required:			\$/ al Energy (3.25	
	·		•••••••••••••••••••••••••••••••••••••••	1	al 2.1 to 2.4 ng Charge: <u>5.</u>	4 2		28.25	\$/ <u>load</u> \$/_load
				2.7 Subtota (2.5 +	al Materials 2.6)	and Supplie	25:	29.74	\$/ <u>load</u>

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Process No.	2 4 0 2 - 1 7			Revision_	Form 6 - Page <u>1</u> of <u>1</u>
3.1 Direct					
3.1]	Uacchory -	Activity:	Machine loading/	/unloading	
	(SAMICS B3096D) Amount Required: 0.50 h/ h	; Rate: \$ <u>3.90</u>	_/h; Load <u>36</u>	%; Cost:	2.65_\$/ <u>load</u>
3.12	Category: Semiconductor distance	Activity:	<u>machine supervi</u>	sion	
•••- <u>-</u>	(SAMICS B3096D) Amount Required: 2.81 h/ h	; Rate: \$	_/h; Load36	%; Cost:	<u>14.90</u> _\$/ <u>load</u>
3 1 3	Category: Maintenance Mechanic	Activity:	Cutting tool ch	nange	
J•±	(SAMICS B3736D) Amount Required: 0.5 h/ h	; Rate: \$5.67	_/h; Load <u>36</u>	5%; Cost:	<u>3.86</u> \$/ <u>load</u>
	,		3.1 Direct La	bor Subtotal:	21.41 \$/load
3.2 Indire	ct Labor: Taken as 25% of direct				
<u>э</u>	Category:	Activity:			
	Amount Required:h/	; Rate: \$	/h; Load	%; Cost:	\$/
3.2	Category:	Activity:			
	Amount Required:h/	; Rate: \$	/h; Load	%; Cost:	\$/
3.2	Category:	Activity:		<u> </u>	
<u> </u>	Amount Required:h/	; Rate: \$	/h; Load	%; Cost:	\$/
			3.2 Indirect	Labor Subtotal:	<u>5.35</u> \$/load
			3.3 Subtotal	3.1 and 3.2	26.76 \$/ load
			3.4 Overhead	on Labor: <u>5.26</u> %	
			3.5 Subtotal	Labor	\$/_load

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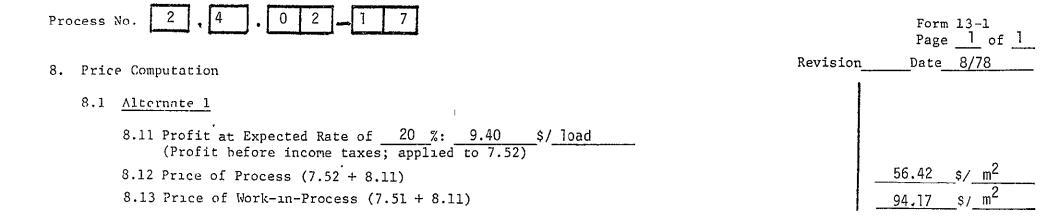
Proc	ess No	. 2 . 4 . 0 2 - 1 7	Revision	-	of <u>1</u> 8/78
4.1	Equip	ment	1		
	4.1_1	Type: STC ID slicing machine with capacity to rotate ingot			
		Cost: 45,000 \$; Installation Cost: \$; Throughput: 158 loads	_/カ;y		
		Plant Oper'g Time8280h/y; Machine Avail'ty:99 %; Machine Oper'g Time_8197.2	2h/y		
		Servicing Costs: Labor52h/y at8.12\$/h;Parts or Outside Service:300	\$/y		
		Useful Life:y; Charge Rate: 21.35 % of Cost/y, Capital Cost: 10,329.74	\$/y	<u>65.38</u>	\$/ <u>load</u>
	4.1_	Type:			
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y		_\$/
	4.1_	Type:	•		
		Cost:\$; Installation Cost:\$; Throughput:	_/h;		
		Plant Oper'g Timeh/y; Machine Avail'ty:%; Machine Oper'g Time	h/y		
		Servicing Costs: Laborh/y at\$/h;Parts or Outside Service:	_\$/y		
		Useful Life:y; Charge Rate:% of Cost/y; Capital Cost:	\$/y	<u></u>	_\$/
		4.1 Subtotal Equipmen	t Cost:	65.38	_ _{S/_} load
			· · · · · · · · · · · · · · · · · · ·		

Proc	ess No. 2, 4, 0	2 - 1 7						Form 8 Page 1 o	fī
4.2	Facilities:						Revision_	Date _8/	
				<u> </u>	m ² ; Throughput:	158 loads	/y		
	Charge Rate:		-		Maintenance Costs:				
	Heating		\$/ 		:h/y ath/y at	\$/1 \$/3	l l		
	Air Cond'g	/y at	\$/		Outside Services: _	\$/	7		
	Lighting	/y at	\$/		Total Cost:	1343.48	\$/y	8.50 \$/_1	oad
	4.2_ Type:		_ Floor Area:		m ² ; Throughput:		_/y		
	Charge Rate:		$\frac{(m^2 \cdot y)}{(m^2 \cdot y)};$	· · ·	Maintenance Costs:	لنيو جدين جديد -	• ••• ••		
		Energy Use:		Labor	:h/y at	\$/ł	1 		
	Heating	/y at	\$/		Supplies:	\$/3	,		
	Air Cond'g	/y at	\$/	1	Outside Services:	\$/:	,		
_	Lighting	/y at	\$/	 	Total Cost:	40	\$ /y	\$/	
_	4.2_ Type:		Floor Area:		m ² ; Throughput:		_/y		
	Charge Rate:		_\$/(m ² ·y);	949 - 149 - 14 	Maintenance Costs:				
	Heating	Energy Use: /y at		Labor	:h/y at	\$/t	ı		
	Air Cond'g			ł	Supplies:	\$/y	7		
	Lighting	/y at			Outside Services: Total Cost:	\$/y	_\$/y	\$/	
	*Includes energy use				4.2 Subt	otal Facilit	ies:	8.50 ş/ lo	bad
				t	4.3 Equipment and Facil	ıties Subtot	al:	73.87 \$/ 10	bad

					Form	9-1	
					Page	<u>]</u> of	1
Pro	cess No	2.2.4.02-17		Revisi	on	Date	8/78
5.	Salva	ged Material (Work-in-process)				1	
	5.1	Quantity of Work-in-Process 1. Contained in Good Output Work-in-Process (per Computation Unit)	9.030	<u>kq</u>	/_ <u>load</u> /		
	5.21	Input Work-in-process 1. Not Contained in Good Output Work-in-Process ("Amount Required" from 1.1 minus 5.1)	9.347	kg	/ load		
	5.22	Net Amount of 5.21 which is sold for Credit As-Is or After Applying Re-Process					
	5.23	Credit for 5.22 at the Market Value of\$/:			\$/		
	5.24	Cost of Reprocessing Material of 5.22 At the Average Reprocessing Cost of\$/:	<u>,</u>		\$/		
	5.25	Net Credit for 5.22 (5.23 minus 5.24):					\$/
_	5.26	Material of Type 1. Lost in Process (5.21 minus 5.22)	9.347	kg	load		
-	5.3	Cost of Work-in-Process Lost (Amount 5.26 Times Unit Cost 1.1)					<u>670.66 \$/10ad</u>
	5.4	Cost of Work-in-Process Contained in Good Output Work-in-Process (Amount 5.2 Times Unit Cost from 1.1)					
-	Salvag	ed Materials Summary:					
	5.8	Total Net Credits for All Salvaged Materials (5.25 + 5.67 + 5.76)			α _ Par Net Son (− 20 − 26 (Net) i A		\$/\$

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	Form	12 l of l
rocess No. 2 . 4 . 0 2 - 1 7		8/78
. Process Cost Computation	7.11 Manufacturing Add-On Costs (sum of 2.7, 3.5, 4.3, 6.)	<u>131.69</u> \$/ load
	7.22 Other Indirect Costs:% of 7.11	\$/_load
	7.21 Total Operating Add-on Costs of Process:	. <u>136:31</u> \$/ load
	7.22 G & A% of 7.21	\$/
	7.31 Total Gross Add-On Cost of Process	136,31 \$/ load
	7.32 Credit for Salvaged Material (5.8)	\$/
	7.33 Cost of Work-in-Process Lost (5.3)	_670.66_\$/_load
	7.34 Specific Add-On Cost of Process (7.31 + 7.33)-(7.32)	_806.97 \$/ load
	7.35 Cost of Input Work-in-Process Contained in Good Output Work-in-Process (5.4)	647.92 \$/ load
	7.36 Loading on Item 7.35 at Rate% .	\$/
	7.37 Cost of Output Work-in-Process (7.34 + 7.35 + 7.36)	1454.89 \$/ load
7.41 Theoretical Yield (or Conversion work-in-process do not equal inpu		
7.42 Practical Yield	95_%	
7.43 Effective Yield (7.41 x 7.42)	<u>0.933 m² kg</u>	
7.44 Number of Units of Good Output Wo Computation Unit Used up to 7.35	rk-in-Process per 17.161 m ² / load	
	7.51 Cost of Unit of Good Output Work-in- Process (7.37 ÷ 7.44)	
	7.52 Specific Add-On Cost per Unit of Good Output Work-in-Process (7.34 ÷ 7.44)	47.02 _{\$/} m ²



Process No. 2 4 0 2 - 1 7

Form 13-2 Page <u>1</u> of <u>1</u> Revision Date <u>8/78</u>

and the second
8.2 <u>Alternate 2</u> (SAMICS Methodology):	ł
8.21 Profit Computation:	
$0.9274 \pm 65.38 \text{ s/ load}$ from Subtotal 4.1 = 60.63 s/ load	
1.946* 8.50 s/ load from Subtotal 4.2 = 16.54 s/ load	
Subtotal = 77.17 \$/ load	
8.22 Costs of Amortization of the One-Time Cost:	
0.192* 29.74 s/ load from Subtotal 2.7 = 5.71 s/ load	
0.192* 28.17 \$/ load from Subtotal 3.5 = .5.40 \$/ load	
0.2958* 65.38 \$/ load from Subtotal 4.1 = 19.33 \$/ load	
2.77* 8.50 \$/ load from Subtotal 4.2 = 23.55 \$/ load	
Subtotal = 54.00 \$/ load	
8.23 Total Net Cost of Equity (8.21 + 8.22):	137.17 \$/ load
8.24 Profit and Amortization of Start-up Costs per Unit of Good Output Work-in-Process: (Divide Subtotal 8.23 by <u>17.161</u> m ² / load from 7.44)	3
7.64 \$/ m ²	
8.25 Price of Process (7.52 + 8.24)	54.66\$/_m ²
8.26 Price of Work-in-Process (7.51 + 8.24)	<u>92.41</u> \$/ <u>m</u> ²

Process No. 2 4 0 2 - 1 7	Form 15 Page <u>1</u> of <u>1</u>
	visionDate8/78
Name of item:Silicon wafers as cut	
Dimensions: 10-cm diameter, 225 µm thick, 210 µm kerf, 350 wafers/load	
Material:High purity silicon	
Other Specifications:	
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